

Toward adiabatic computation

July 10, 2015

NiPS Summer School 2015

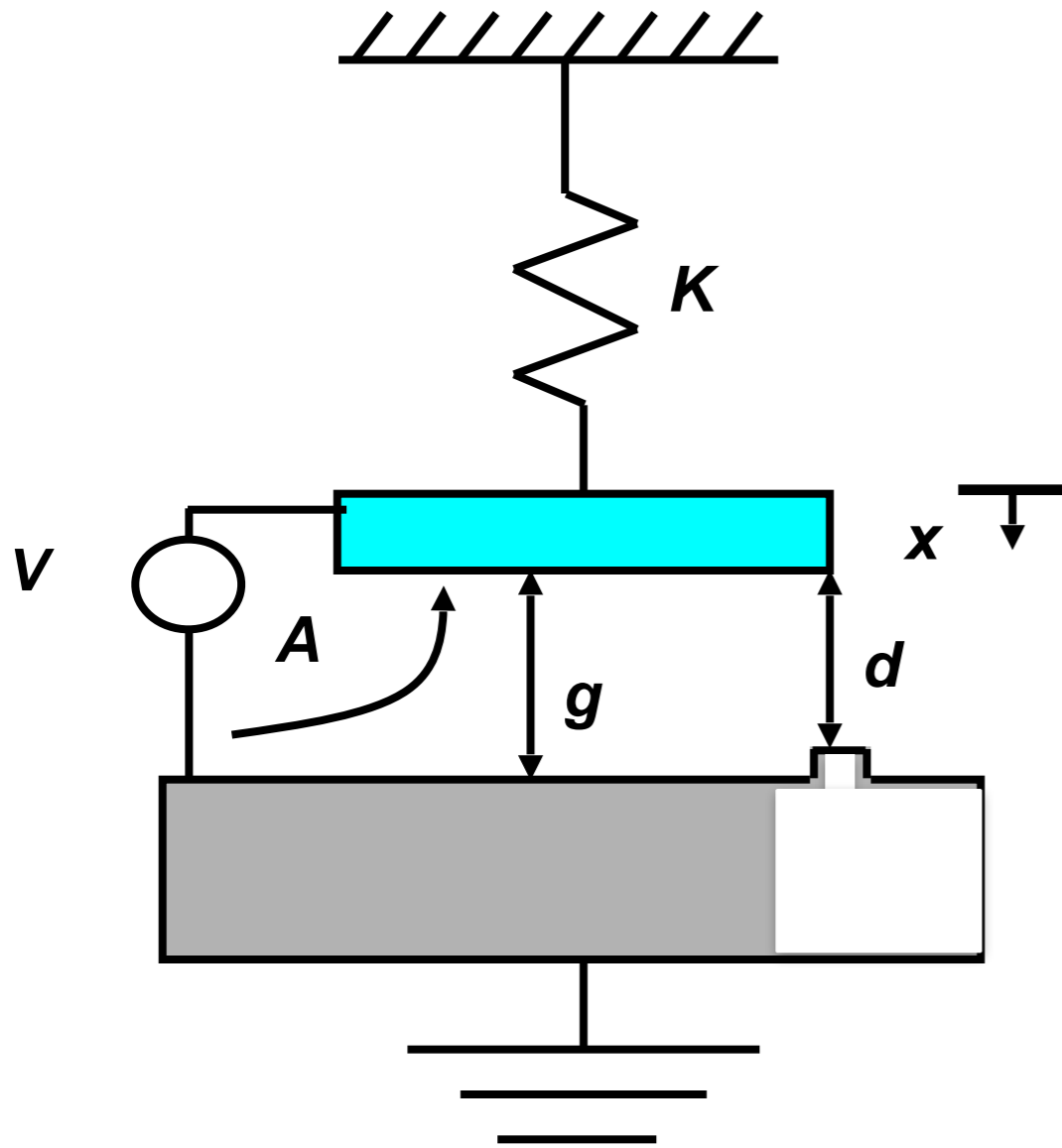
ICT-Energy: Energy consumption in future ICT devices



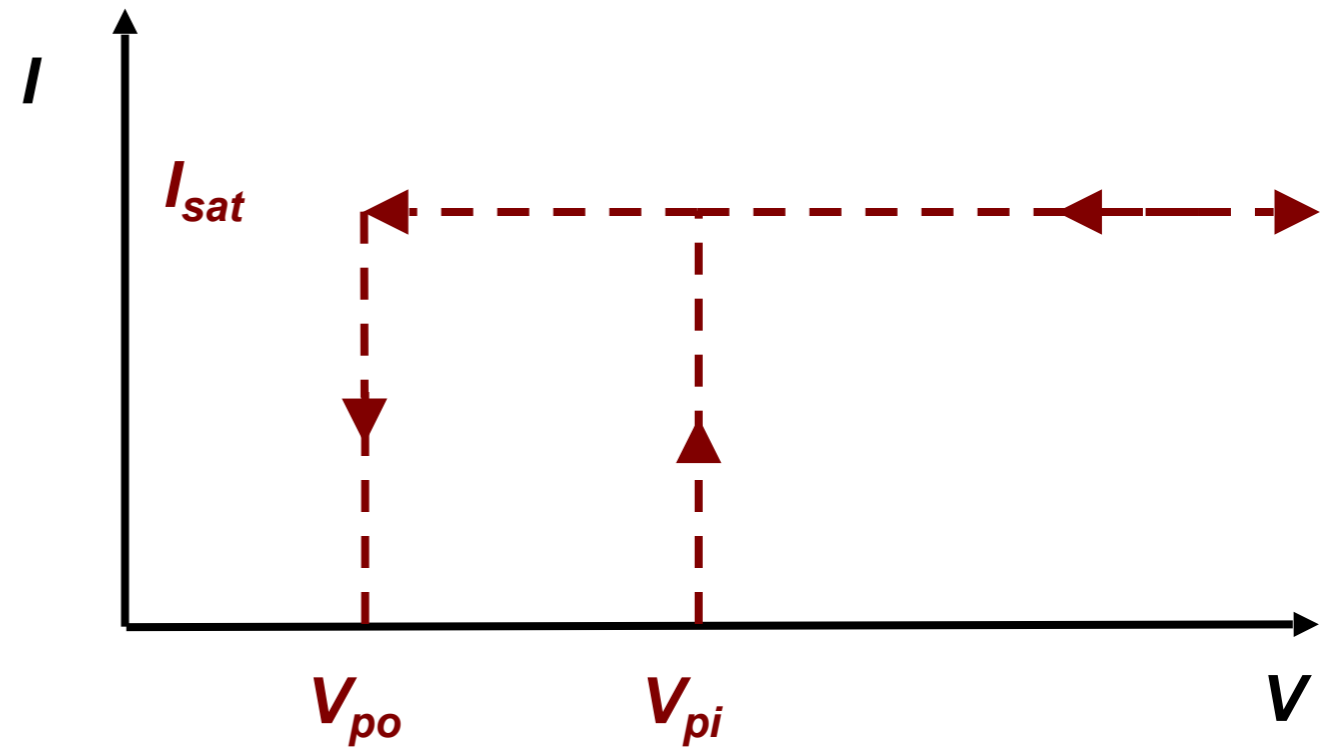
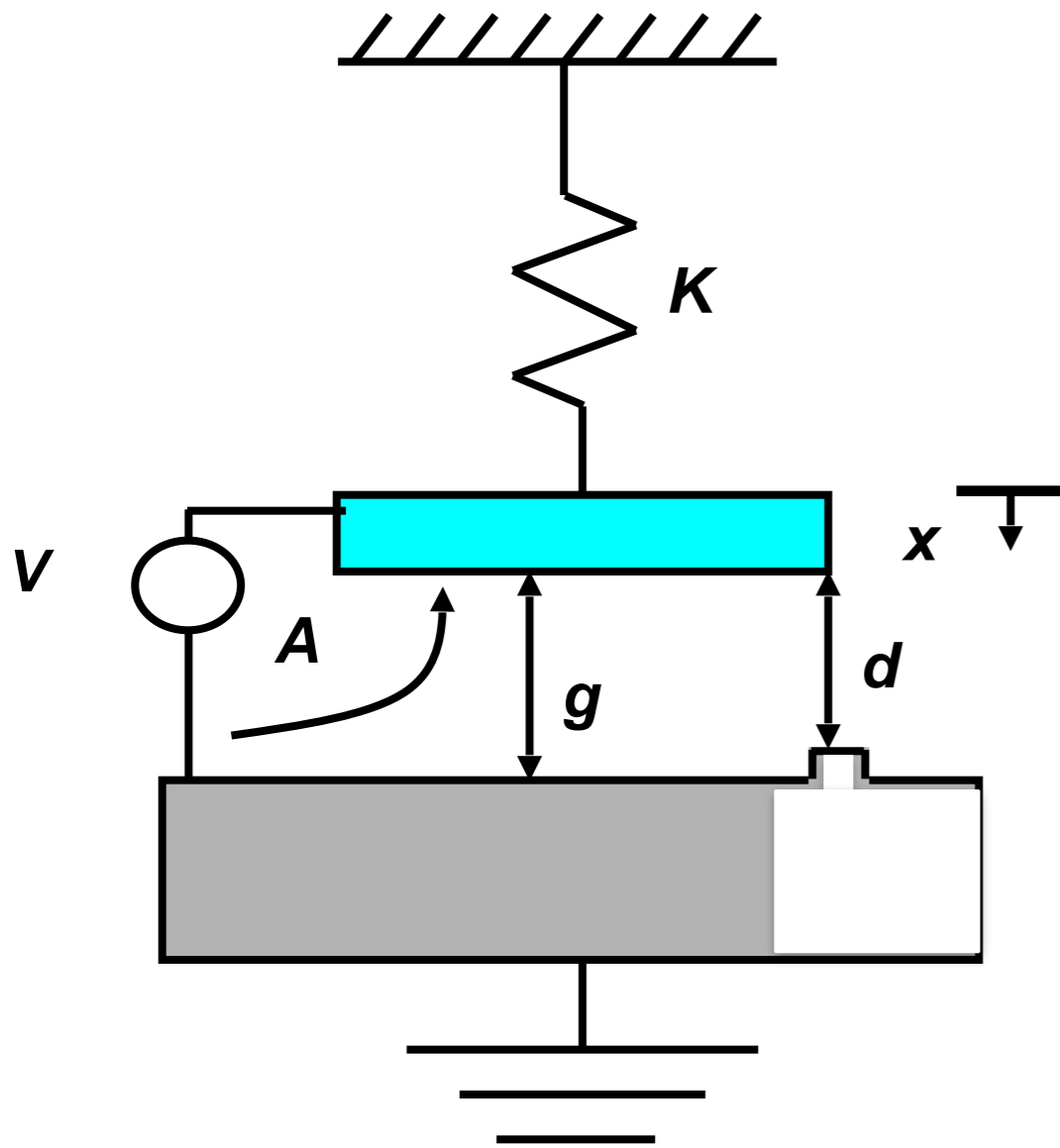
Outline

- Performance of NEMS switches: reality vs. necessity
- Adiabatic NEMS-based logic circuits
- Adiabatic MEMS logic gate
- Adiabatic NEMS memory device

Electrostatic NEMS Switches (back to basics)



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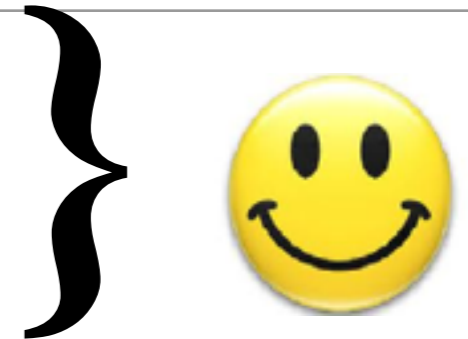
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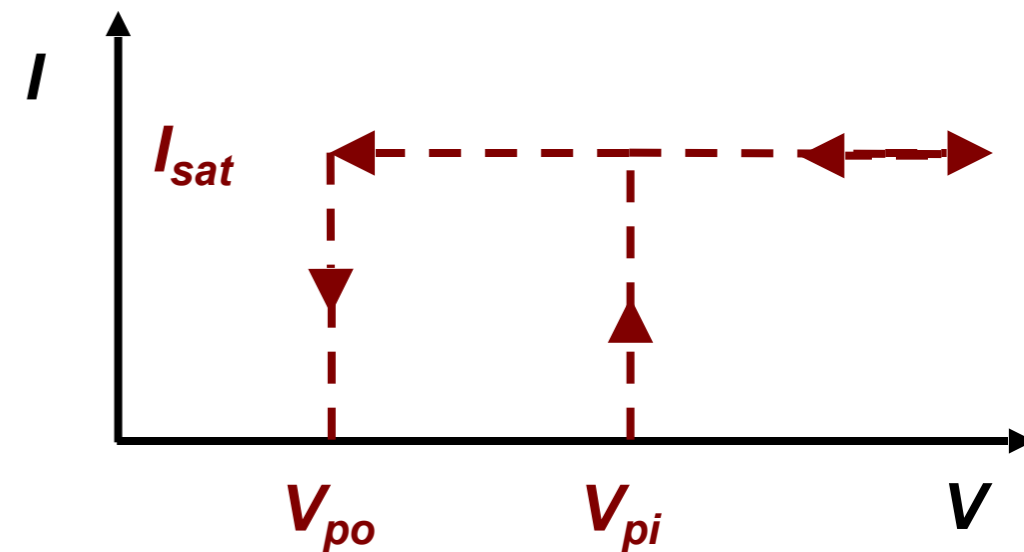
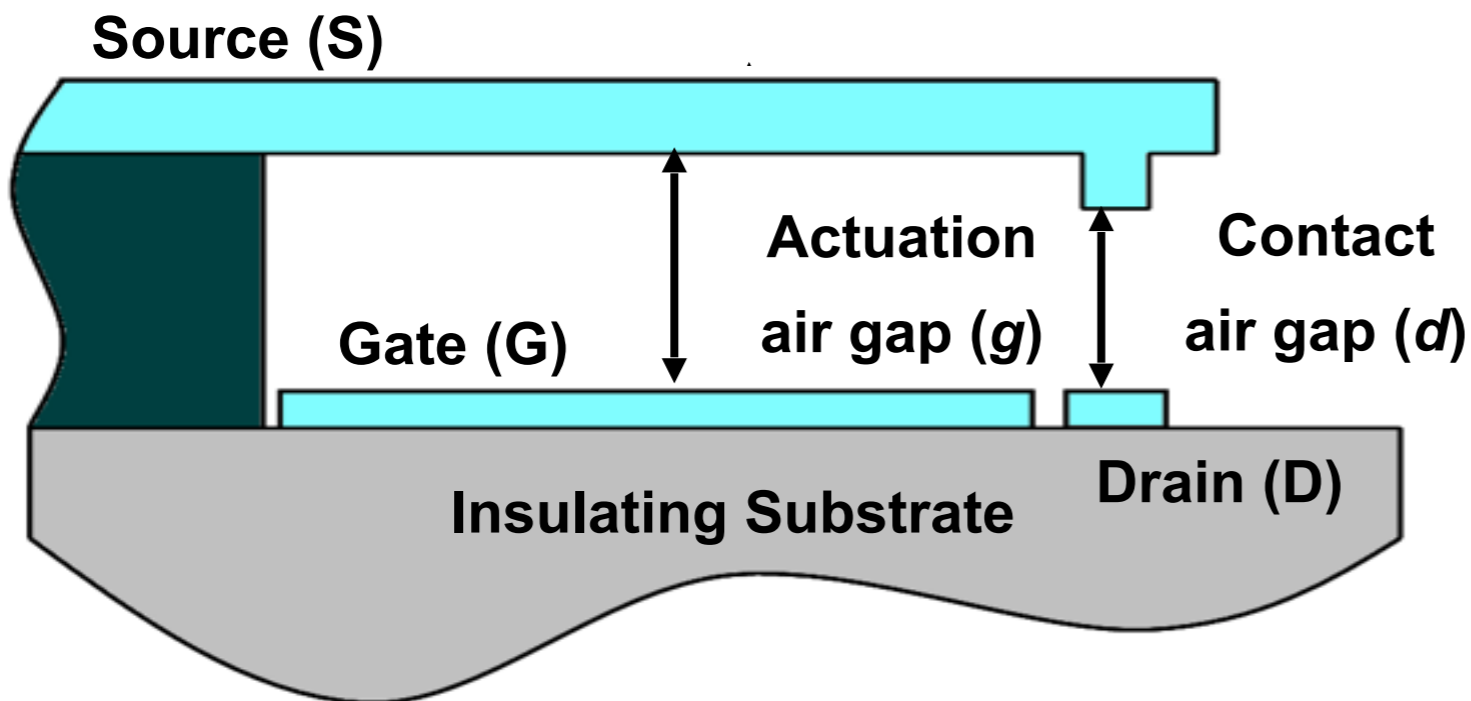
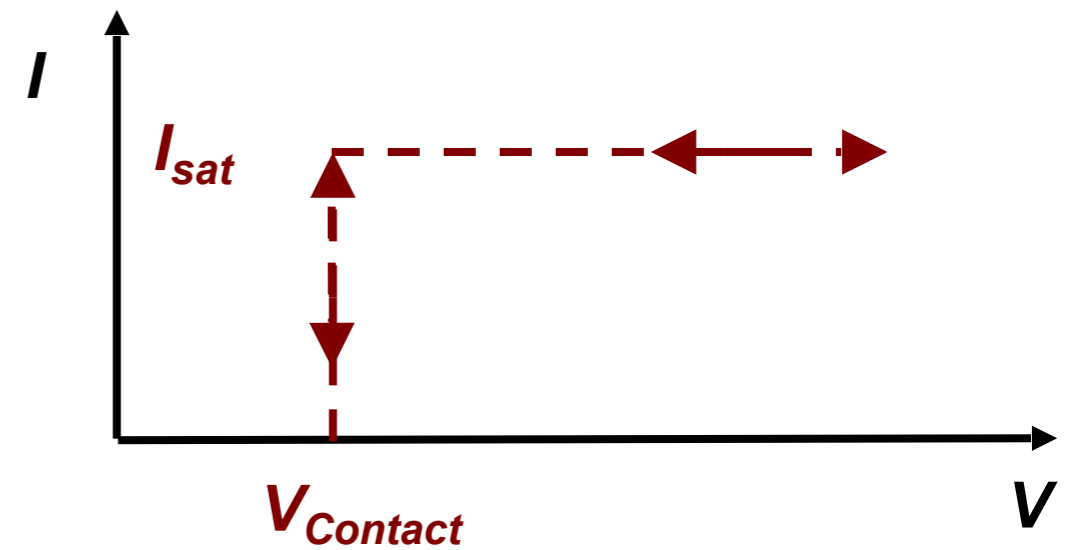
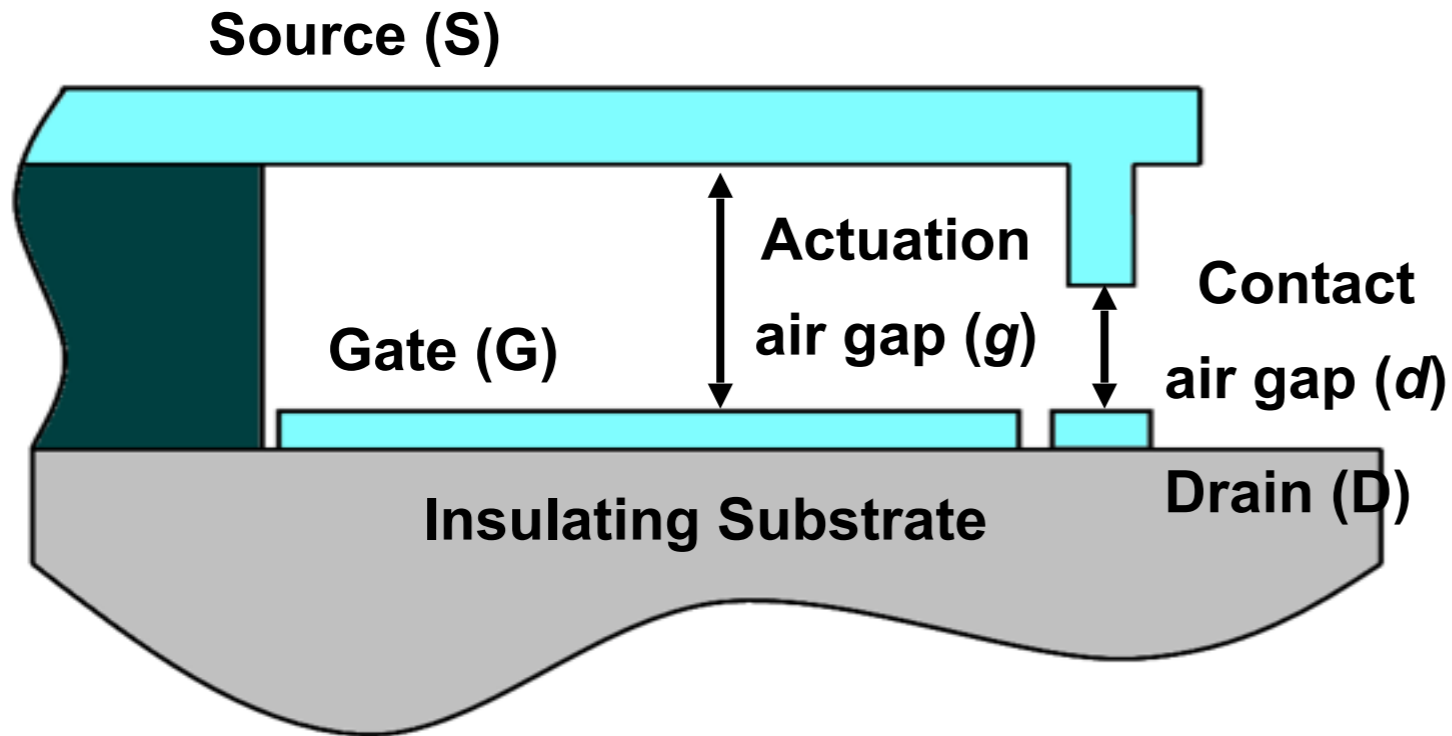
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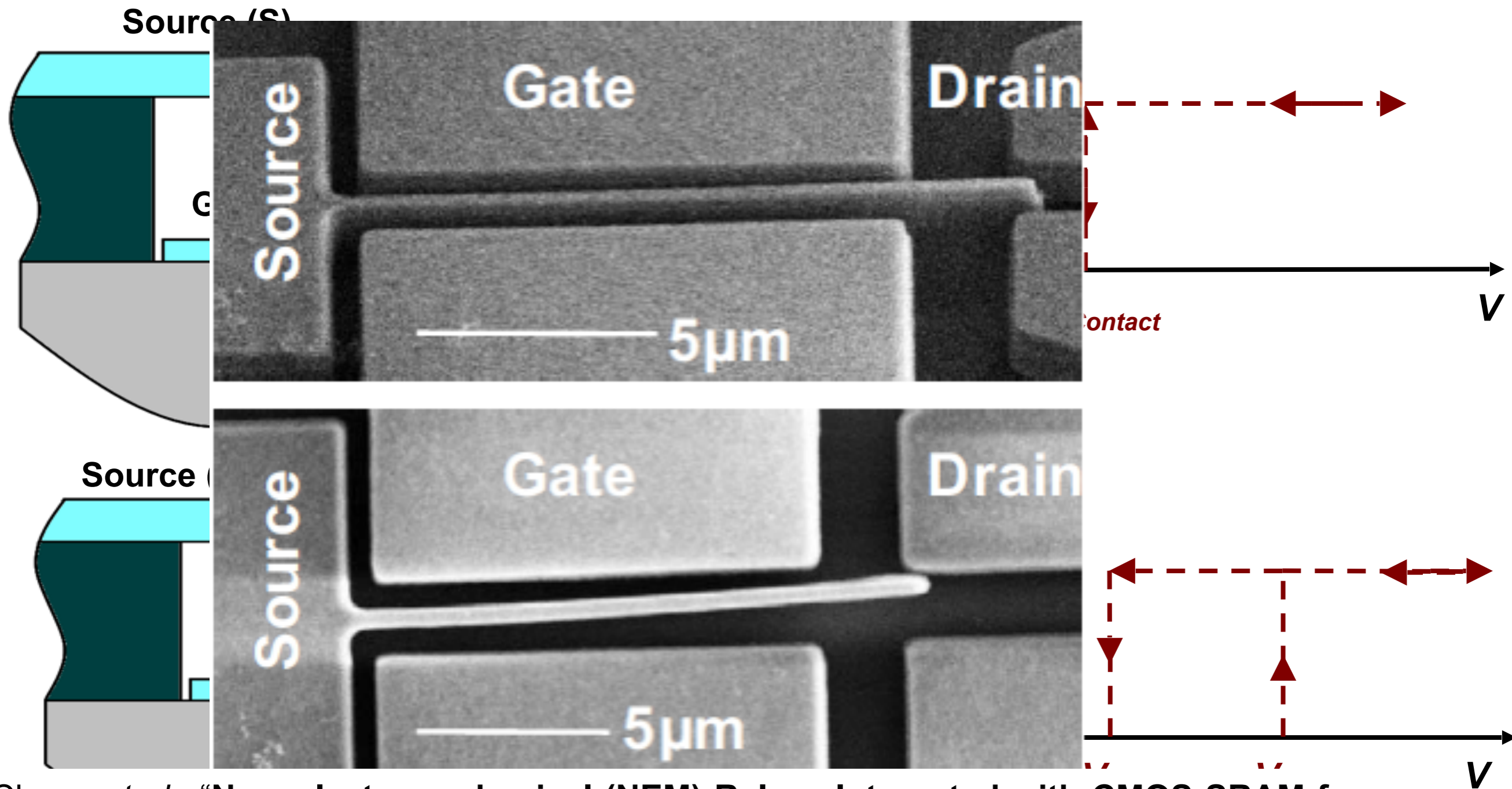
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Electrostatic NEMS Switches (back to basics)

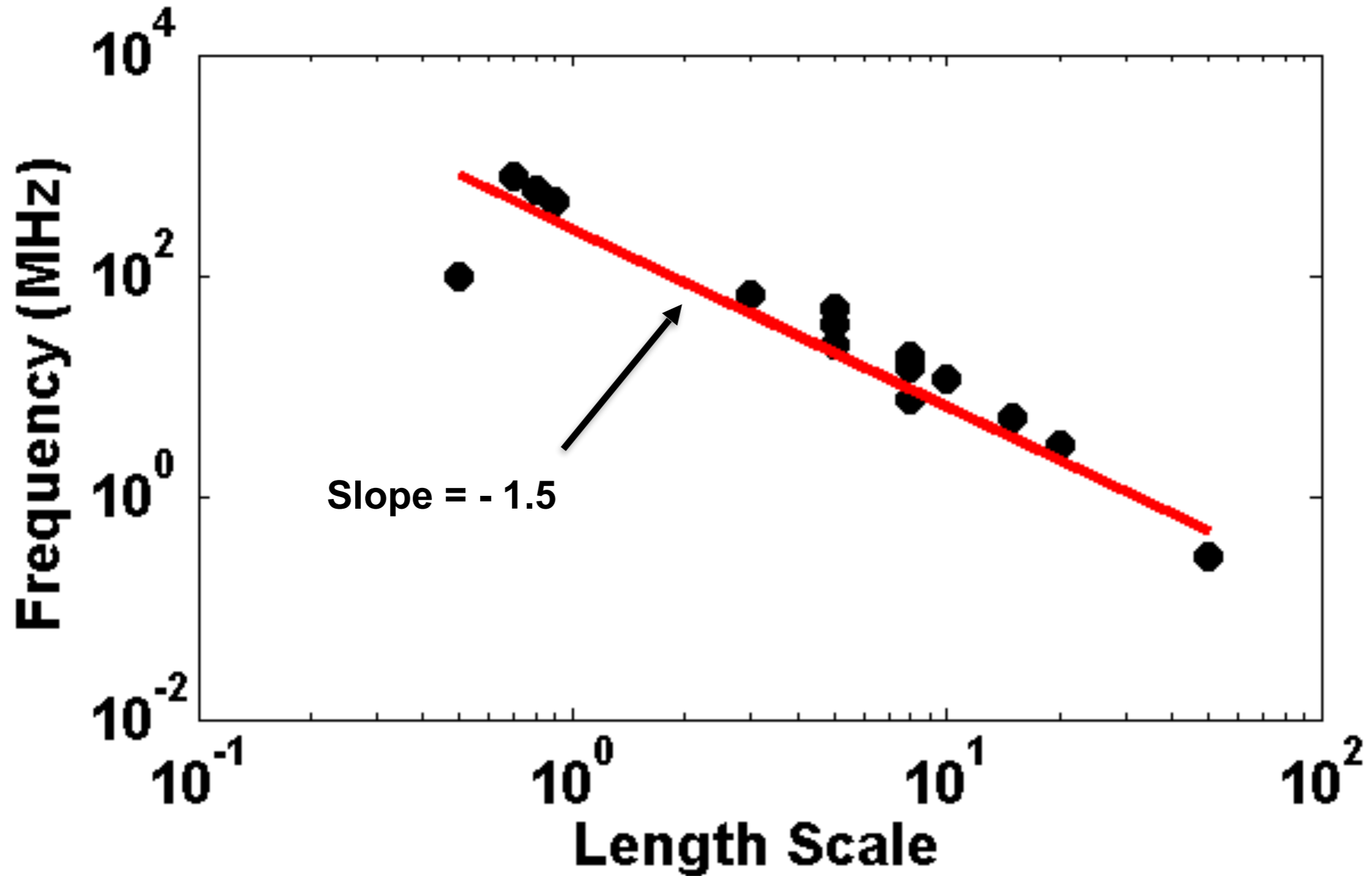


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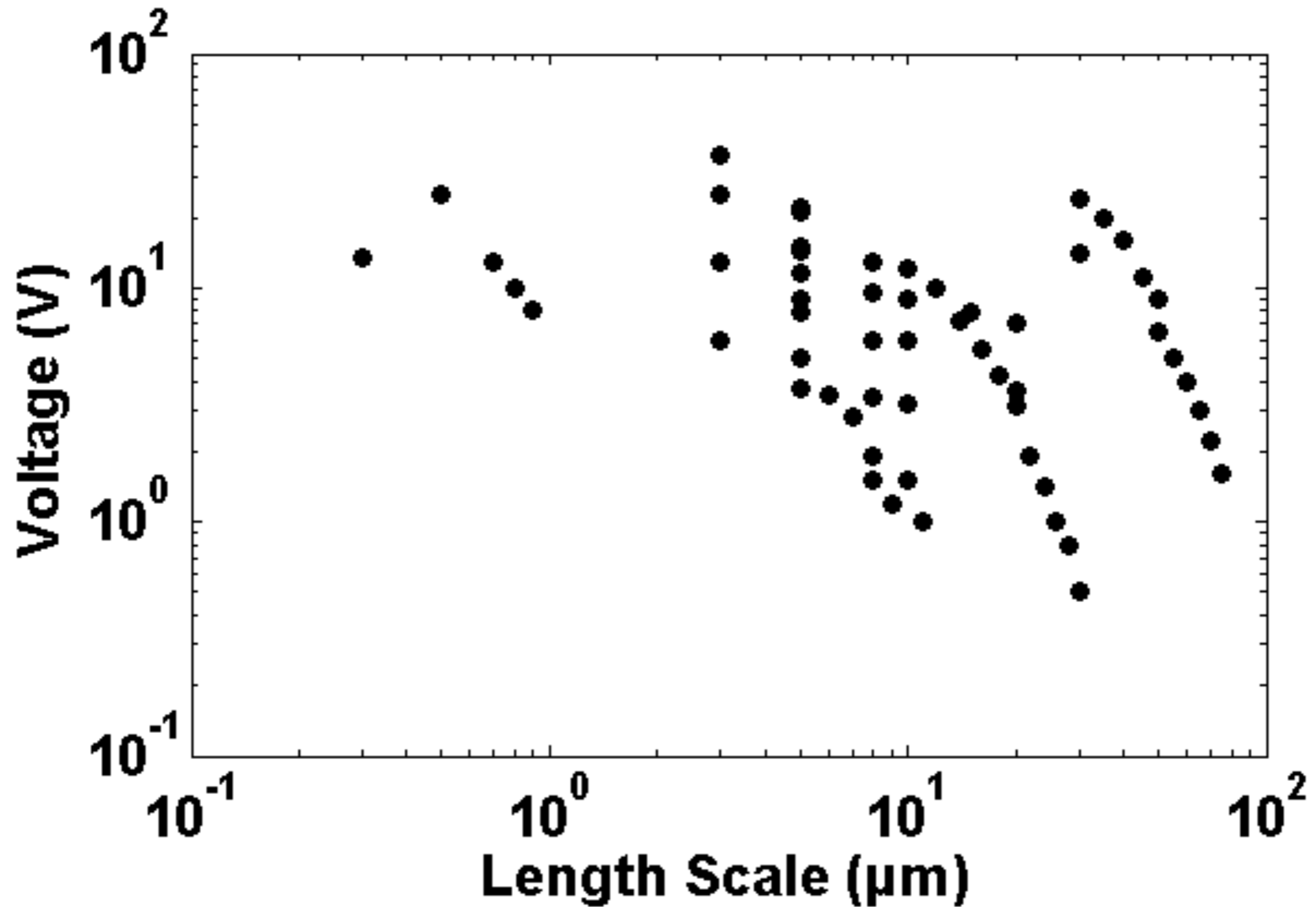


S. Chong *et al.*, “Nanoelectromechanical (NEM) Relays Integrated with CMOS SRAM for Improved Stability and Low Leakage”, *ICCAD 2009*.

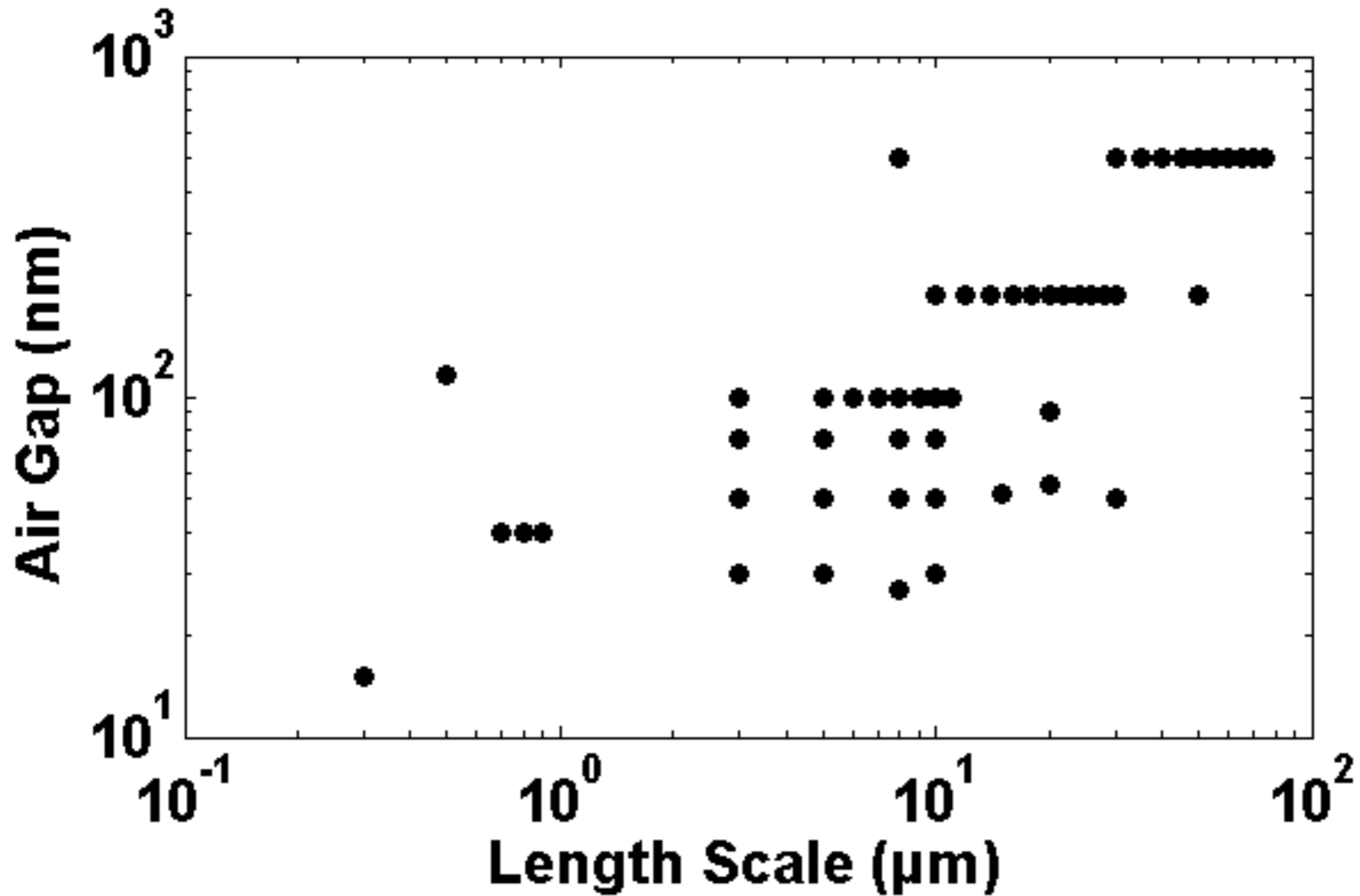
Scaling of NEMS Switches (*in real life*)



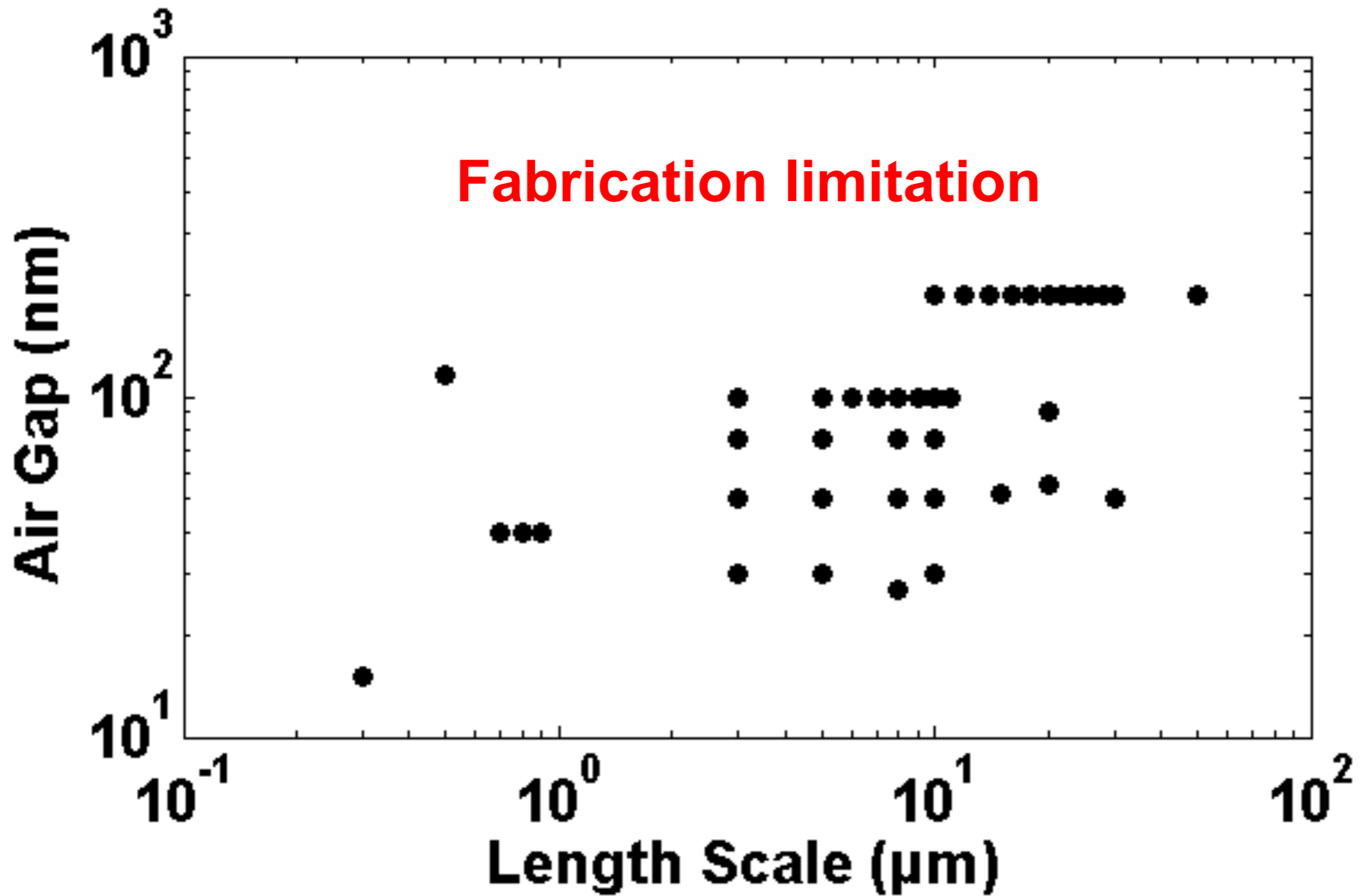
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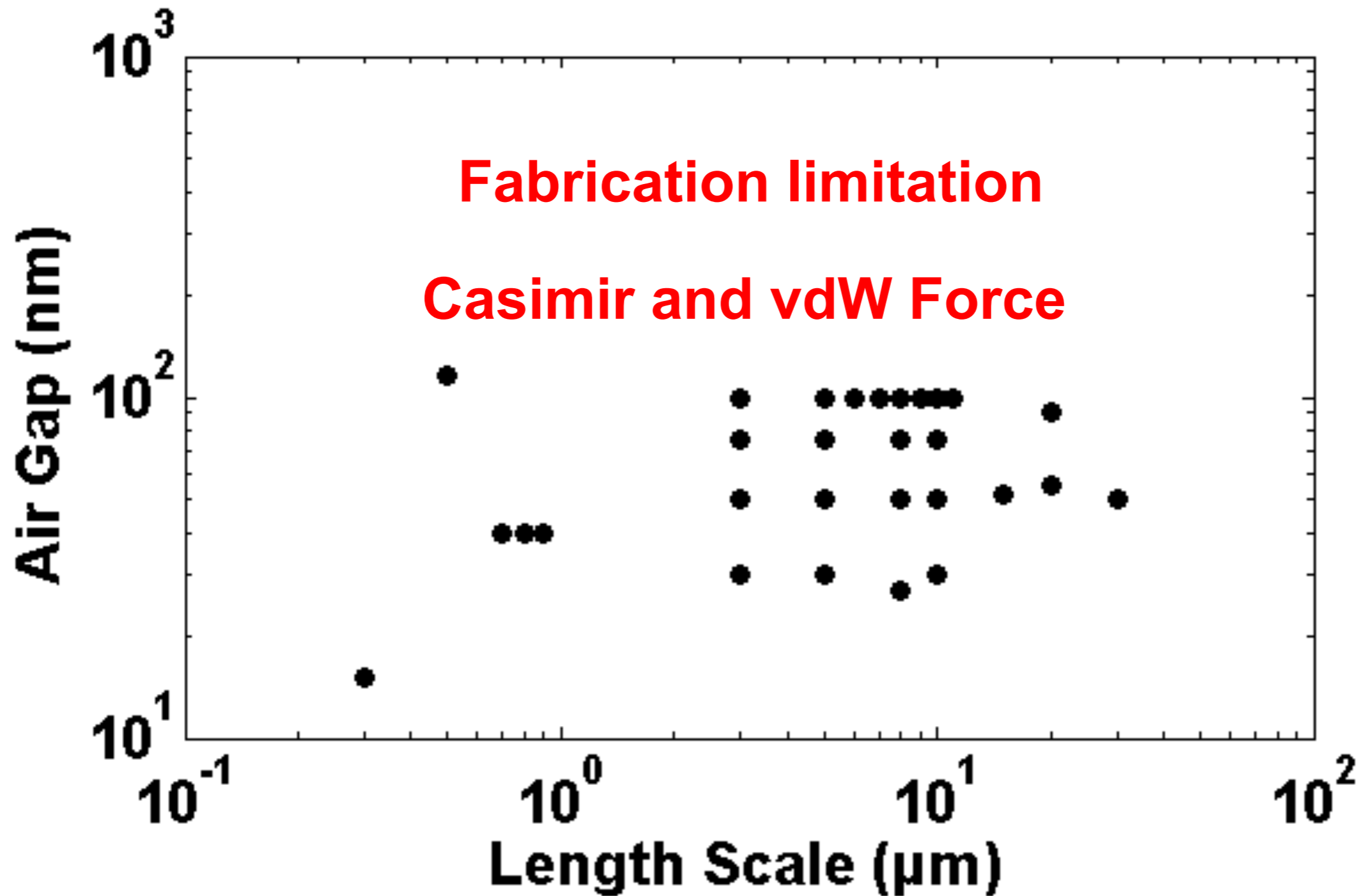
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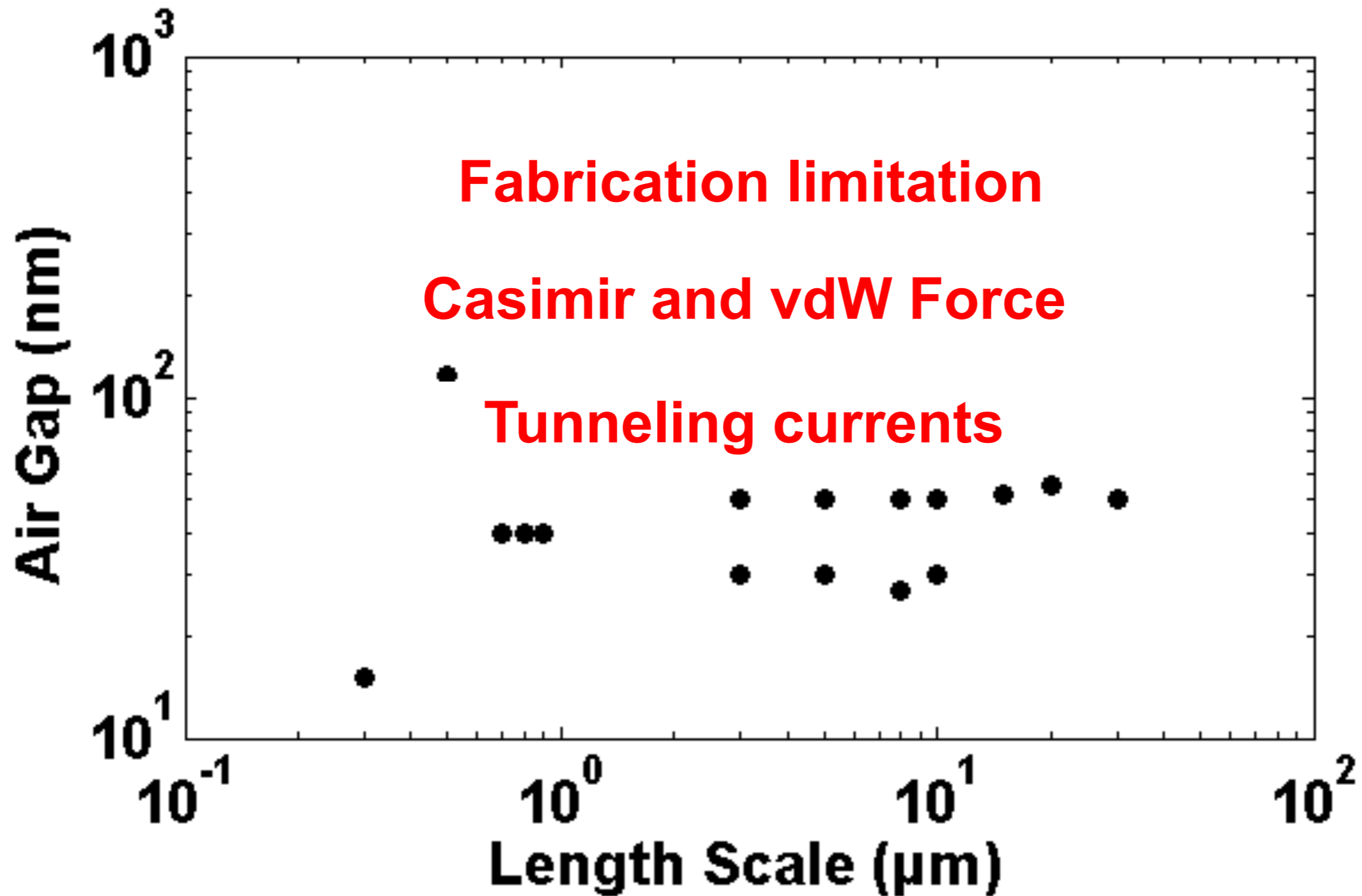
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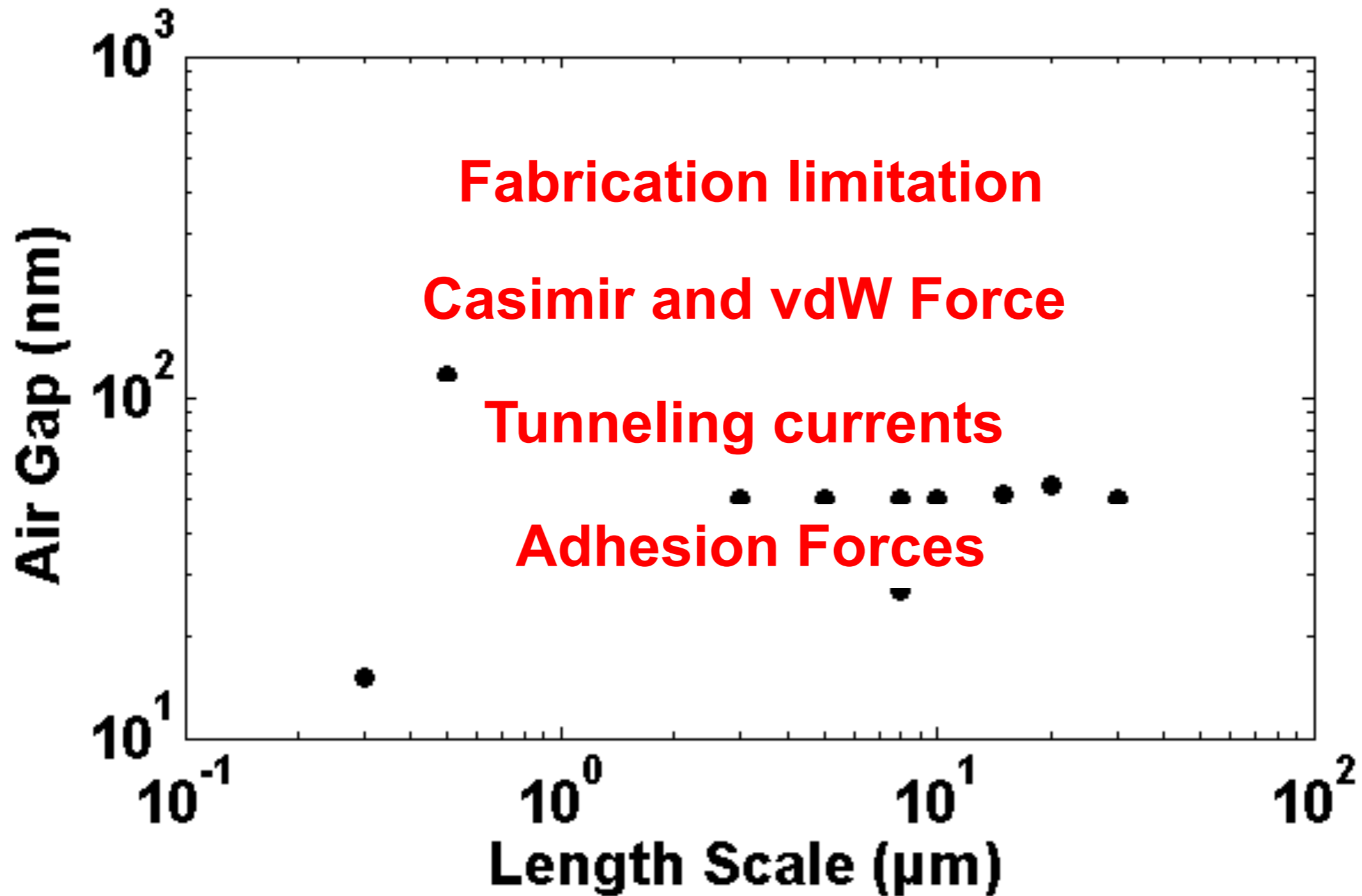
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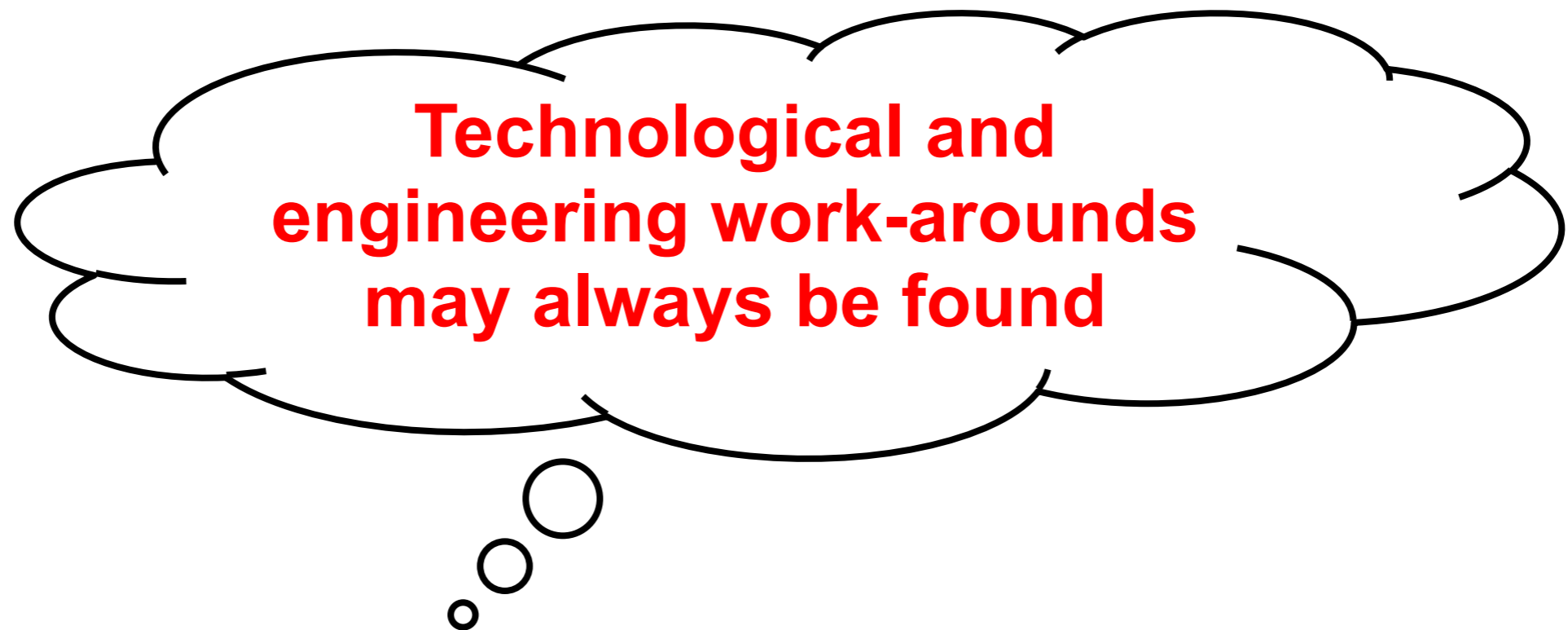


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Remember the end of Moore's law

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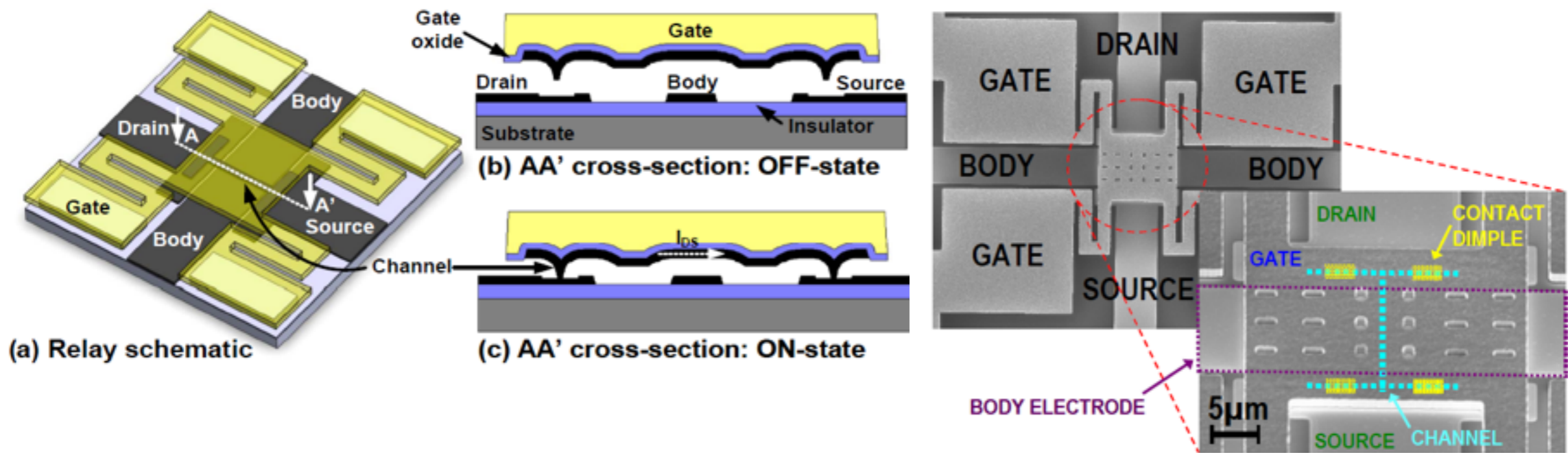
Some possible solutions

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R. Nathanael *et al.*, “4-Terminal Relay Technology for Complementary Logic”, *IEDM*, 2009.

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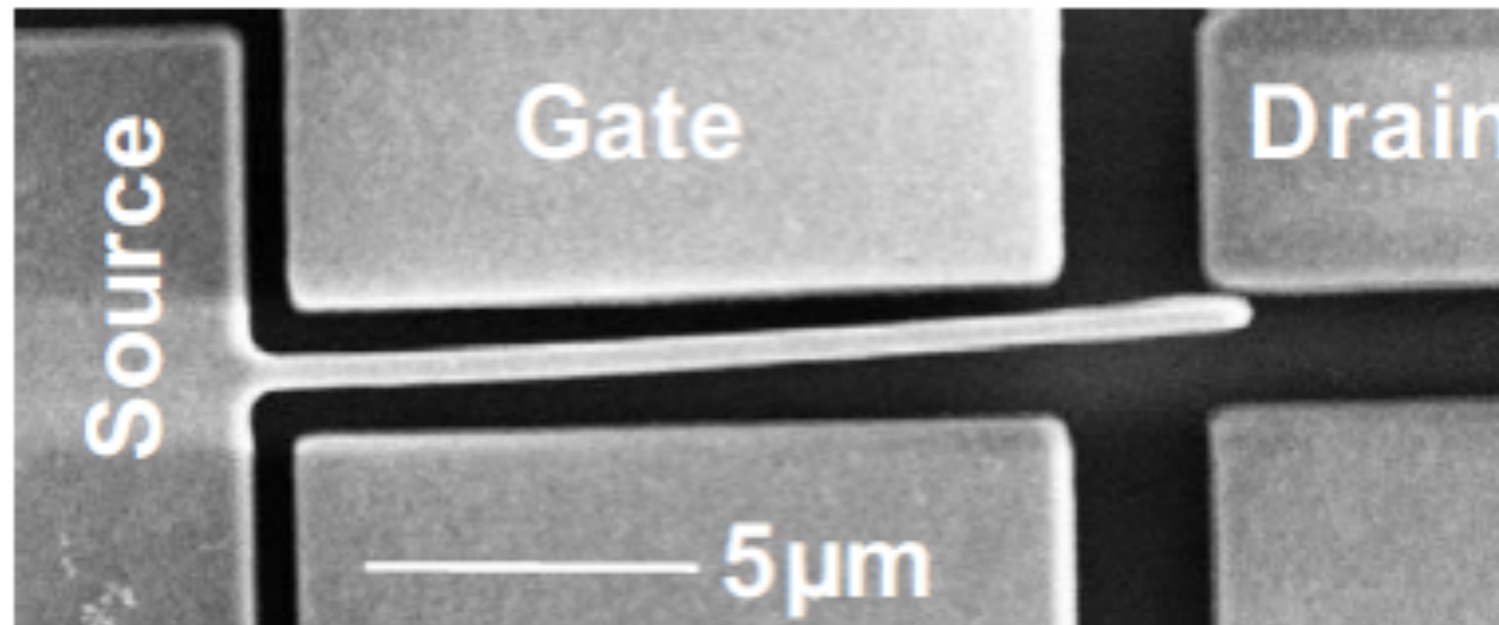
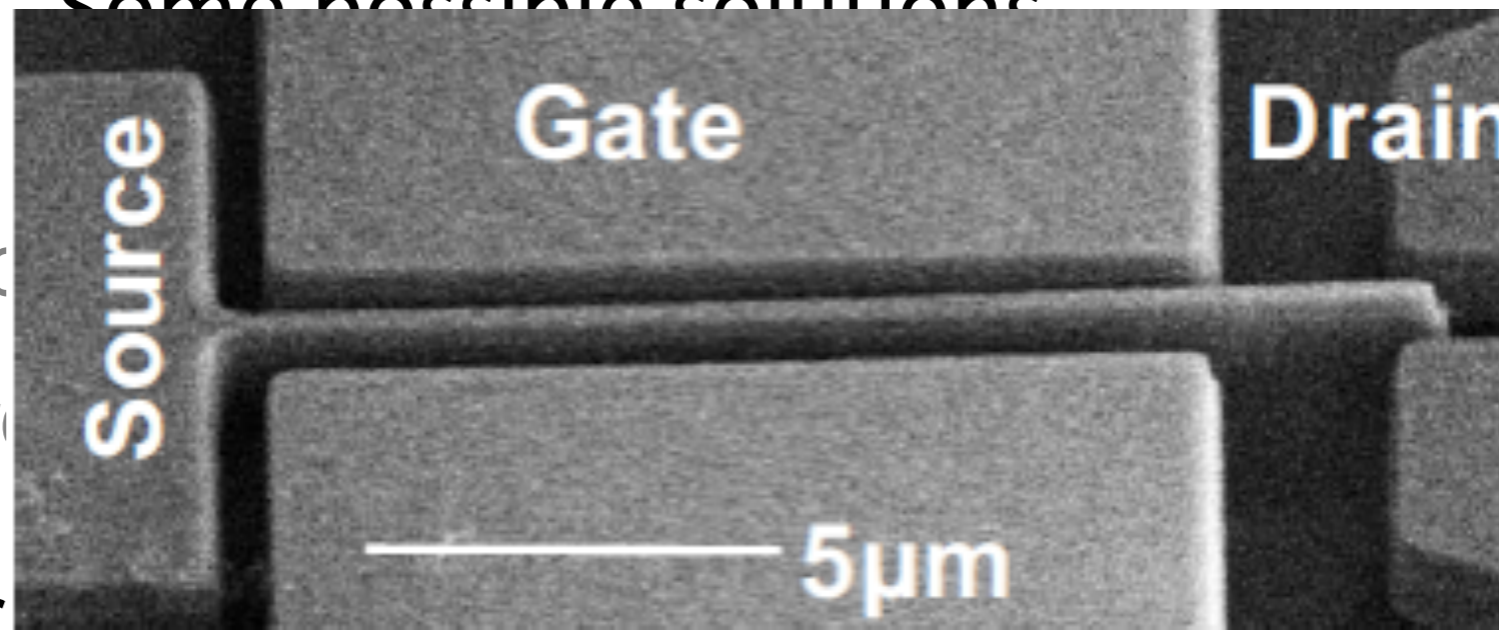
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- Apply pre-baked adhesion for
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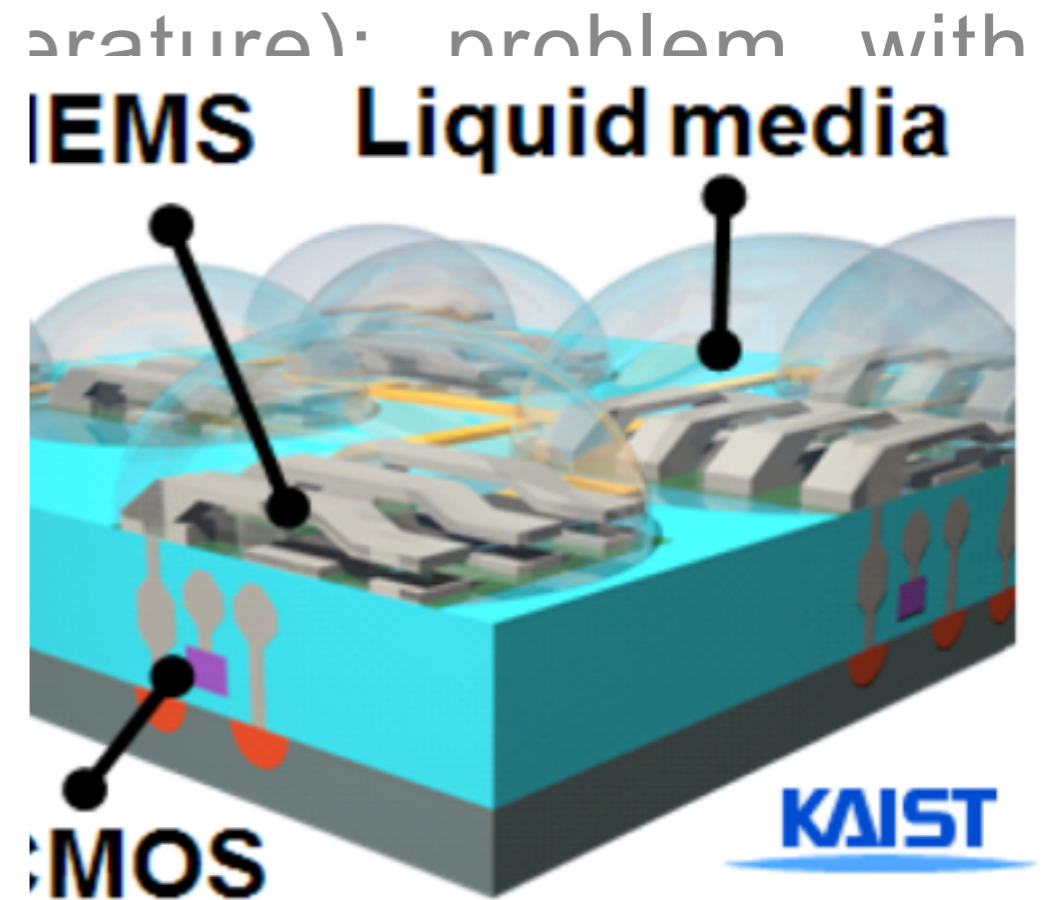
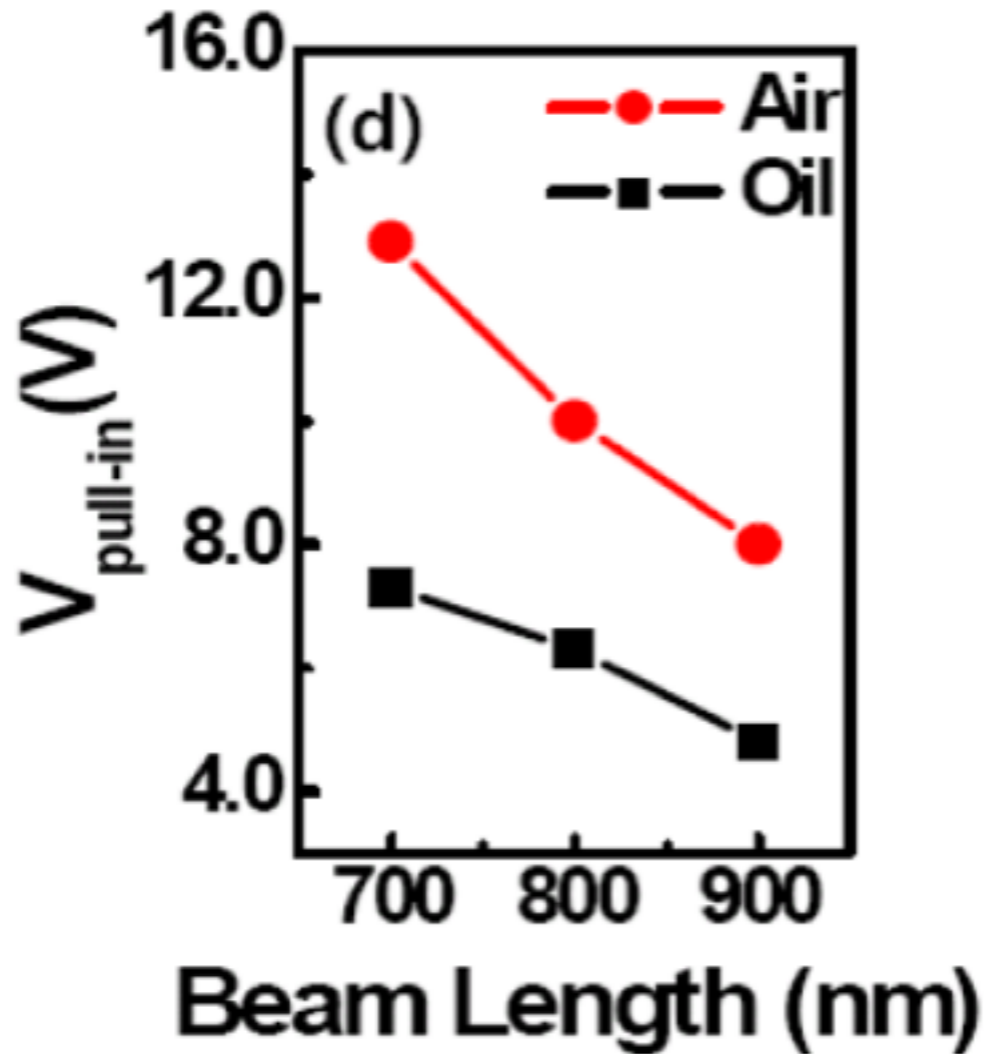
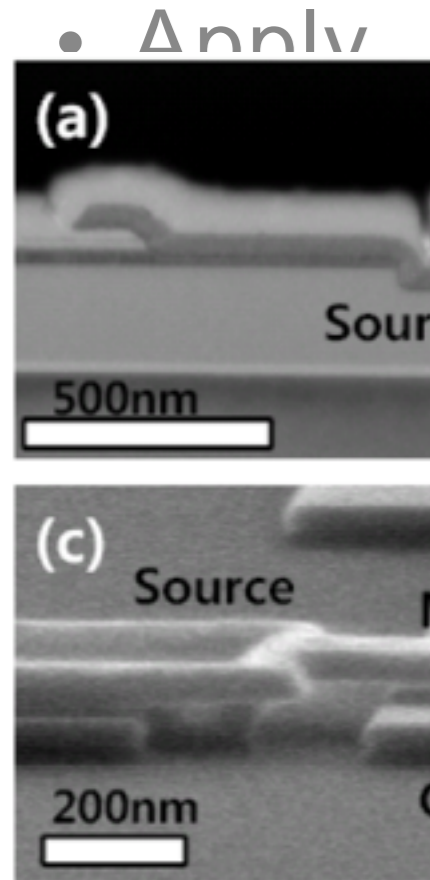
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J-O Lee *et al.*, "3-Terminal Nanoelectromechanical Switching Device in Insulating Liquid Media for Low Voltage Operation and Reliability Improvement", IEDM 2009

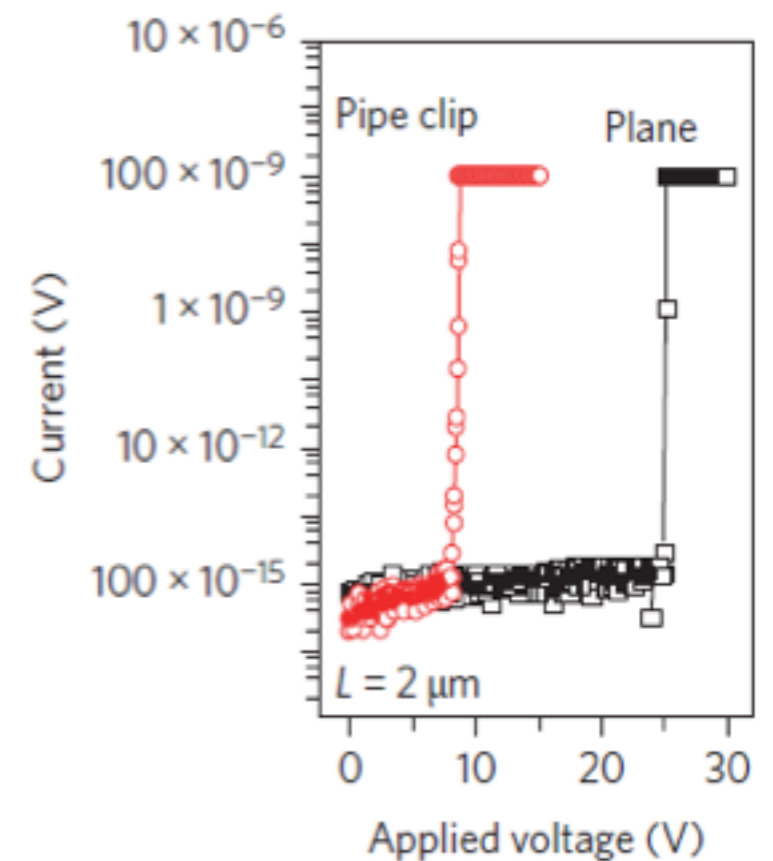
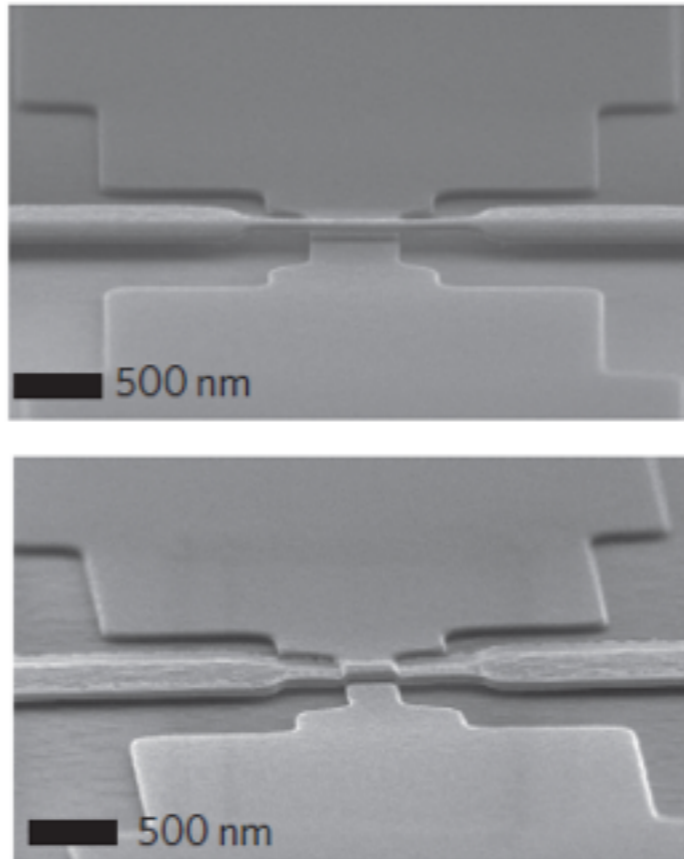
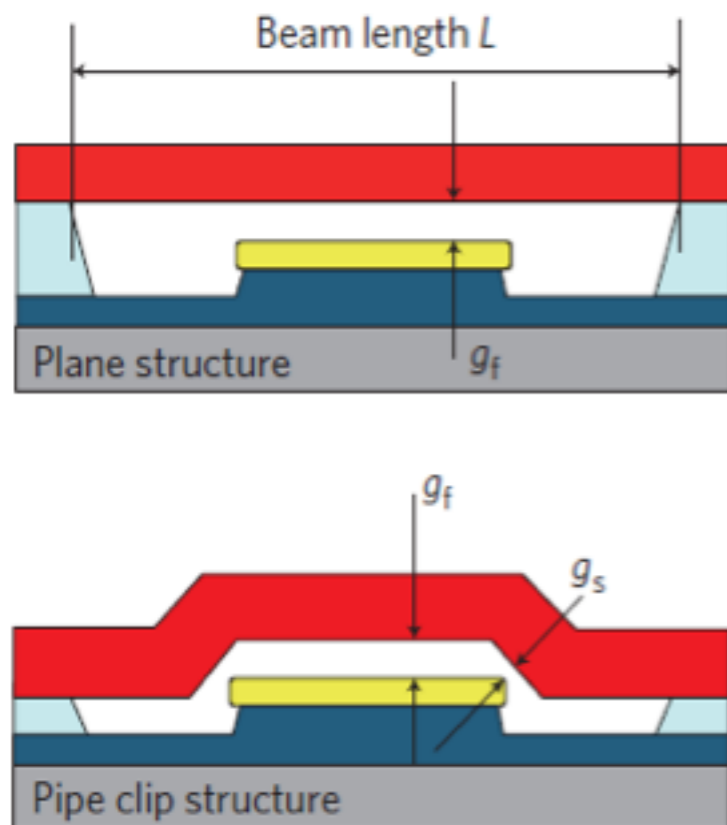
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- **Innovative fabrication process**

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J. O. Lee *et al.*, "A sub-1-volt nanoelectromechanical switching device", *nature nanotechnology*, 2012.

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- Innovative fabrication process
- **Explore new materials and modes of operation**

NEMS-Based Adiabatic Logic Circuits A Match Made in Heaven ?

NEMS-Based Adiabatic Logic

Circuit Level Approach

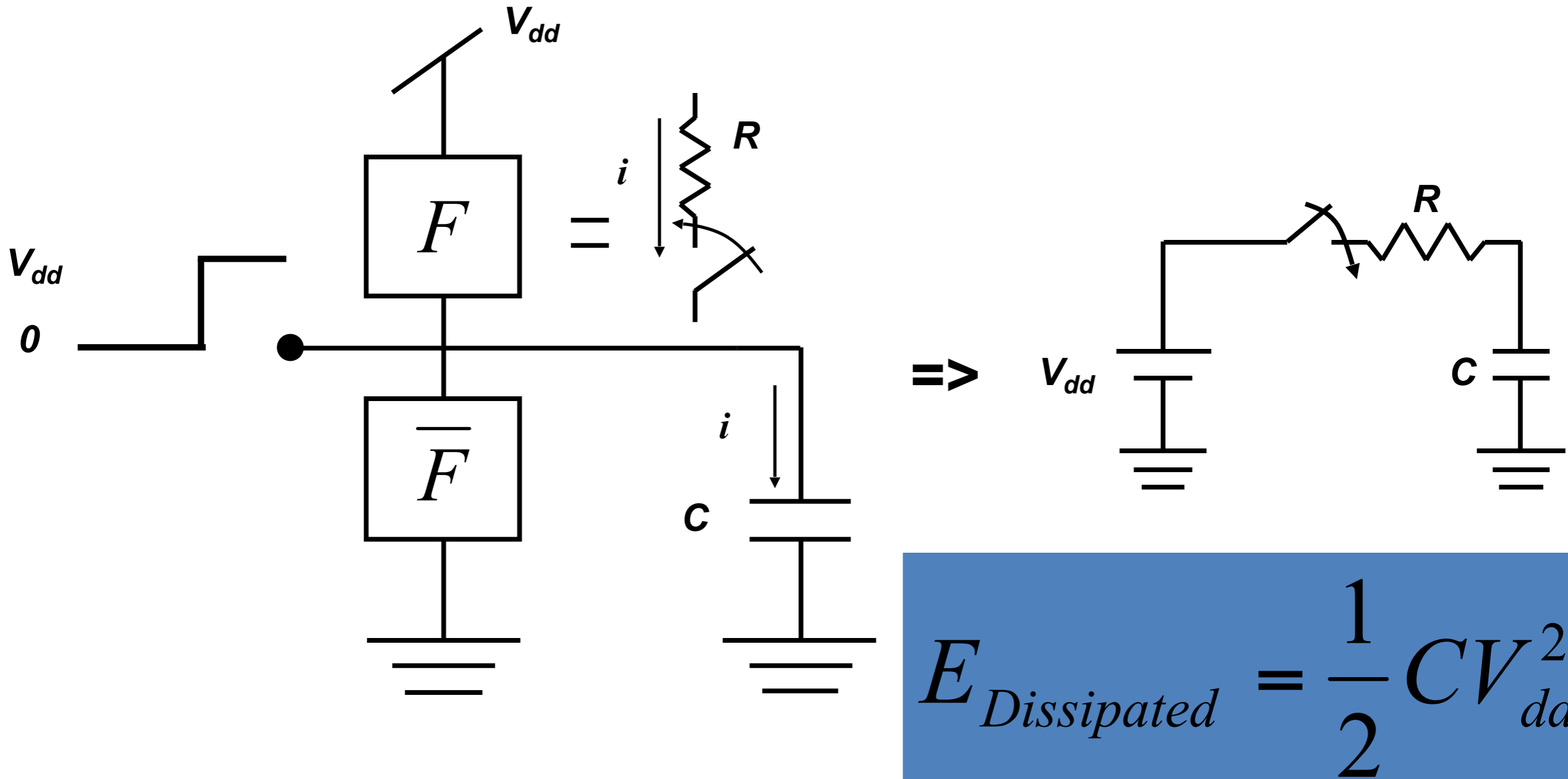
- Sub-threshold
- Parallelism
- Power Gating
- Asynchronous
- **Adiabatic**

+

Device Level Approach

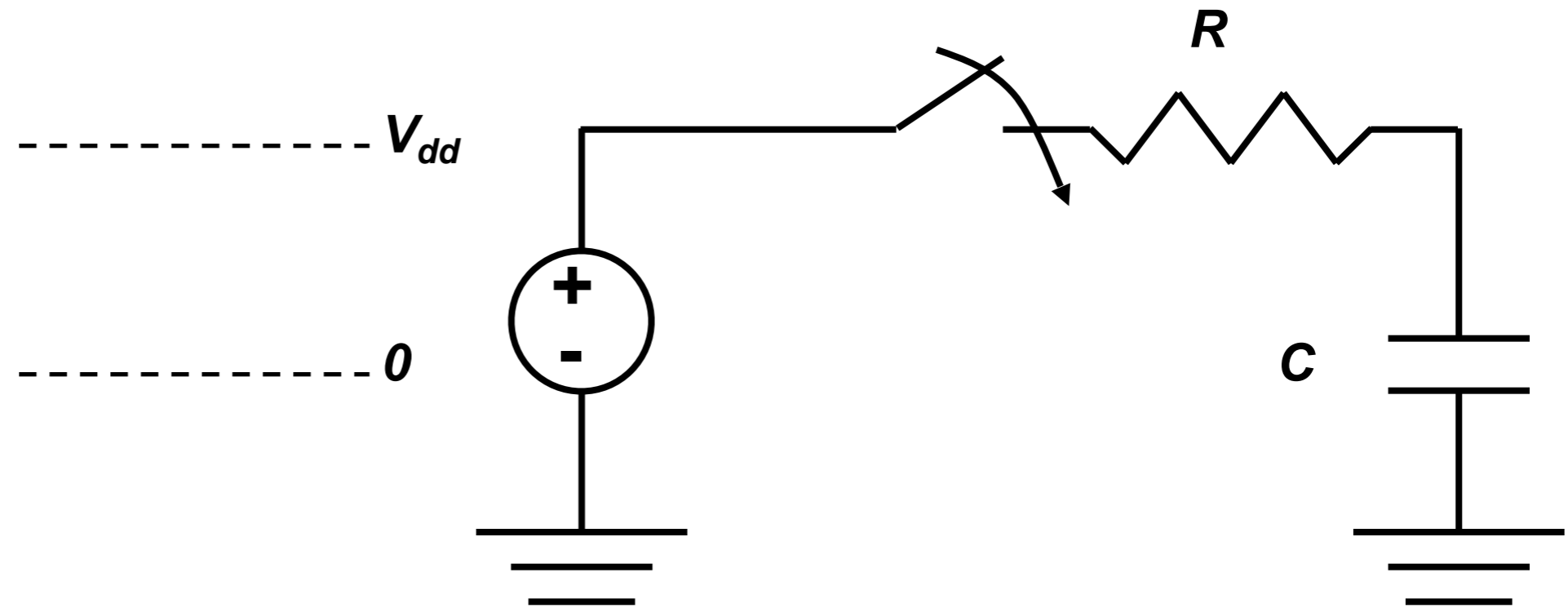
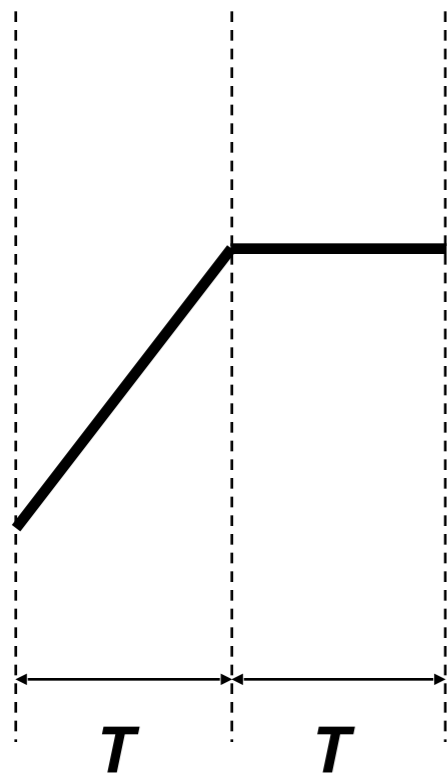
- SOI/ FDSOI
- FinFET
- TFET
- III-V FET
- NWFET
- CNTFET
- **NEMS**

Classical Logic (*quick reminder*)



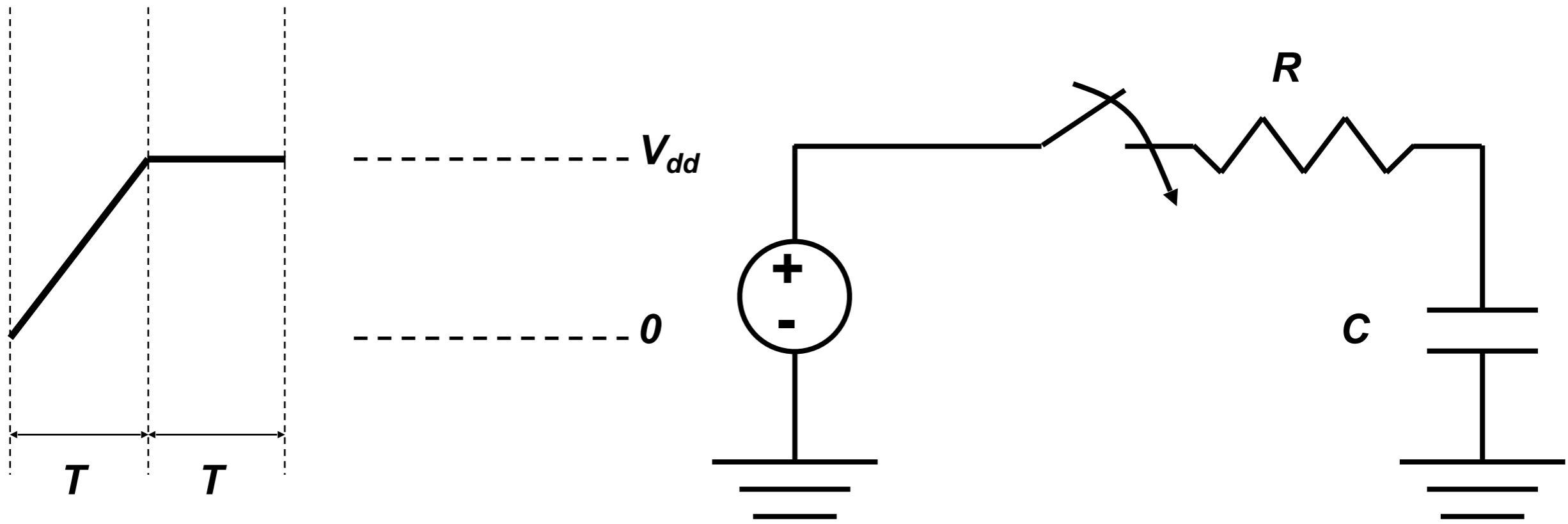
$$E_{Dissipated} = \frac{1}{2} C V_{dd}^2$$

Adiabatic Charging of Capacitors



S. Paul, A. M. Schlaffer, J. A. Nossek, "Optimal charging of capacitors," *IEEE Transactions on Circuits and Systems –I*, vol. 47, pp. 1009-1016, July 2000.

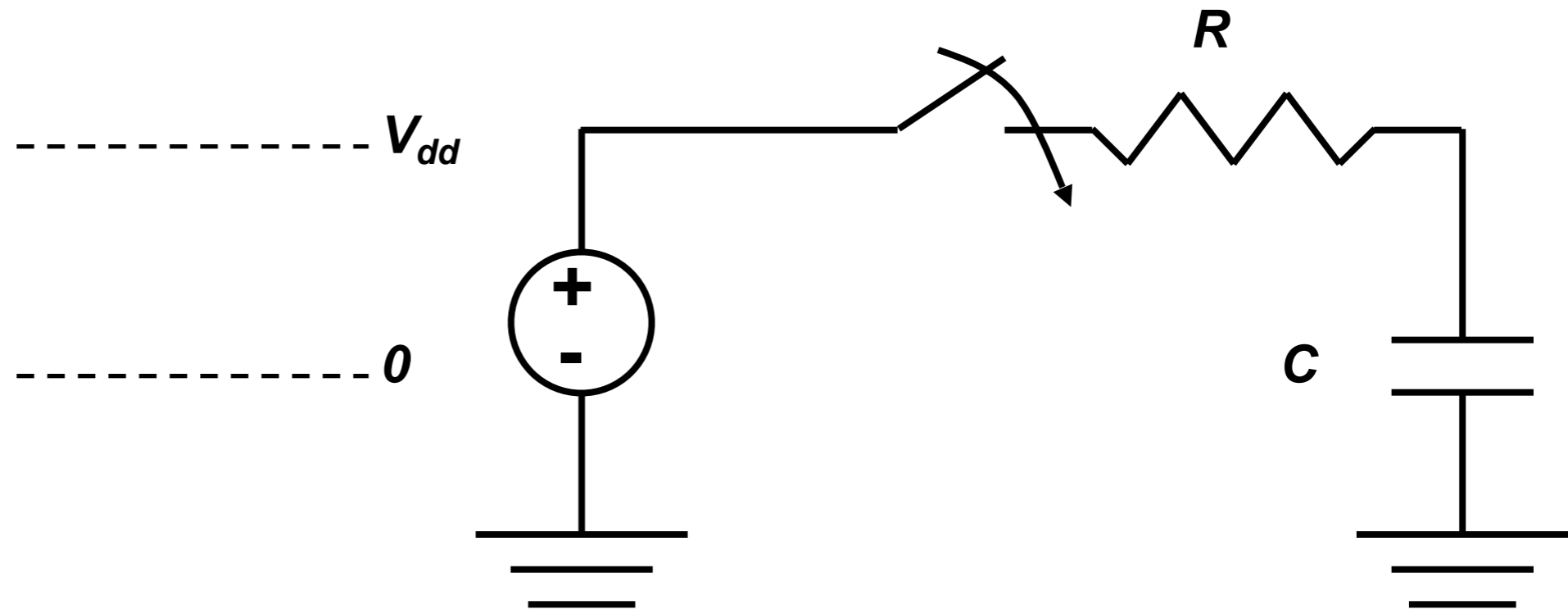
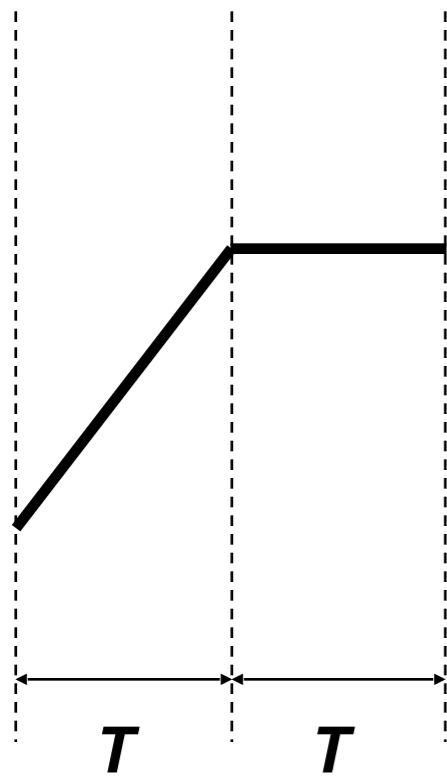
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$$E_{adiabatic} \cong \frac{RC}{T} CV^2$$

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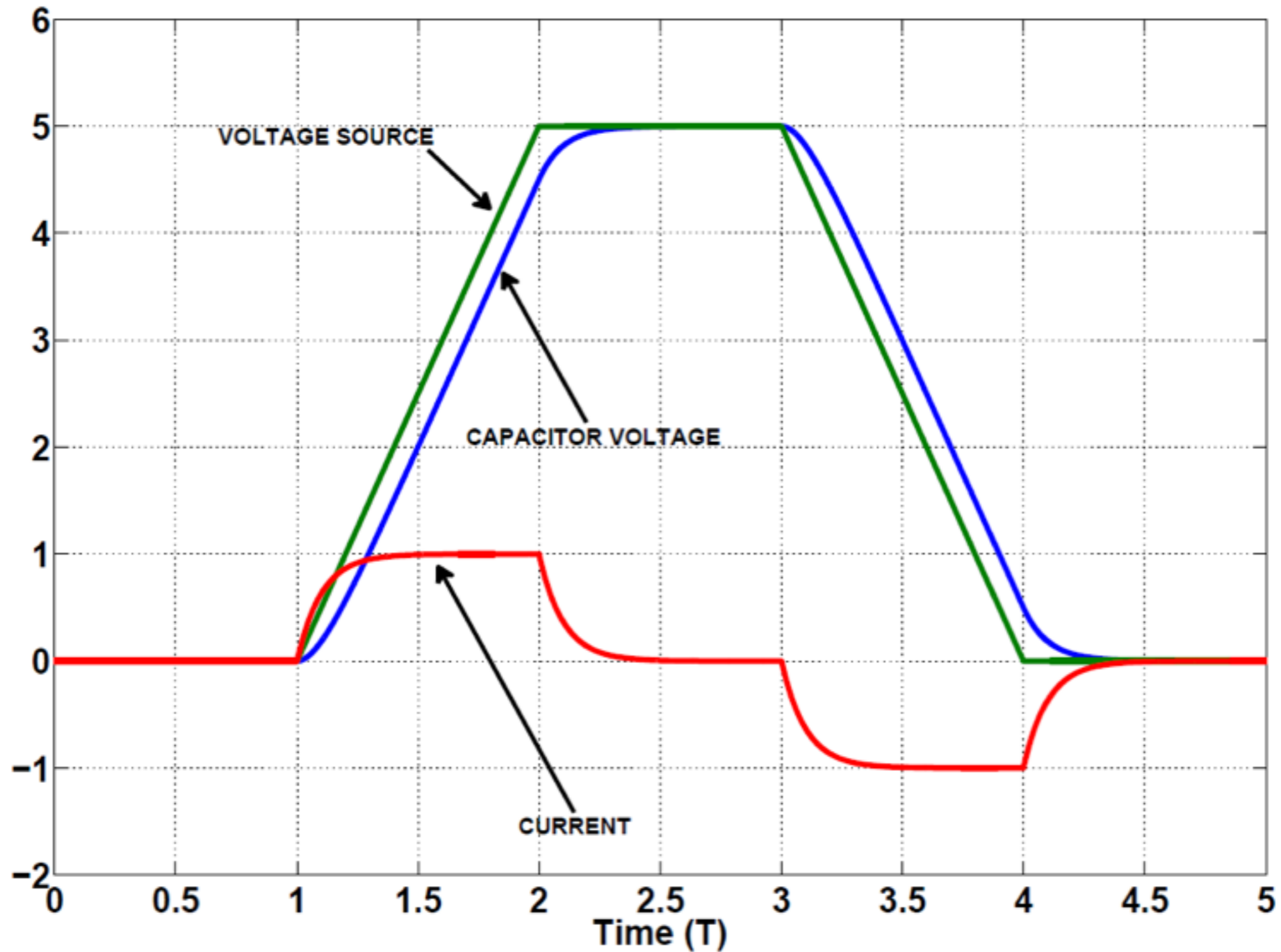


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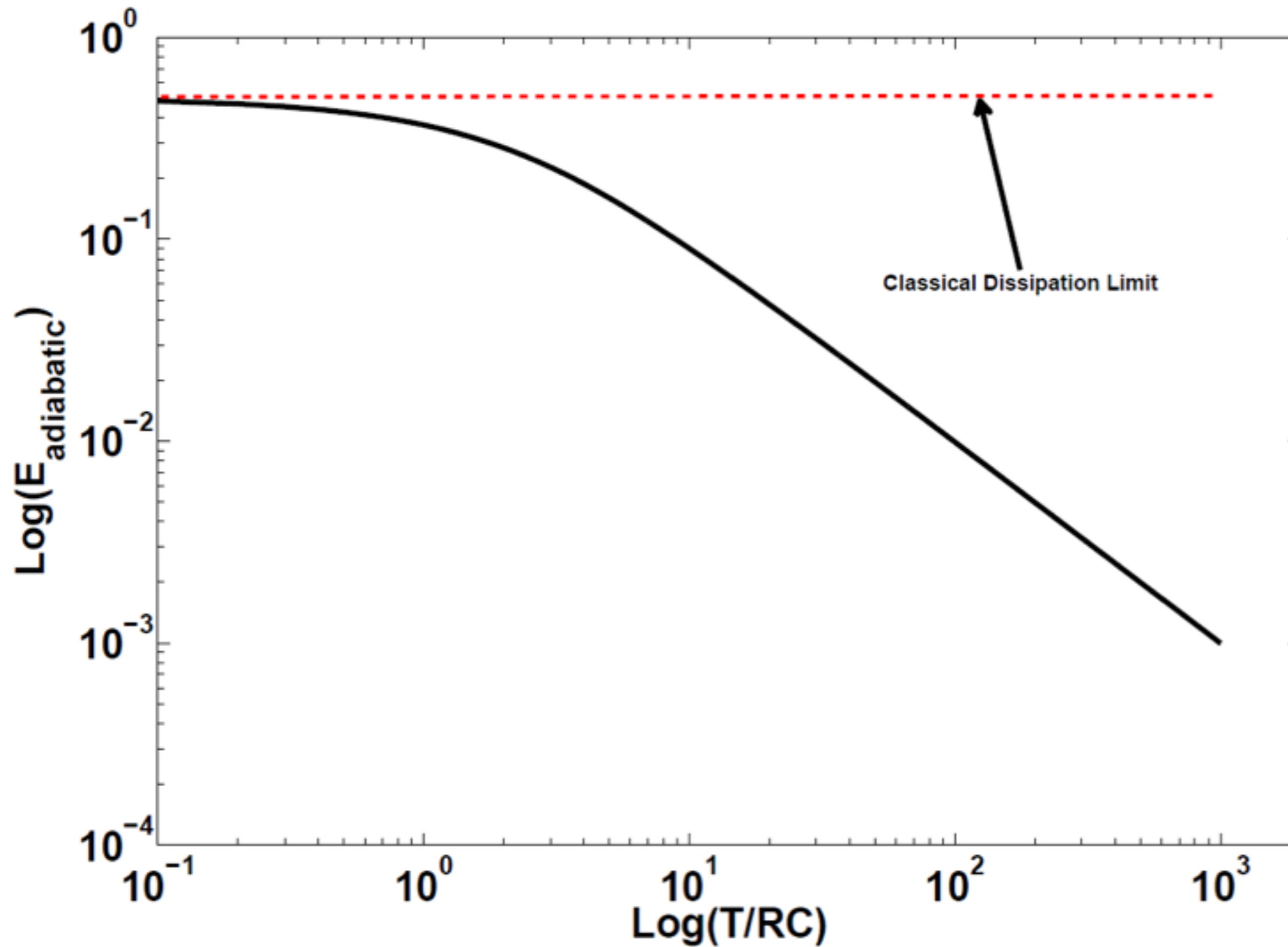
$$ESF \cong \frac{T}{2RC}$$

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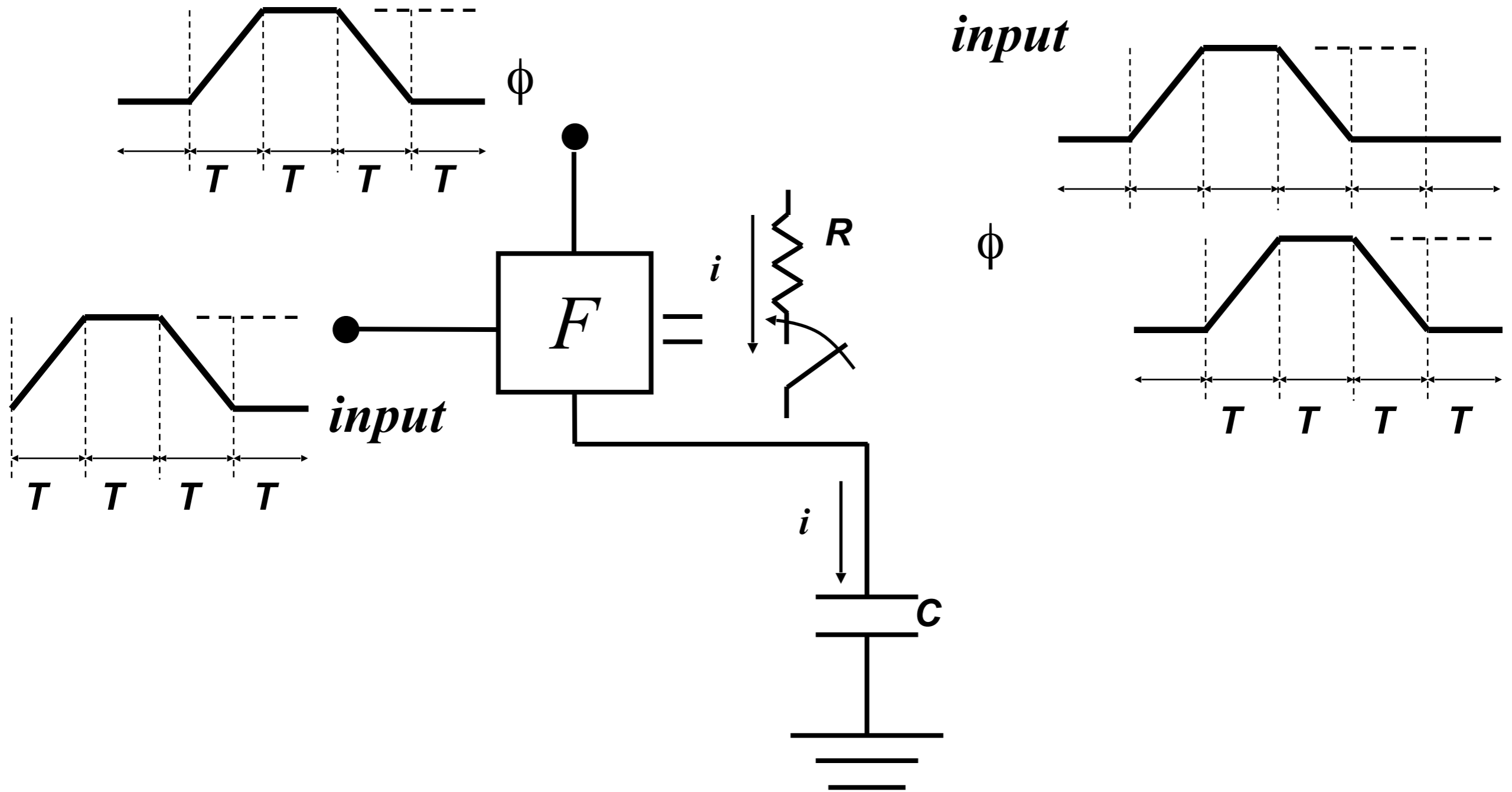


REMEMBER

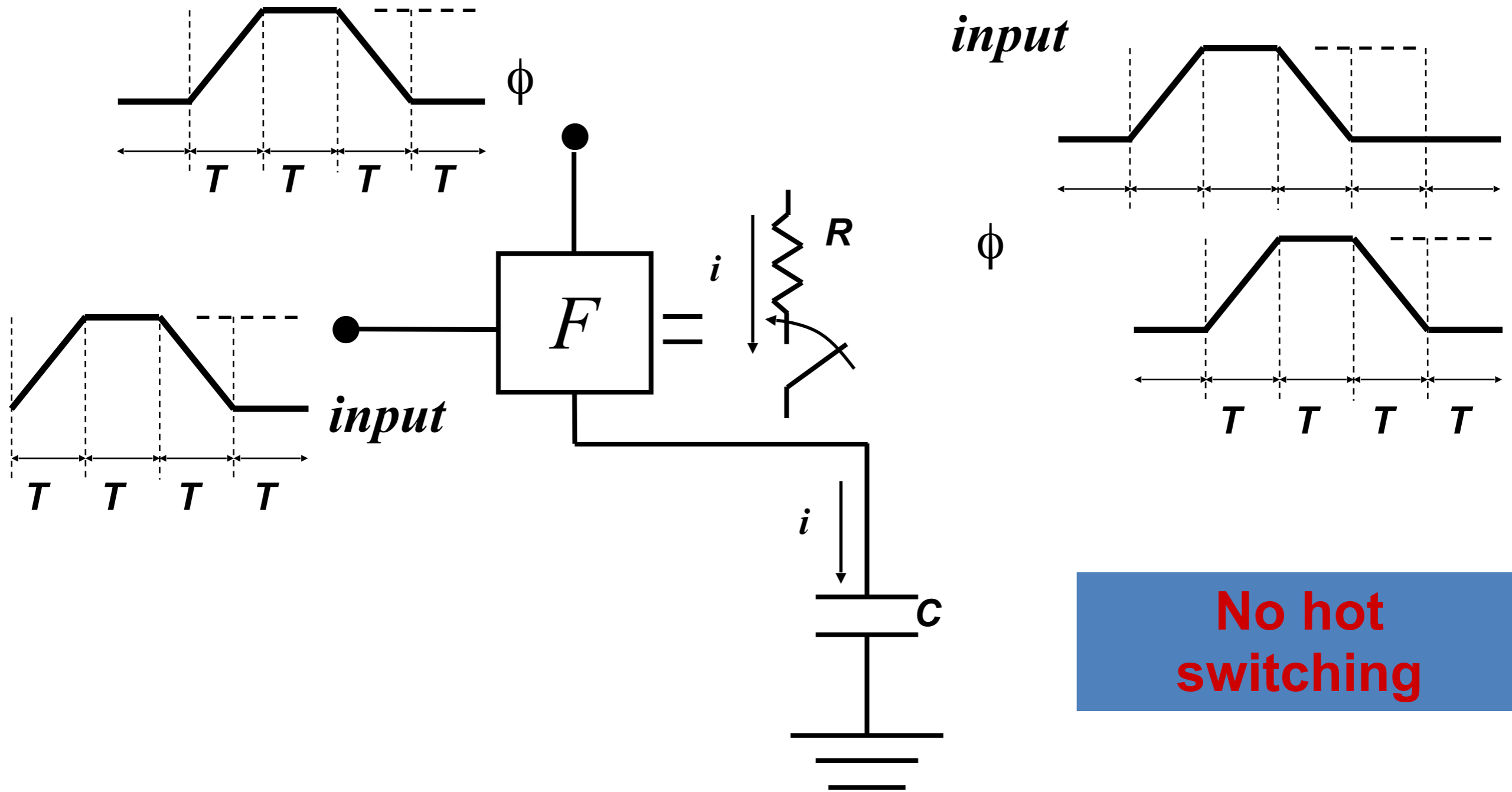
REMEMBER

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Adiabatic Logic



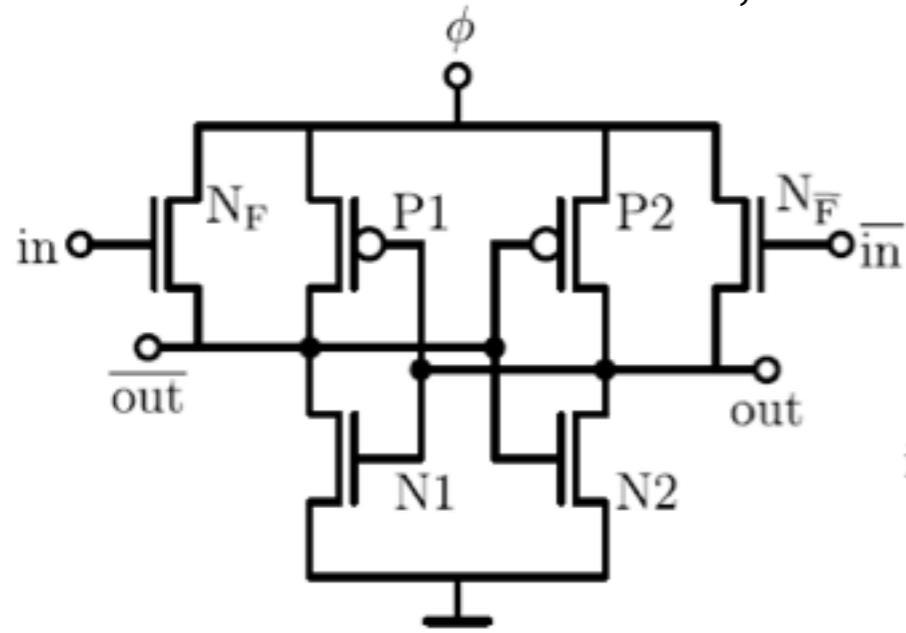
Adiabatic Logic



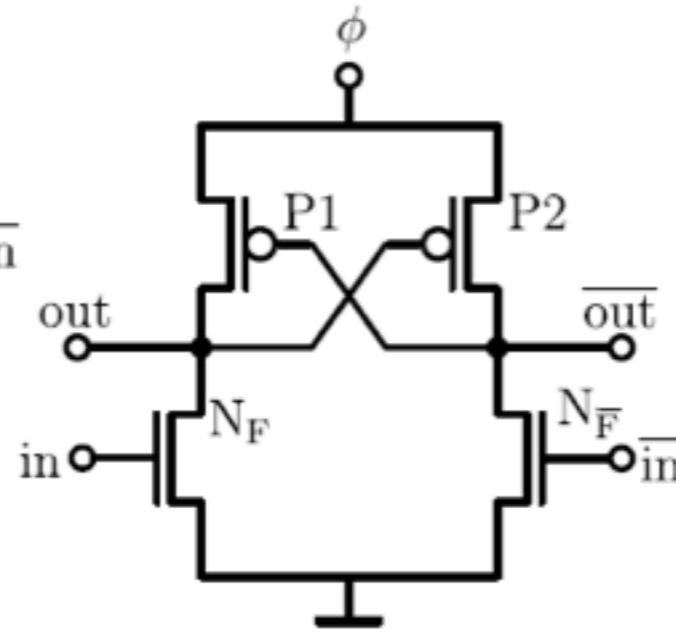
No hot switching

CMOS Adiabatic Logic

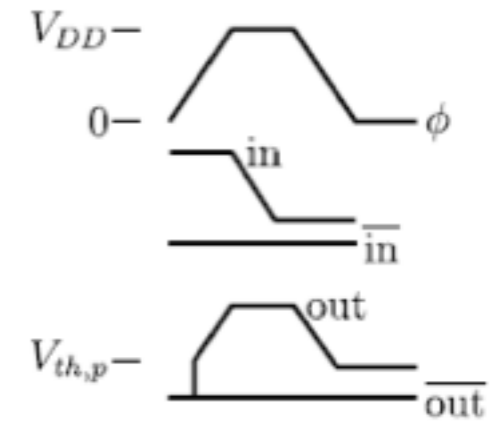
P. Teichmann, 2012



a)



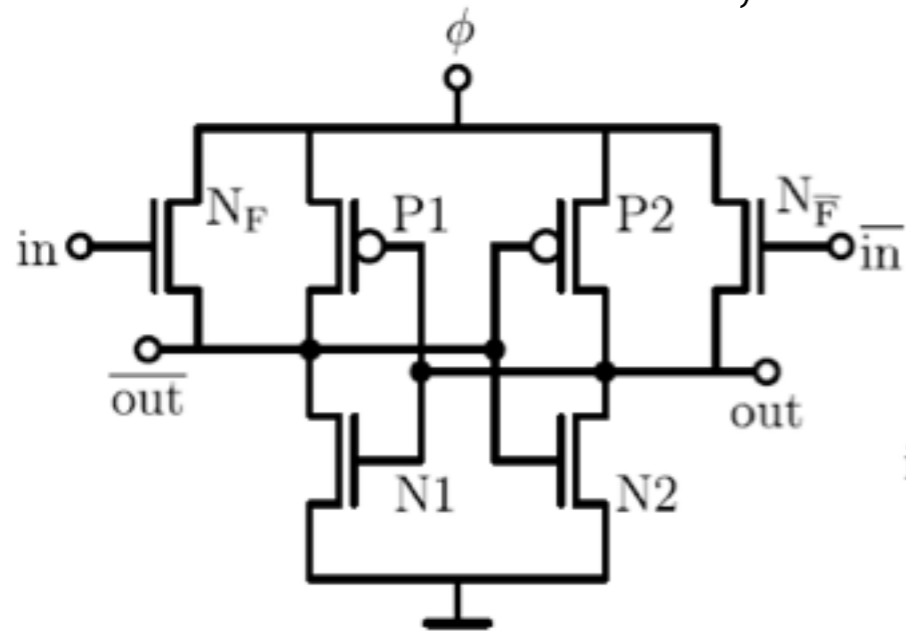
b)



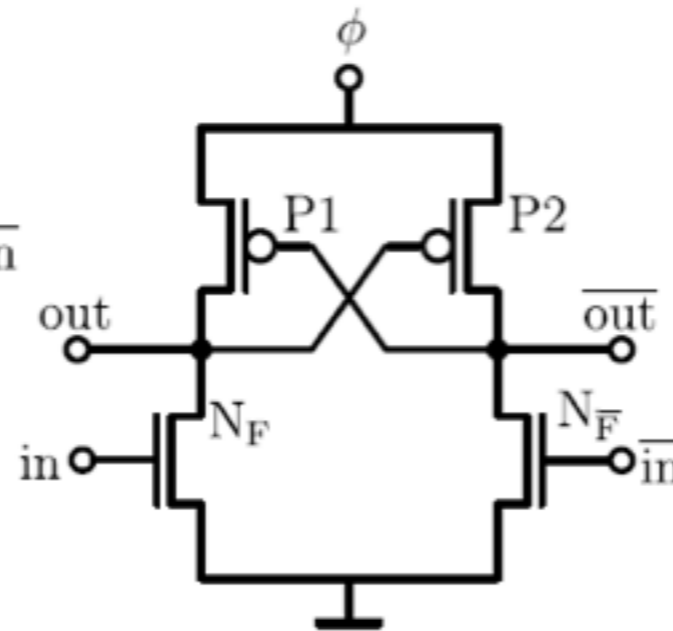
Inverter circuit in the (a) PFAL and (b) ECRL family

CMOS Adiabatic Logic

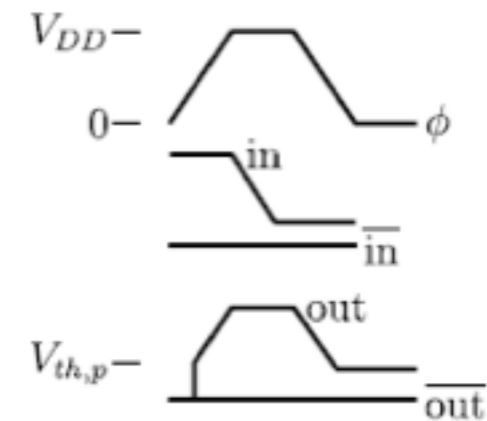
P. Teichmann, 2012



a)



b)



Inverter circuit in the (a) PFAL and (b) ECRL family

Adiabatic

Non-Adiabatic

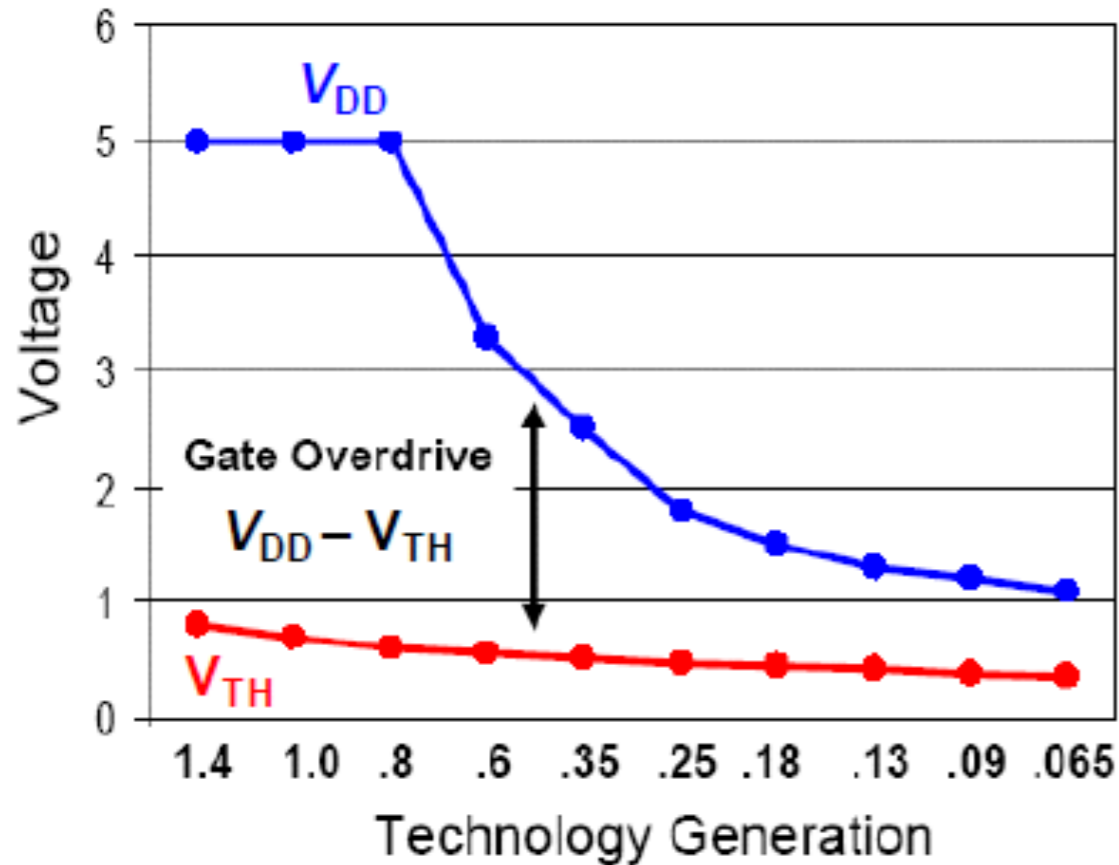
Static

$$E_{dissipated} \cong \frac{RC}{T} CV^2 + \frac{1}{2} CV_T^2 + I_{leakage} V_{dd} T$$

CMOS Adiabatic Logic

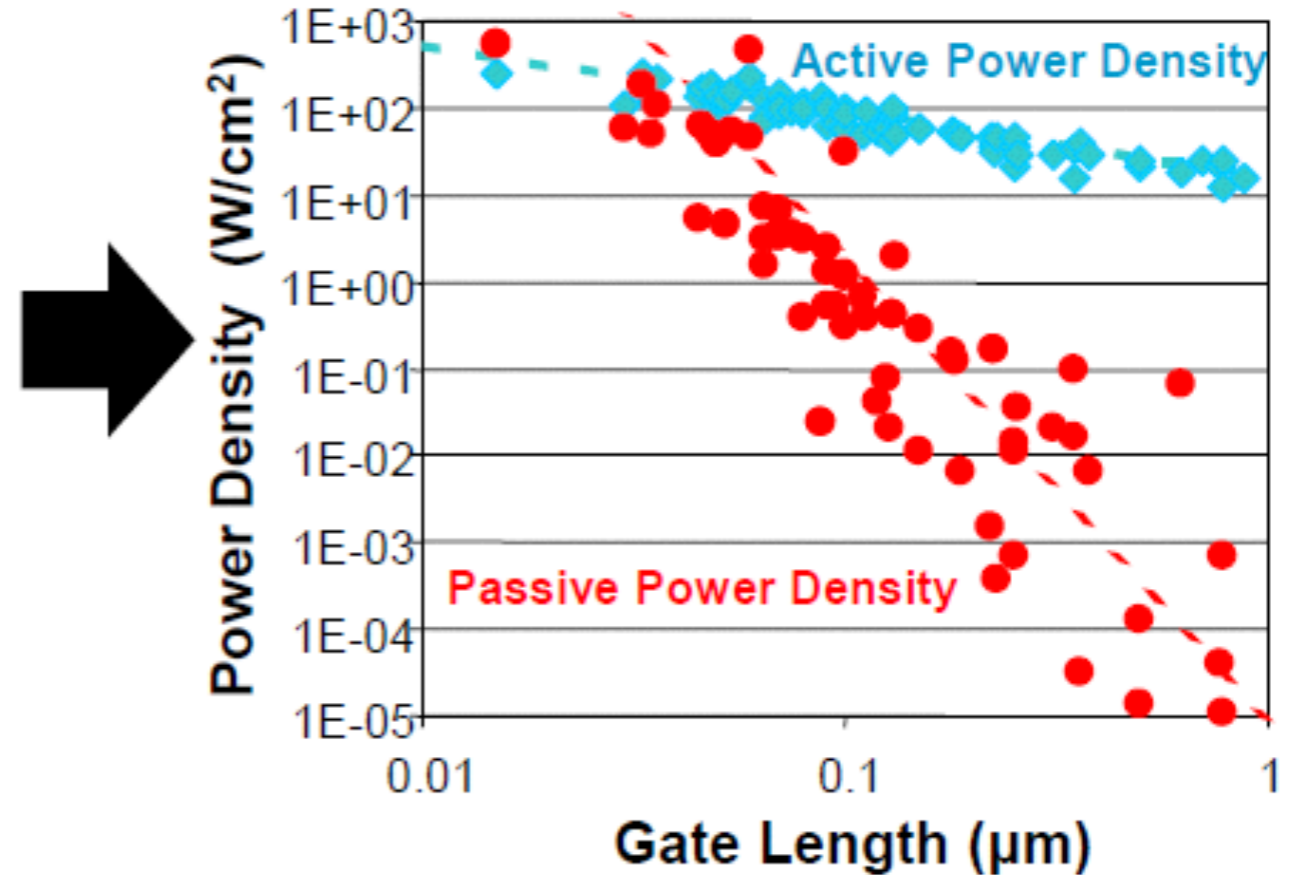
P. Teichmann, 2012

CMOS VOLTAGE SCALING



Source: P. Packan (Intel),
2007 IEDM Short Course

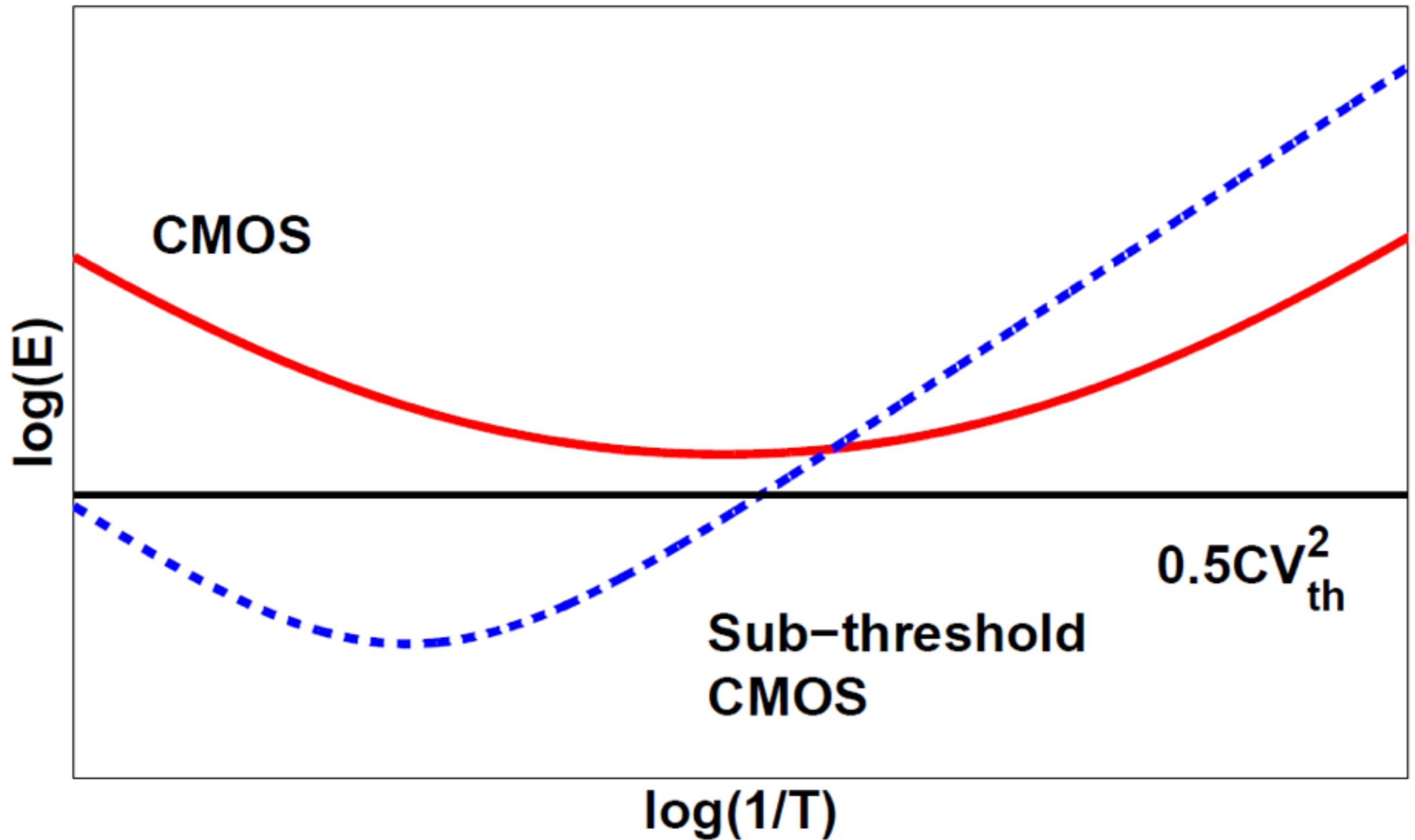
POWER DENSITY VS. GATE LENGTH



Source: B. Meyerson (IBM)
Semico Conf., January 2004

$$E_{dissipated} \cong \frac{1}{T} CV^2 + \frac{1}{2} CV_T^2 + I_{leakage} V_{dd} T$$

CMOS Adiabatic Logic



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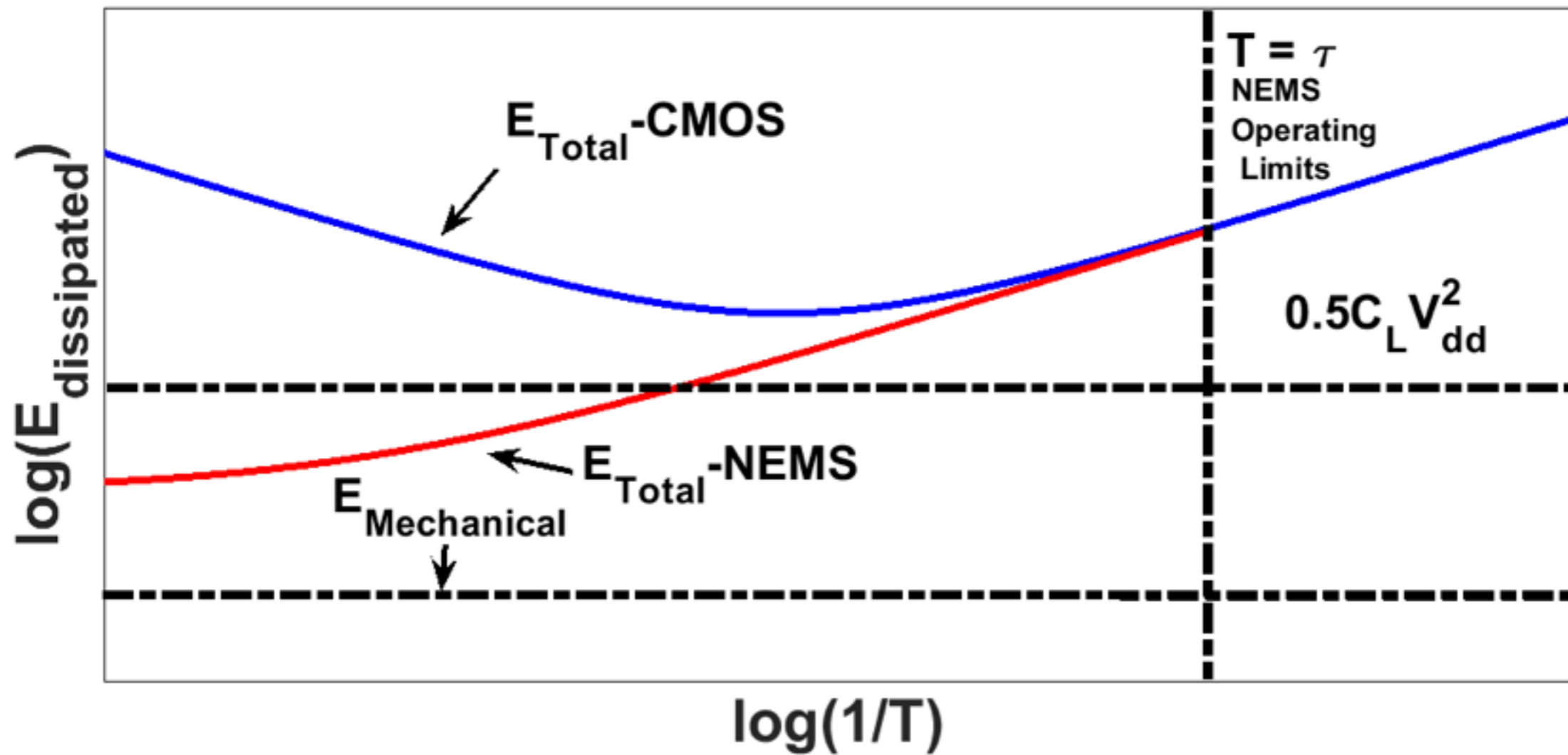
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3. Adiabatic circuit => Reduce losses associated with high voltage

4. NO LEAKAGE

NEMS Adiabatic Logic





Unconventional computing

Robust Soldier Crab Ball Gate

Yukio-Pegio Gunji

Yuta Nishiyama

Department of Earth and Planetary Sciences

Kobe University

Kobe 657-8501, Japan

Andrew Adamatzky

Unconventional Computing Centre

University of the West of England

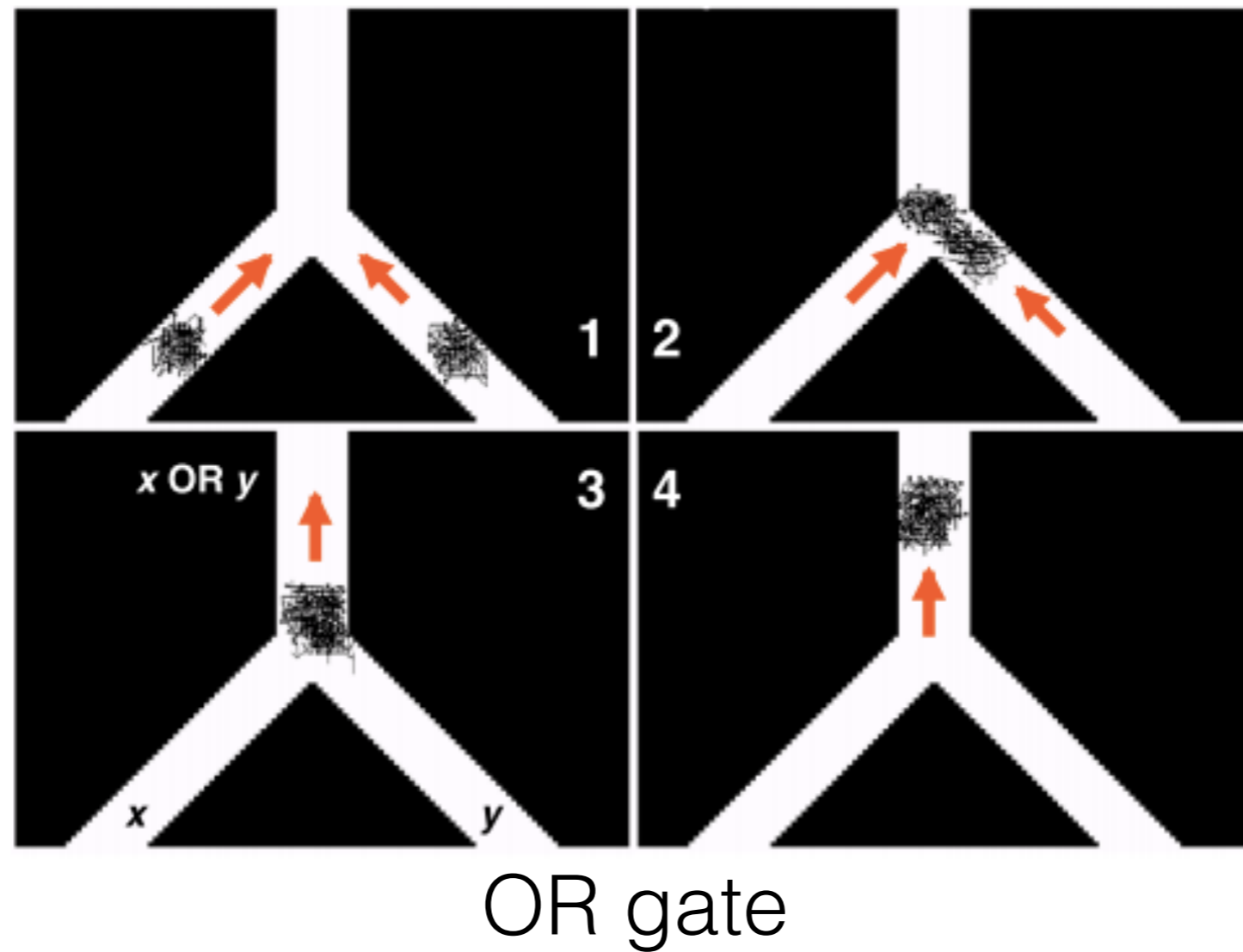
Bristol, United Kingdom

Soldier crabs *Mictyris guinotae* exhibit pronounced swarming behavior. Swarms of the crabs are tolerant of perturbations. In computer models and laboratory experiments we demonstrate that swarms of soldier crabs can implement logical gates when placed in a geometrically constrained environment.

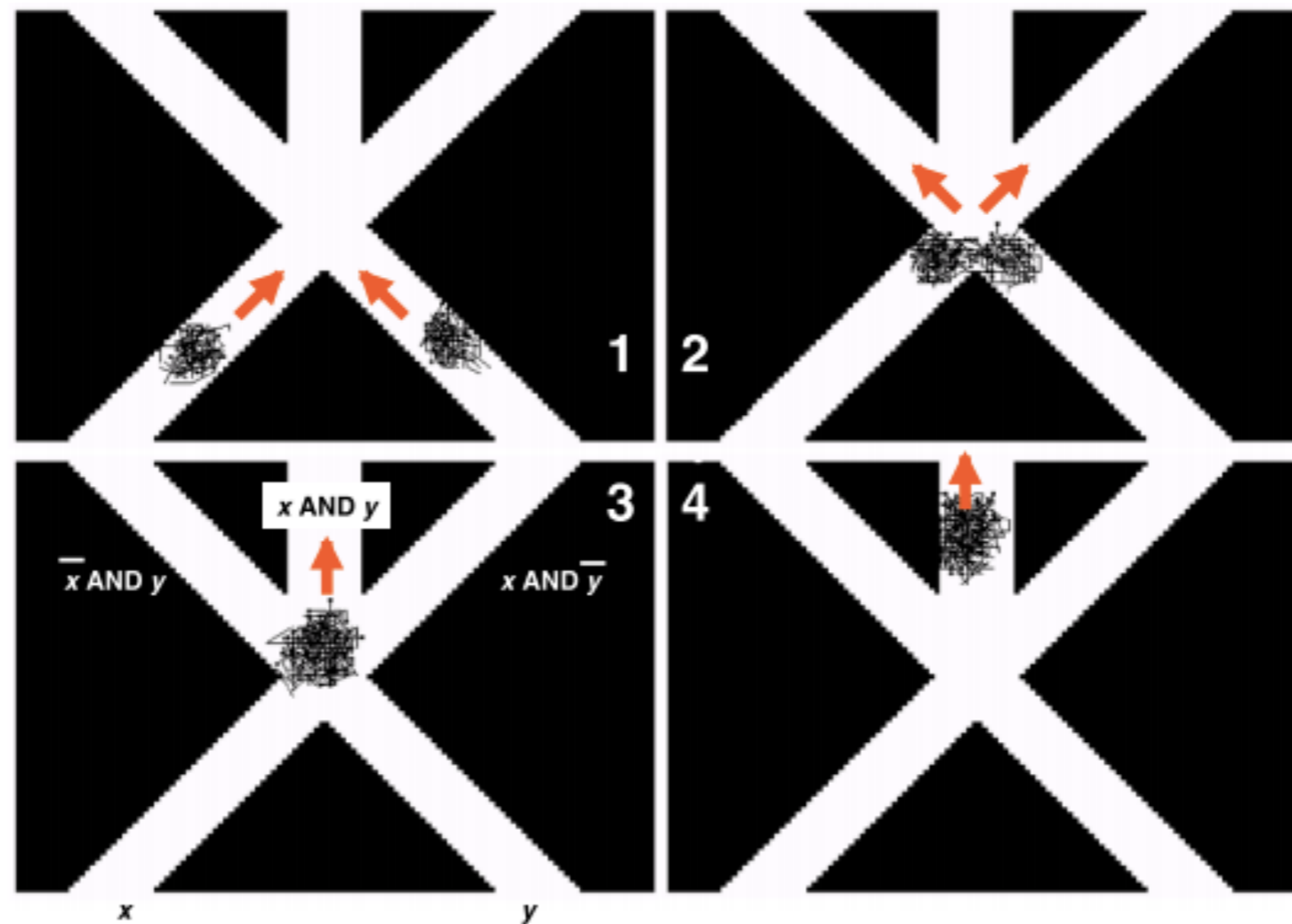
Robust Soldier Crab Ball Gate

Yukio-Pegio Gunji, Yuta Nishiyama, Andrew Adamatzky

Robust Soldier Crab Ball Gate

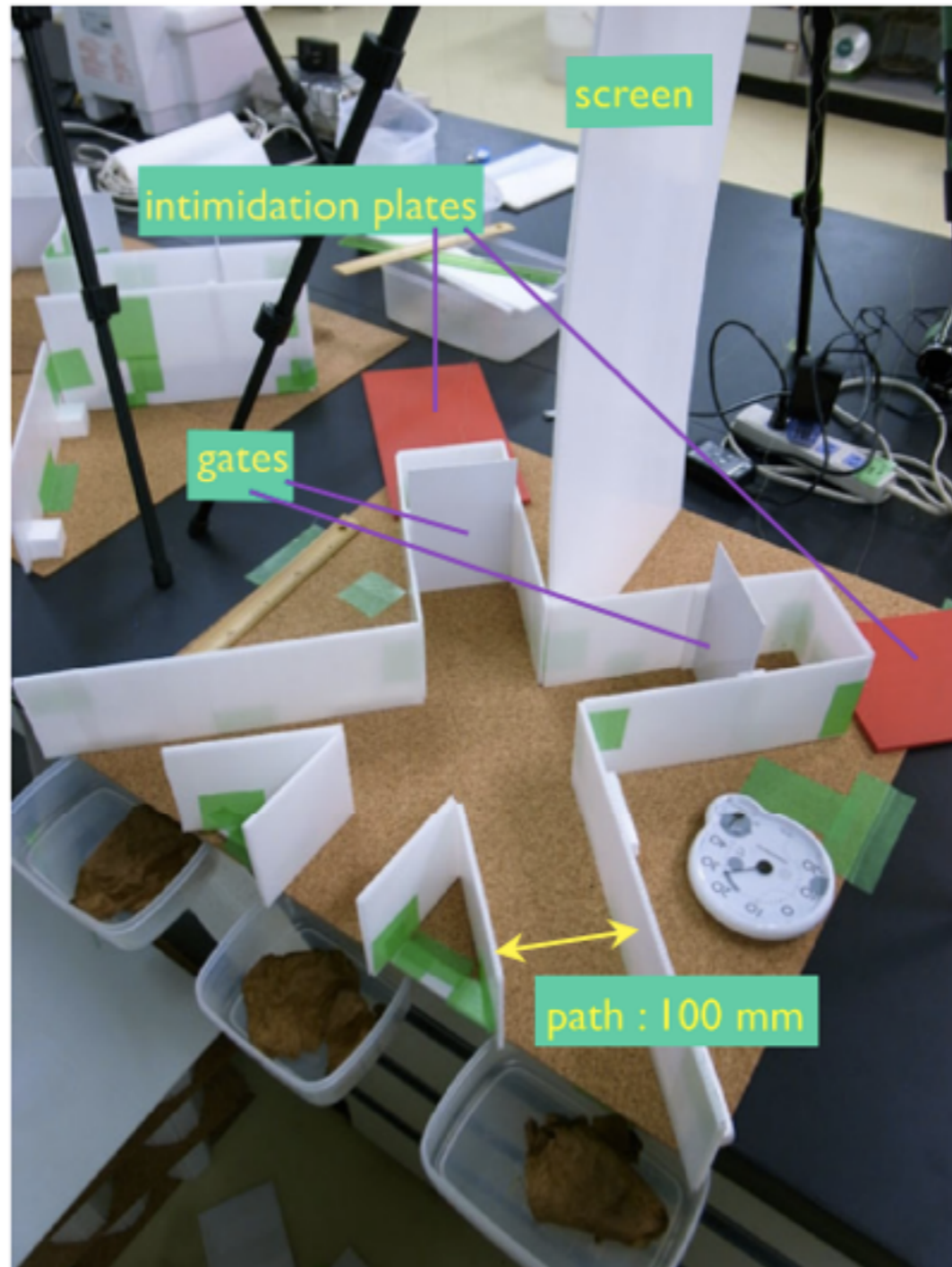


Robust Soldier Crab Ball Gate



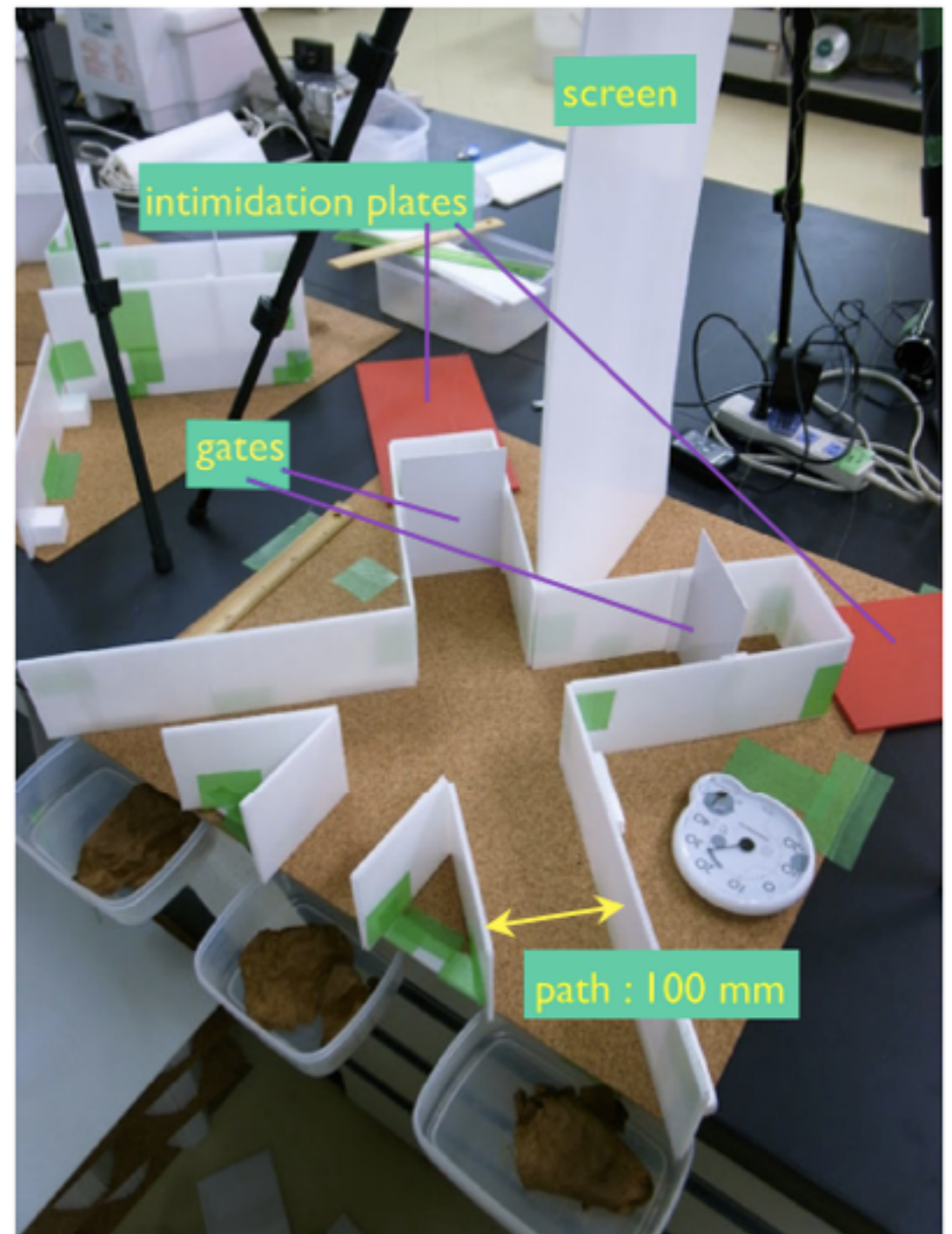
AND gate

Robust Soldier Crab Ball Gate



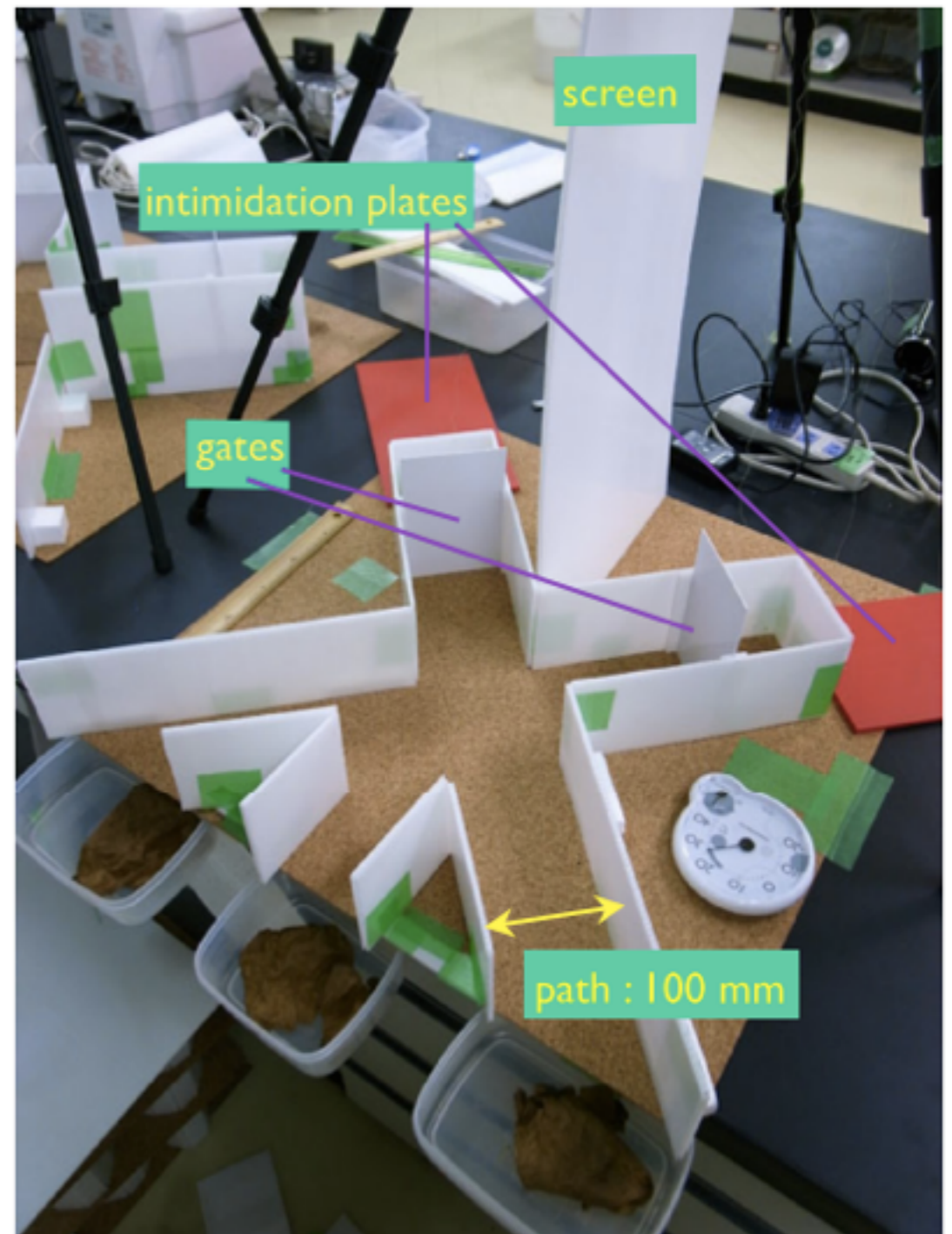
Robust Soldier Crab Ball Gate - Yukio-Pegio Gunji, Yuta Nishiyama, Andrew Adamatzky

Robust Soldier Crab Ball Gate



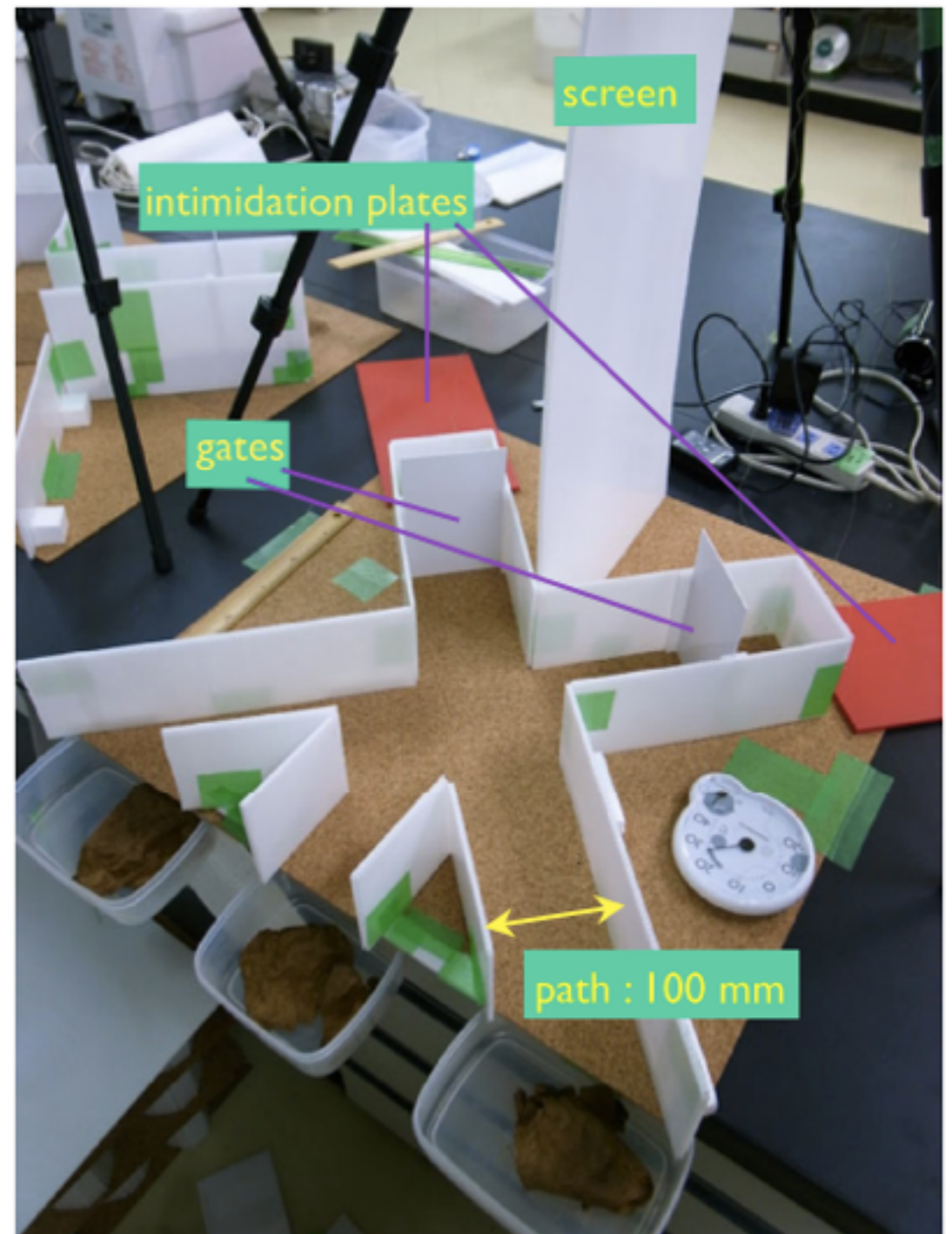
Robust Soldier Crab Ball Gate

- How much energy?



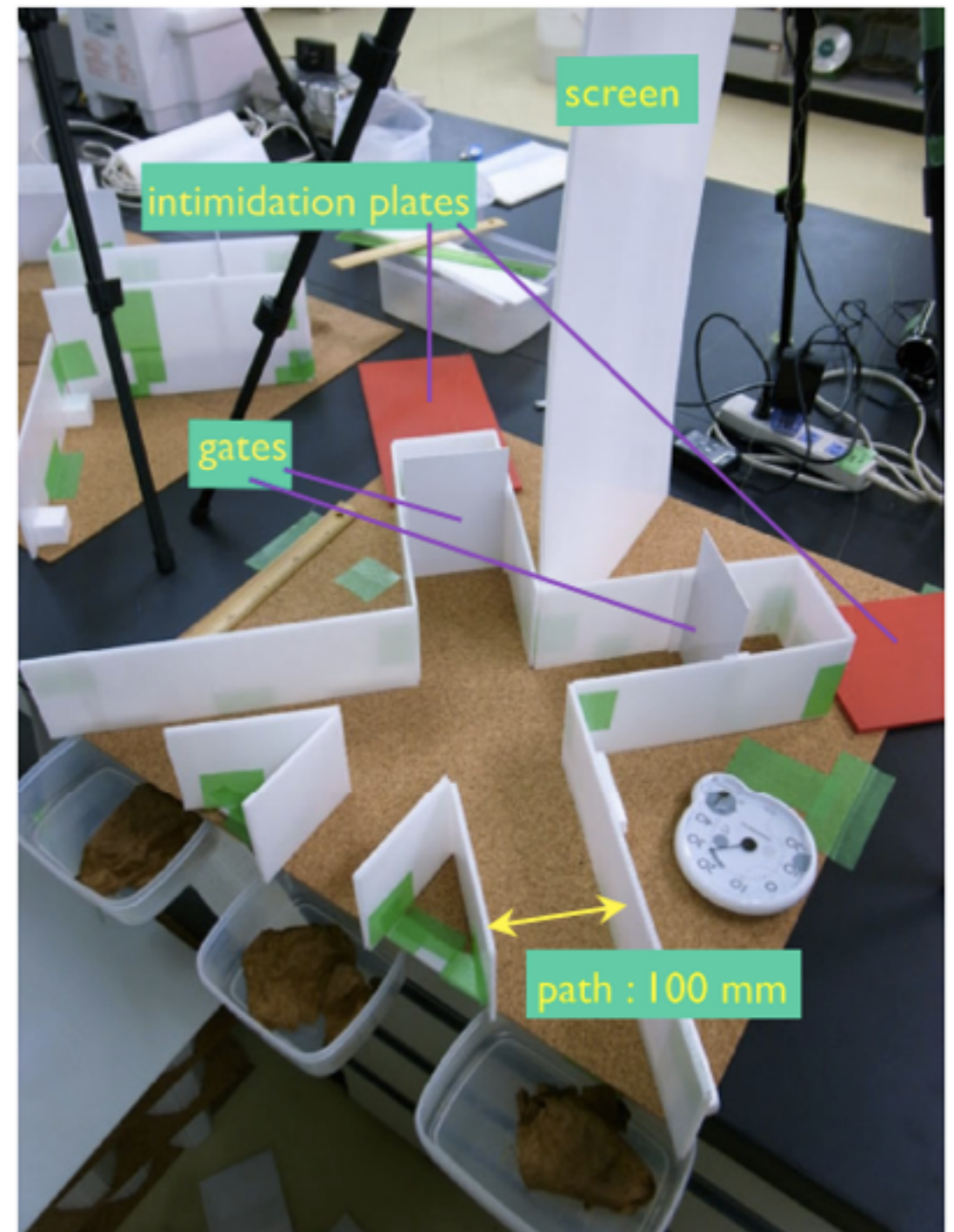
Robust Soldier Crab Ball Gate

- How much energy?
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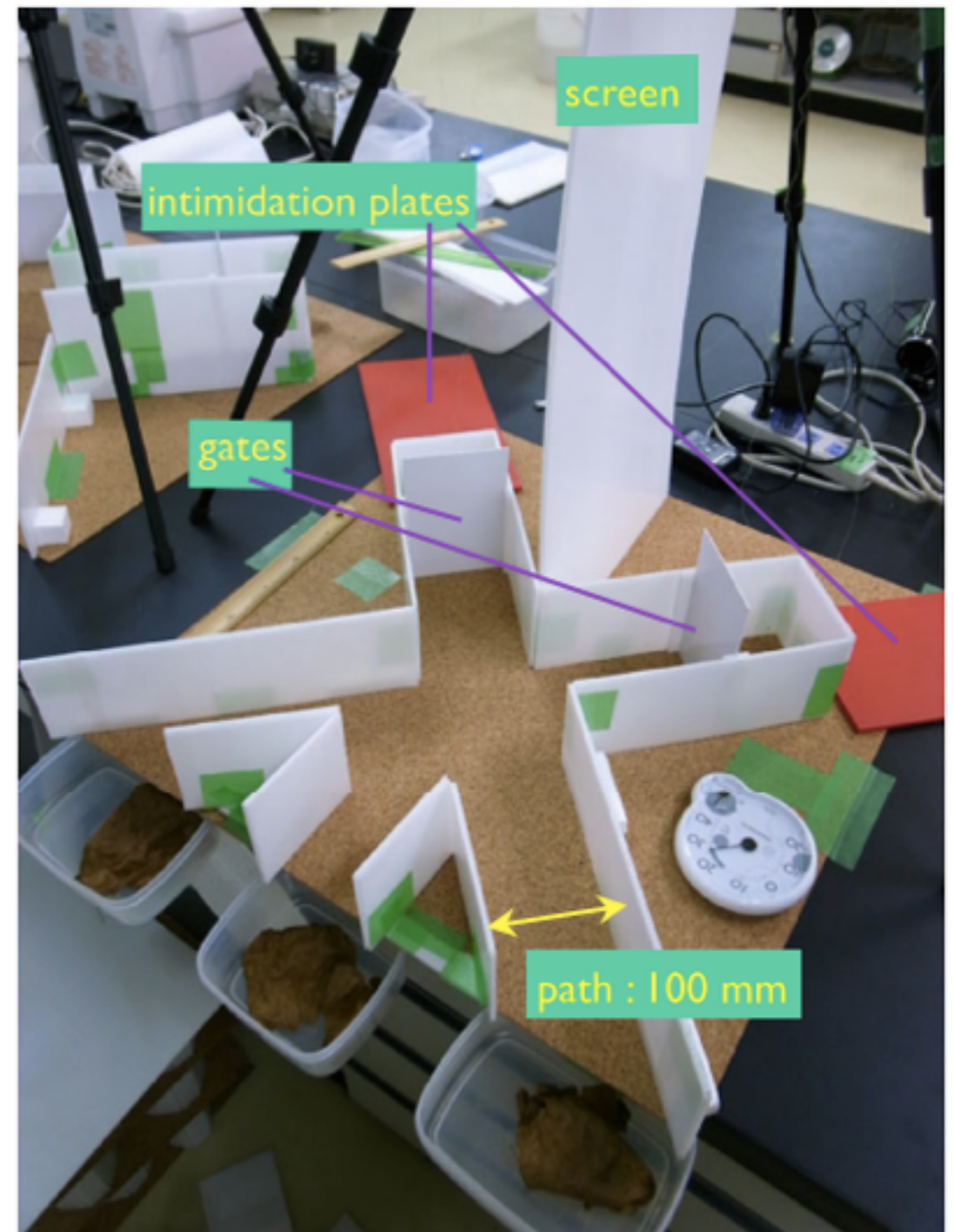
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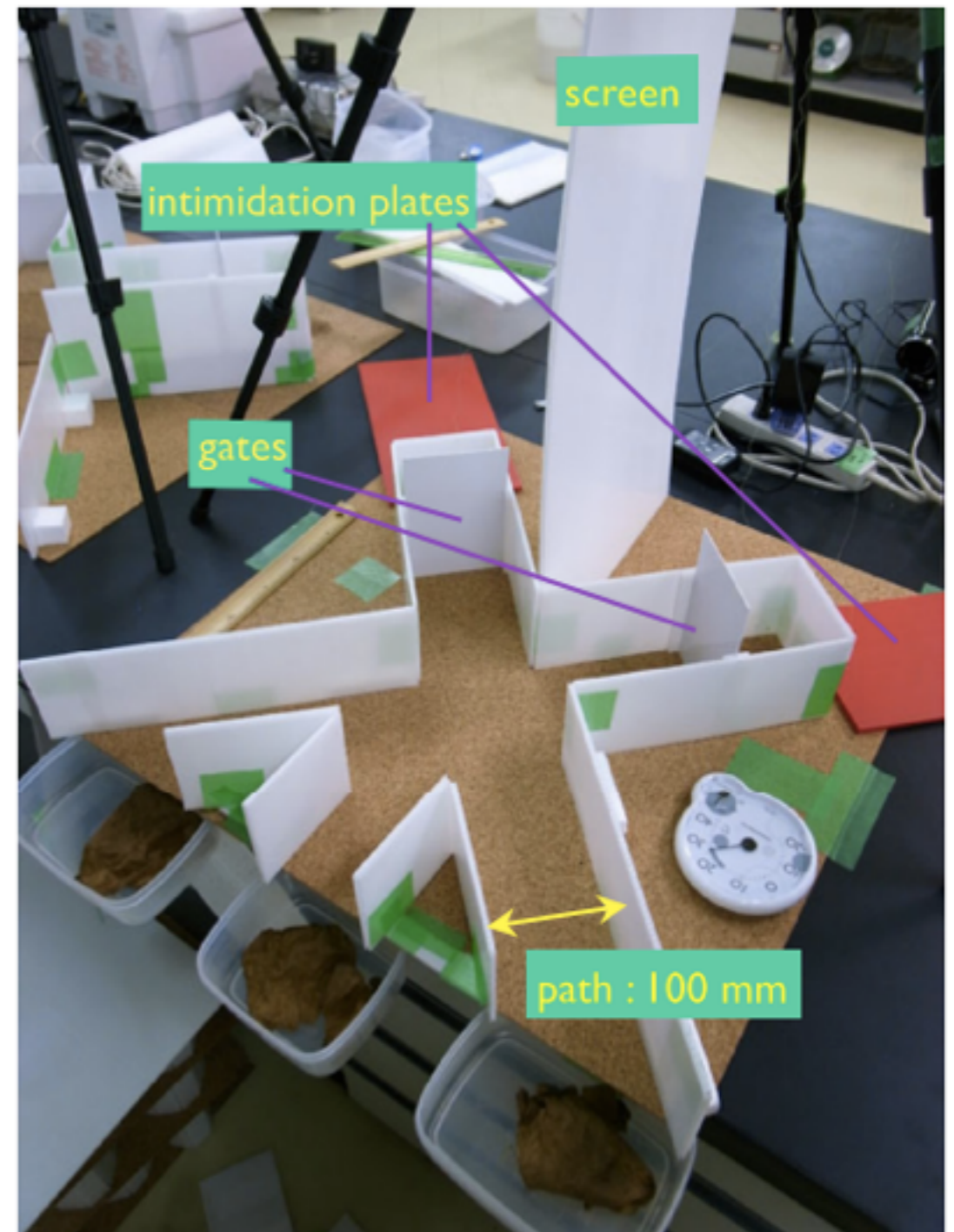
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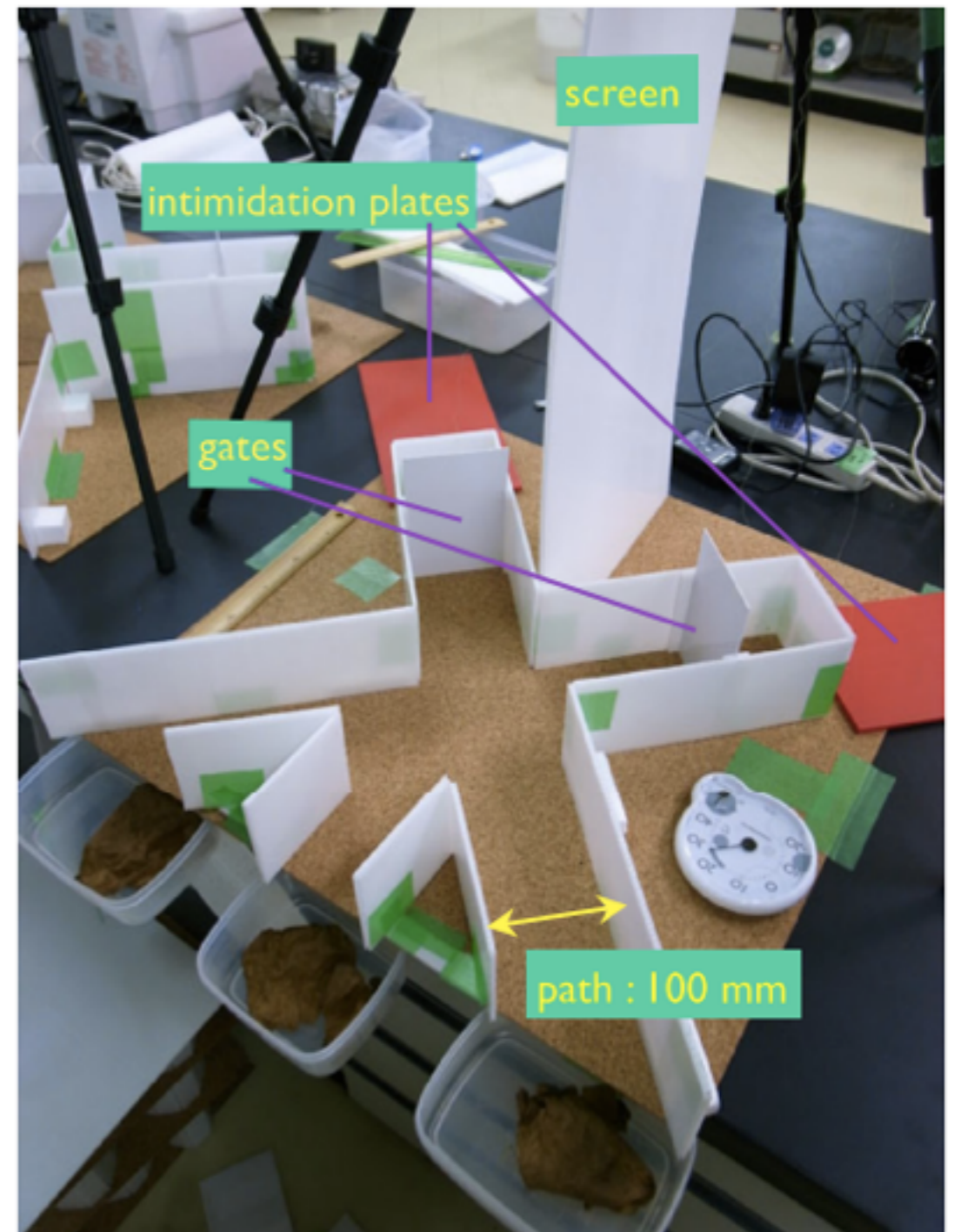
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- Suppose daily need is 50% of its weight: 21g of algae and thus 35kcal



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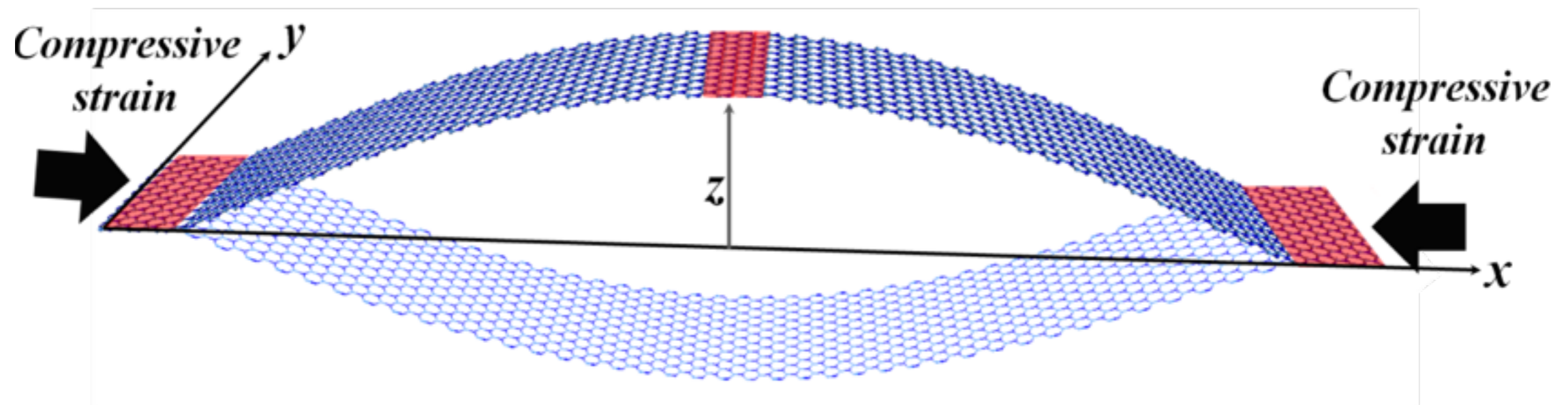
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- Average weight of the crabs was 42g
- Suppose daily need is 50% of its weight: 21g of algae and thus 35kcal
- 146440J of energy for daily operating a crab logic gate or 1.7W of power



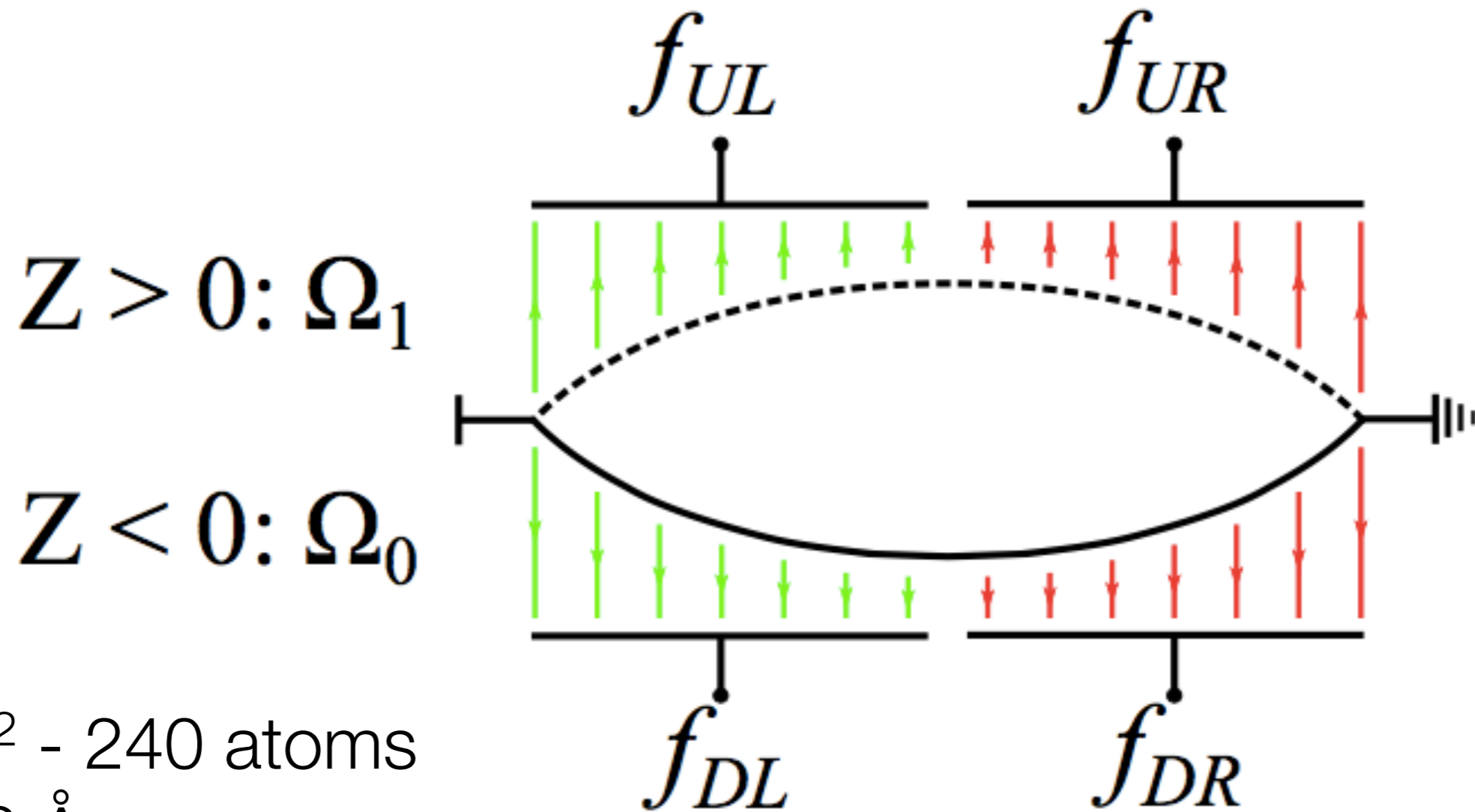
What about the memory?



NEMS system



NEMS system



$6 \times 1 \text{ nm}^2$ - 240 atoms

$a = 2.42 \text{ \AA}$

$Y = 0.85 \text{ TPa}$

$T = 10 \text{ K}$

Heat production evaluation

$$H(\mathbf{P}, \mathbf{R}, t) = H_{kin}(\mathbf{P}) + H_{int}(\mathbf{R}) + H_{ext}(\mathbf{R}, t)$$

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$$H_{ext}(\mathbf{R}, t) = \sum_{i=1}^n \left[\theta \left(x_i - \frac{l}{2} \right) \left(\frac{f_{UL}(t)}{(g - z_i)} - \frac{f_{DL}(t)}{(g + z_i)} \right) + \right. \\ \left. + \theta \left(\frac{l}{2} - x_i \right) \left(\frac{f_{UR}(t)}{(g - z_i)} - \frac{f_{DR}(t)}{(g + z_i)} \right) \right]$$

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$$W = \left\langle \int_{t_0}^{t_{end}} \frac{\partial H_{ext}(\mathbf{R}, t)}{\partial t} dt \right\rangle$$

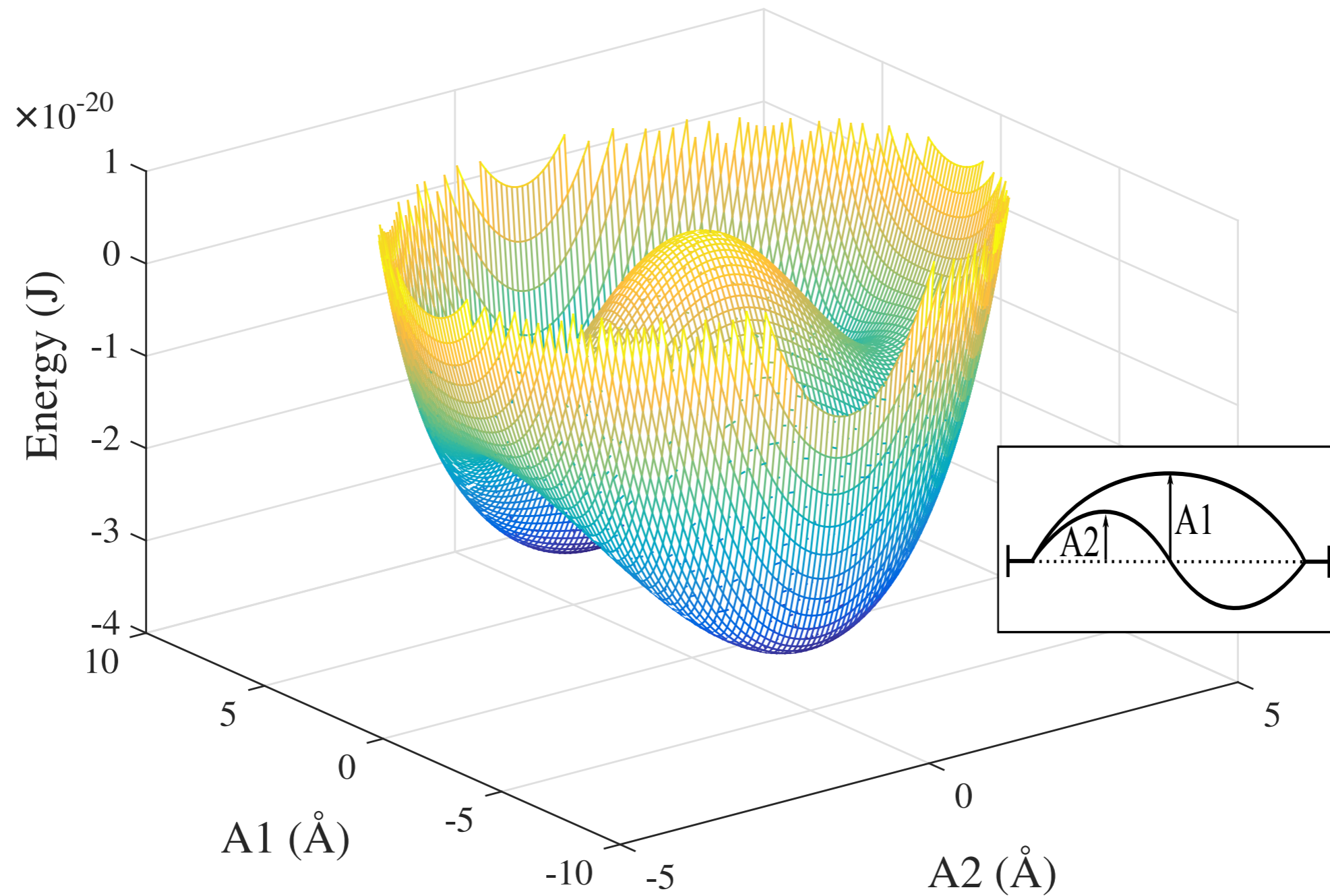
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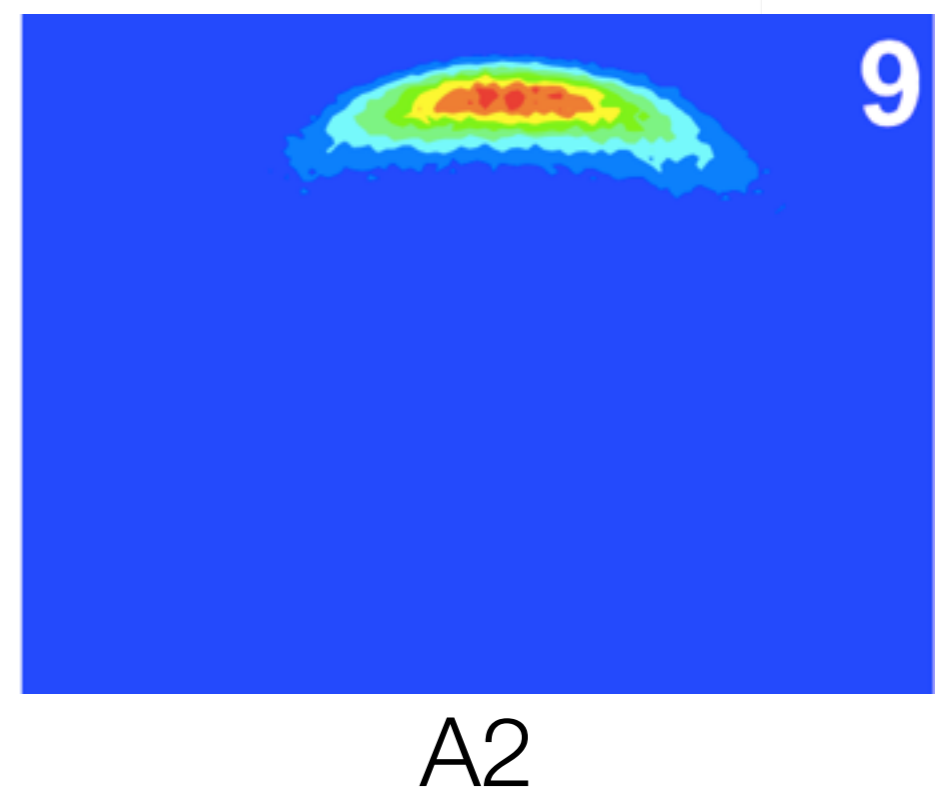
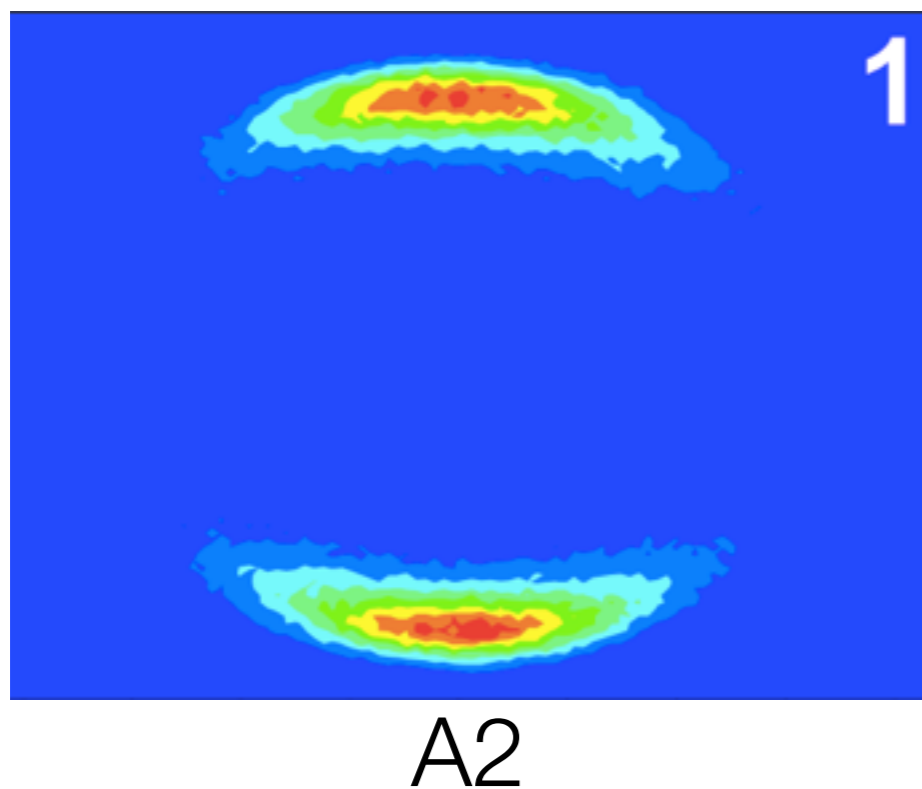
$$W = \left\langle \int_{t_0}^{t_{end}} \frac{\partial H_{ext}(\mathbf{R}, t)}{\partial t} dt \right\rangle \quad \Delta H = 0 \quad Q = W$$

2-DOF potential landscape



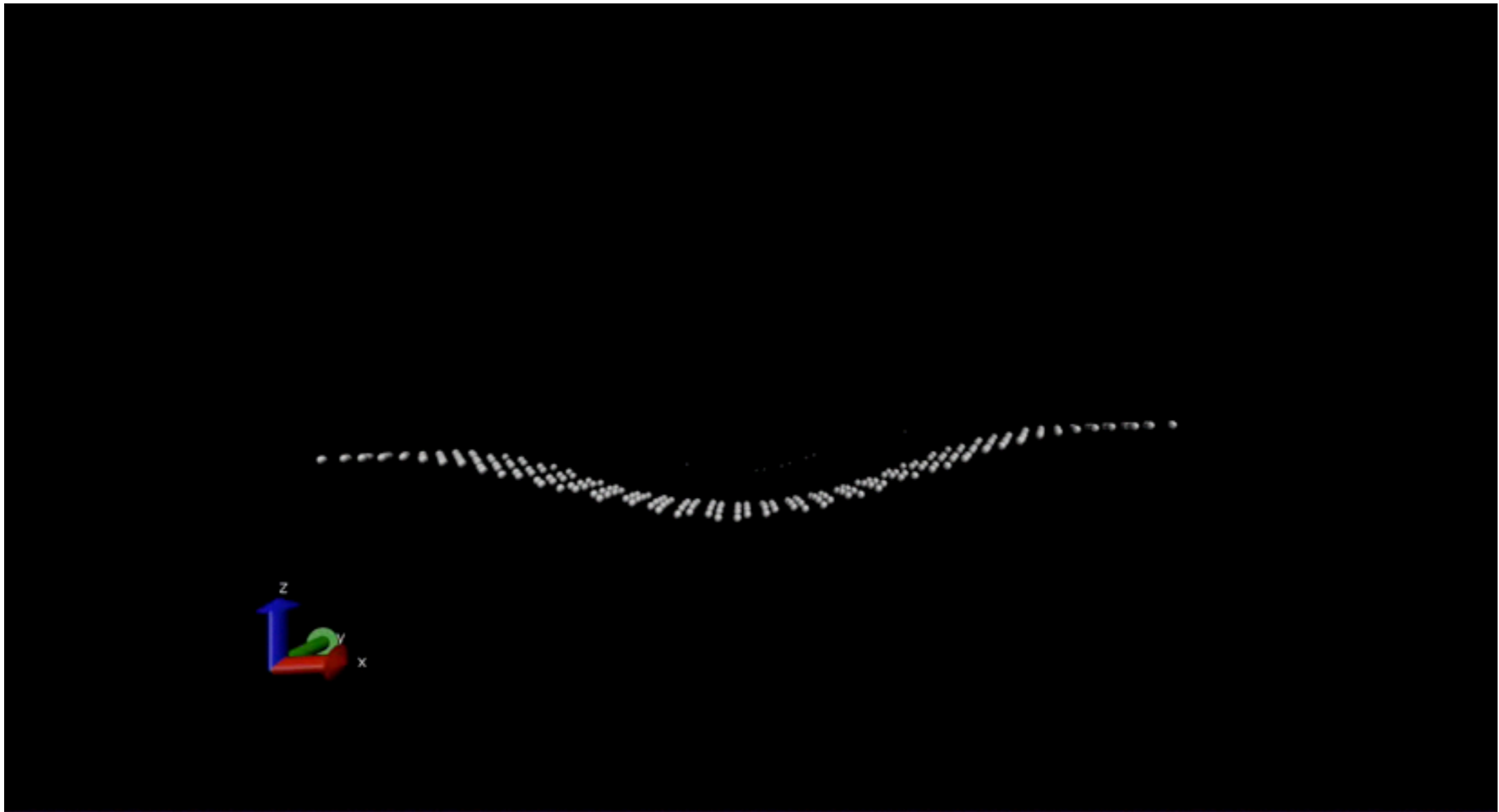
Reset protocol

- Objective: move the system from an unknown state to known state
- $\Delta S = k_B \log(2)$
- $Q_{\min} = k_B T \log(2)$



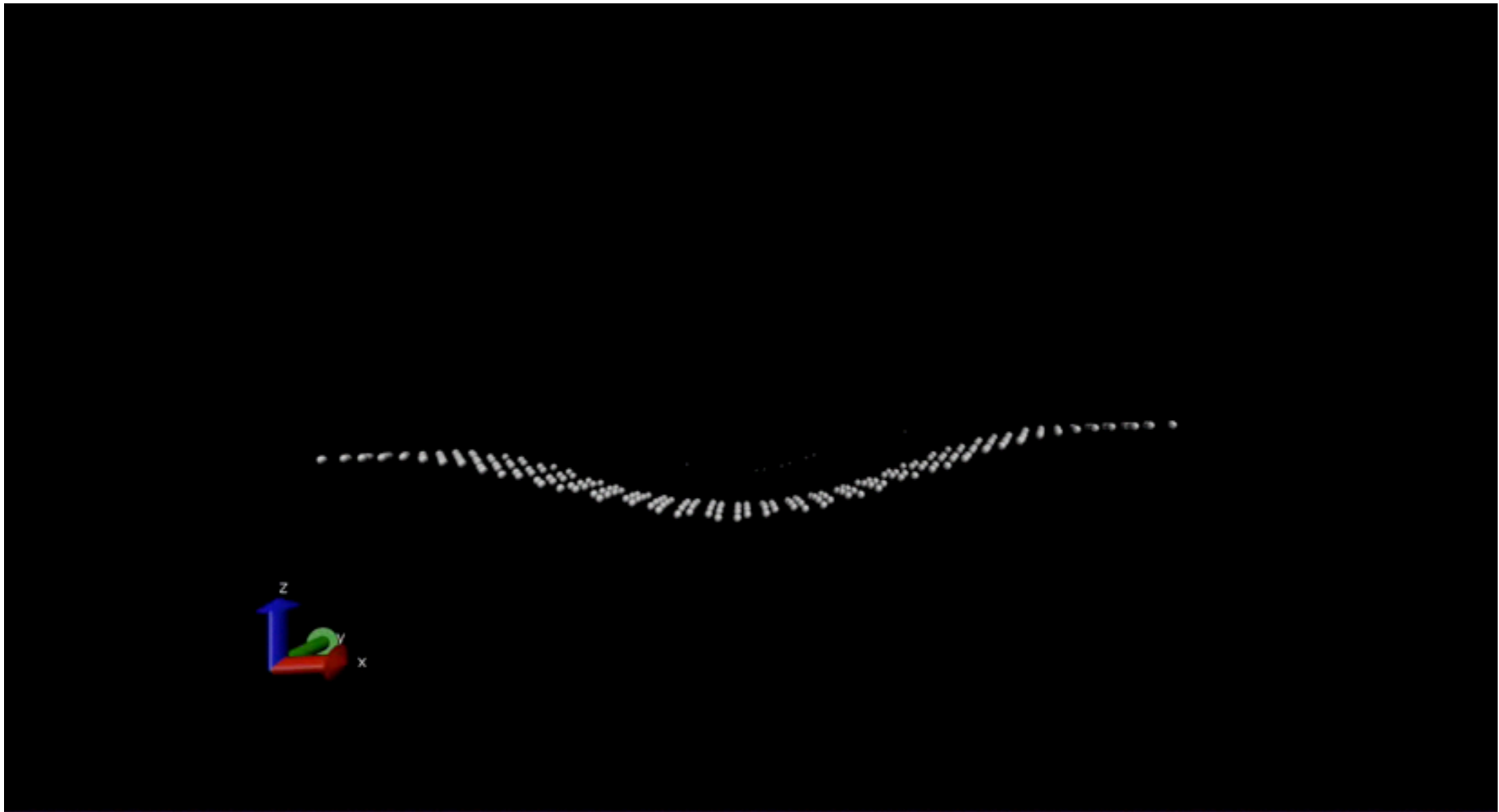
Reset protocol

Quick and dirty: apply a positive force along Z on all atoms



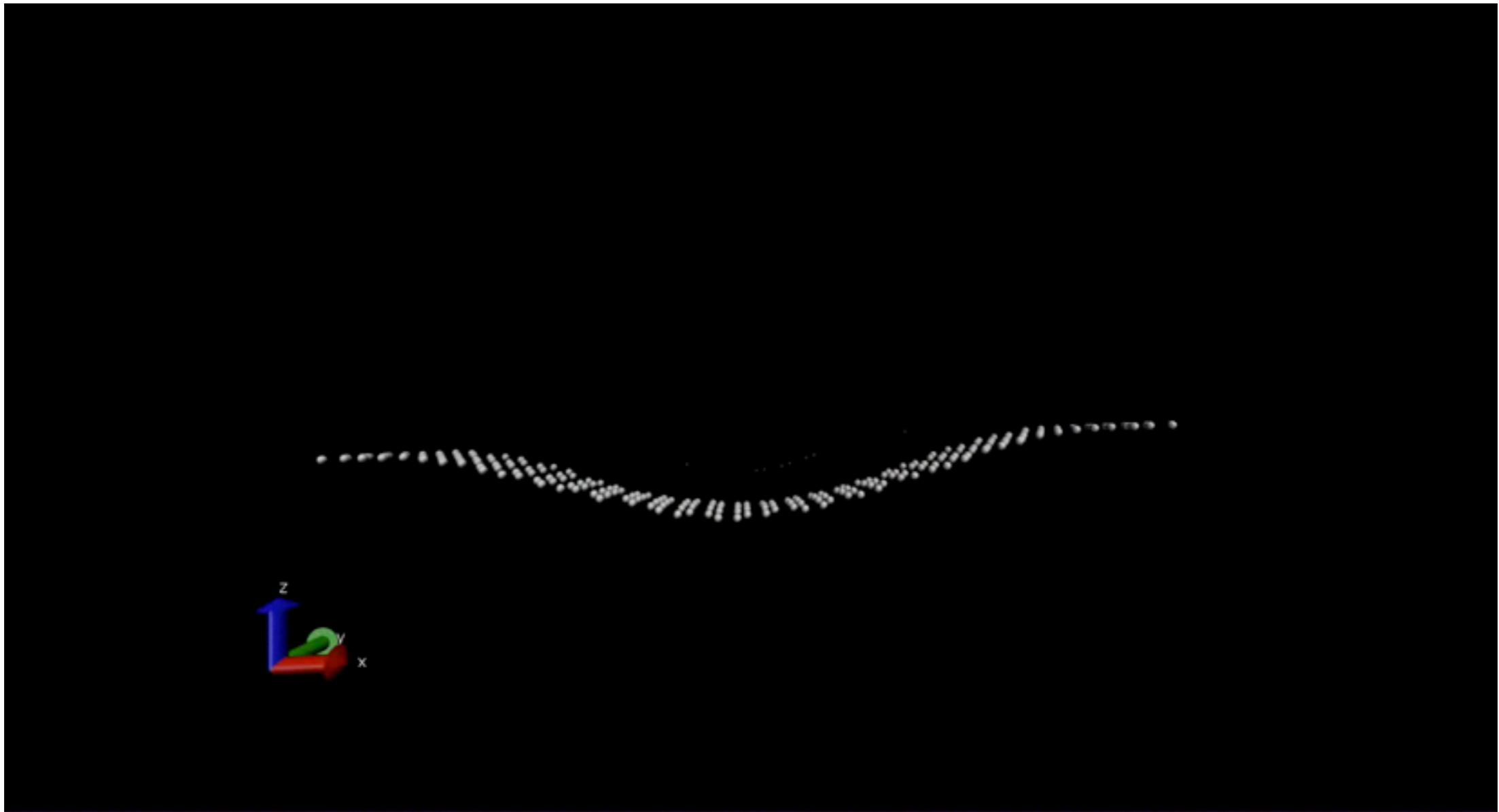
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Reset protocol

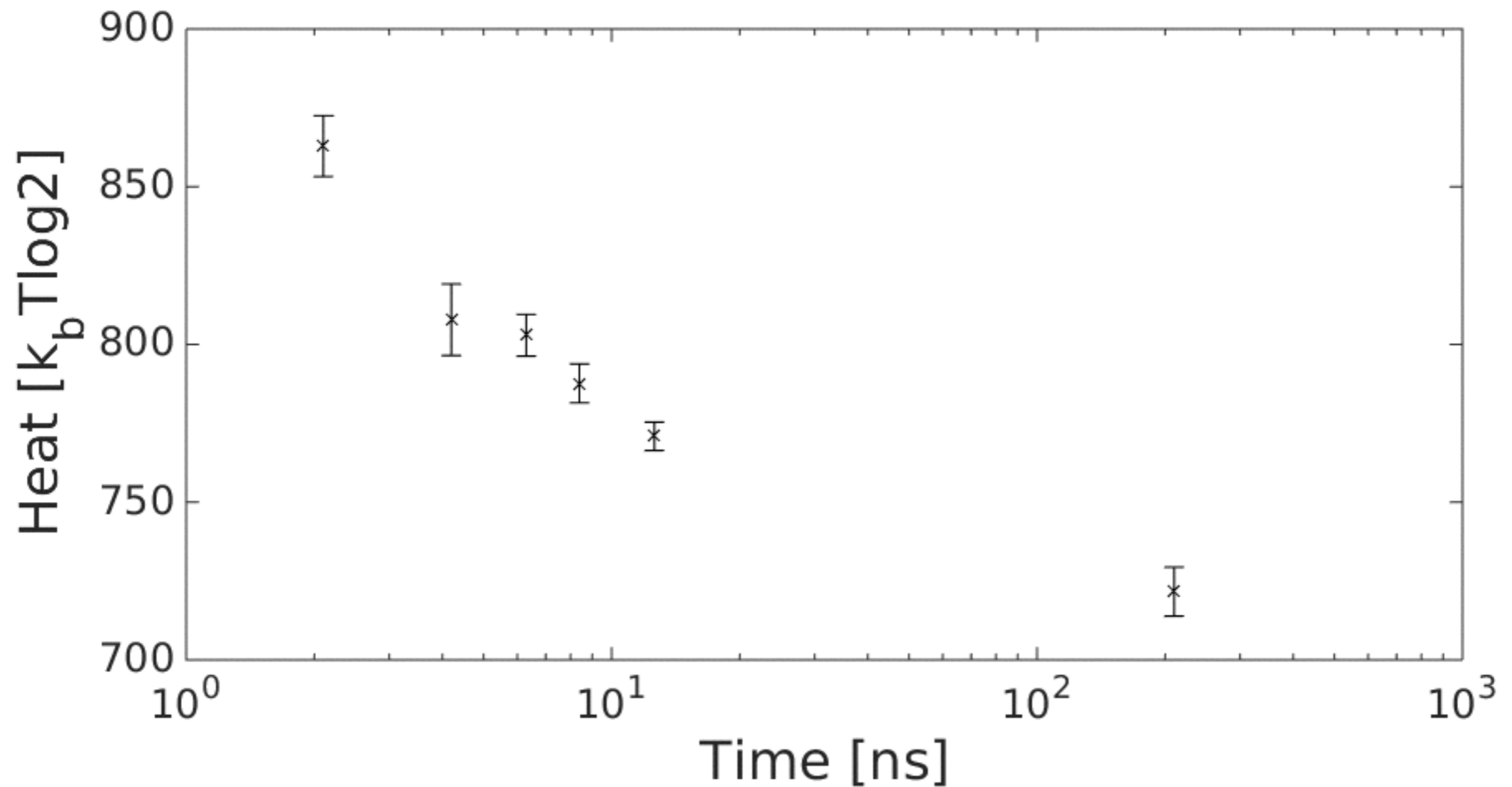
Quick and dirty: apply a positive force along Z on all atoms



WRONG: it is not possible to control the velocity!

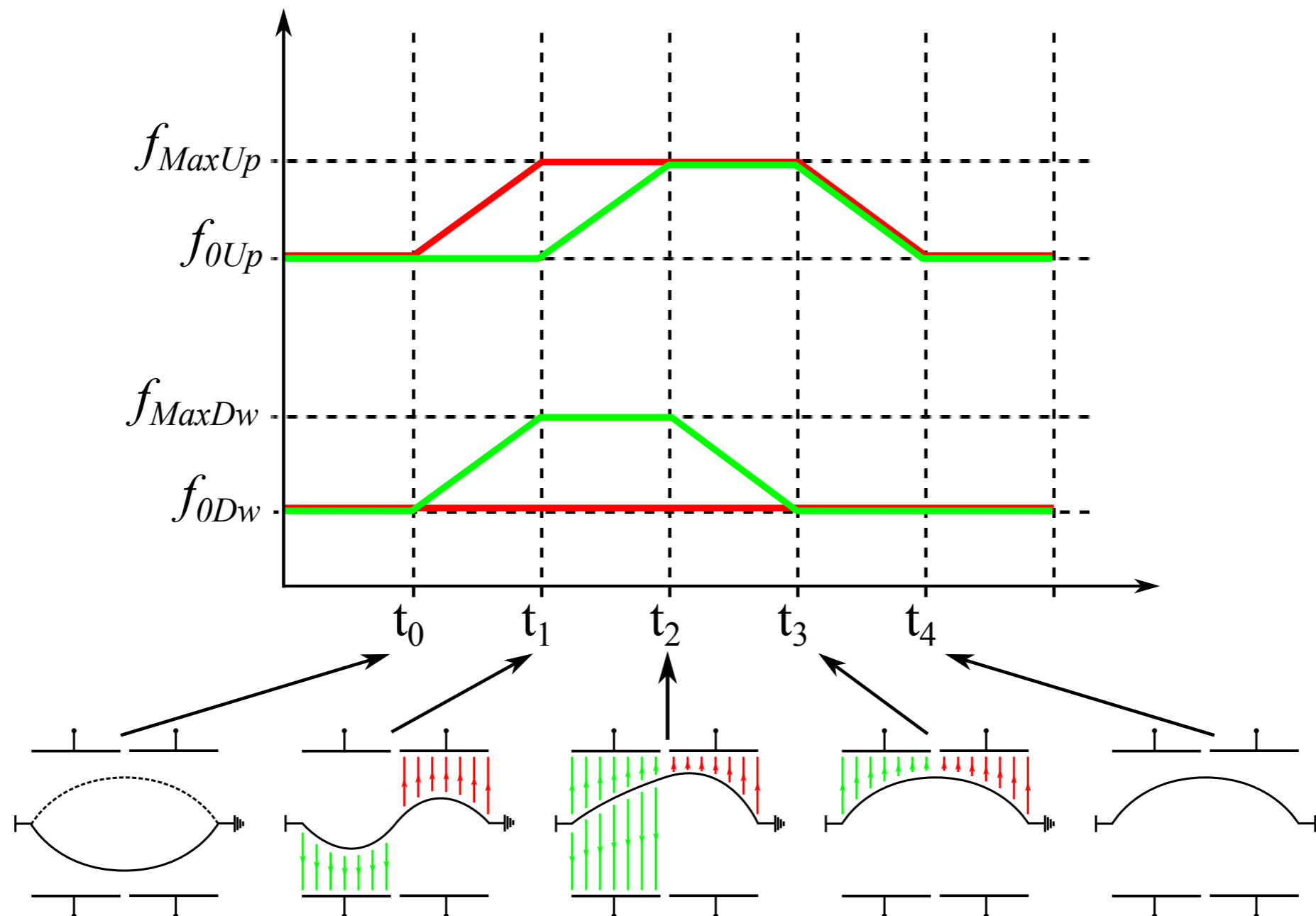
Reset protocol

Quick and dirty: apply a positive force along Z on all atoms



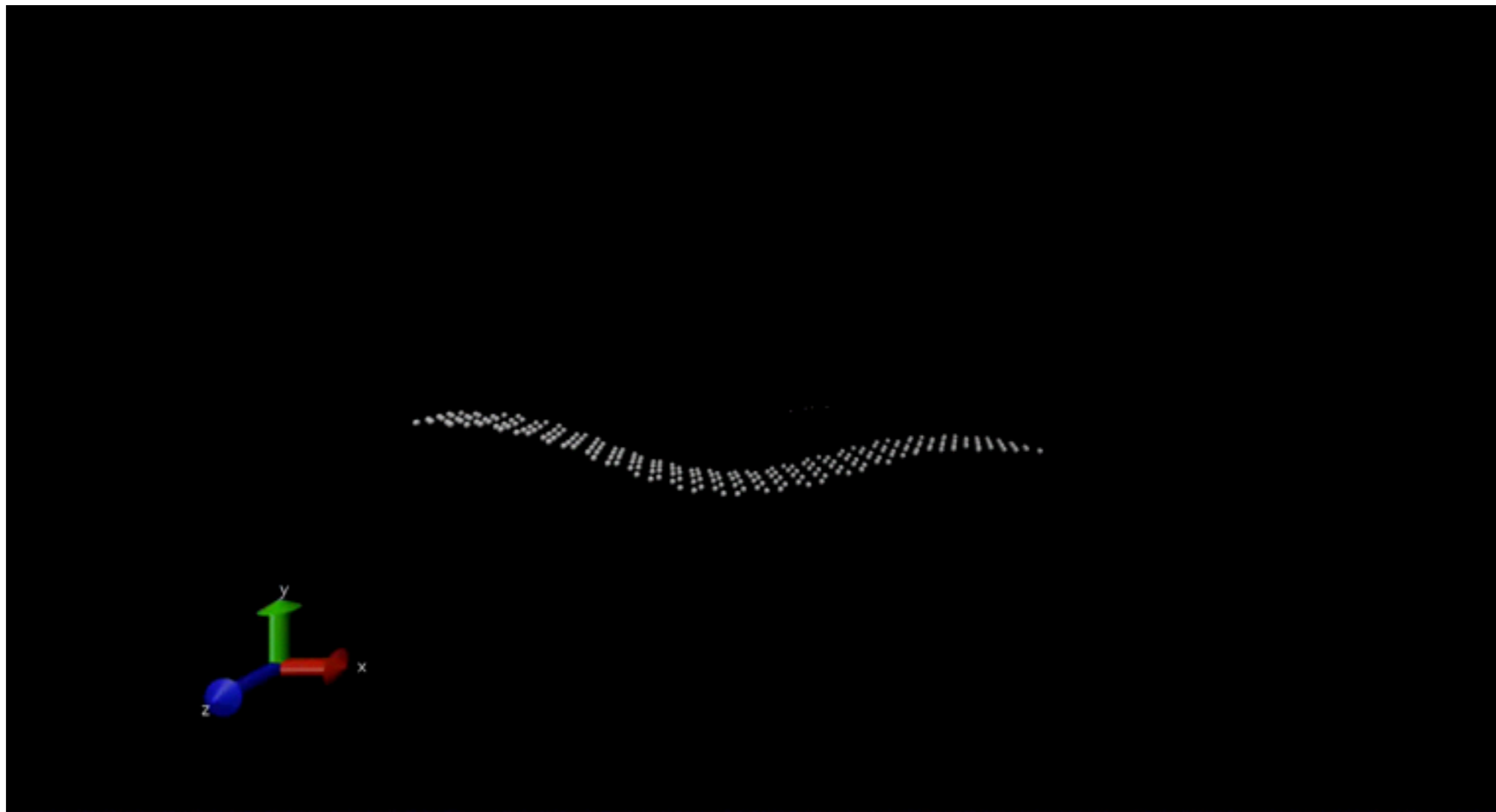
Reset protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



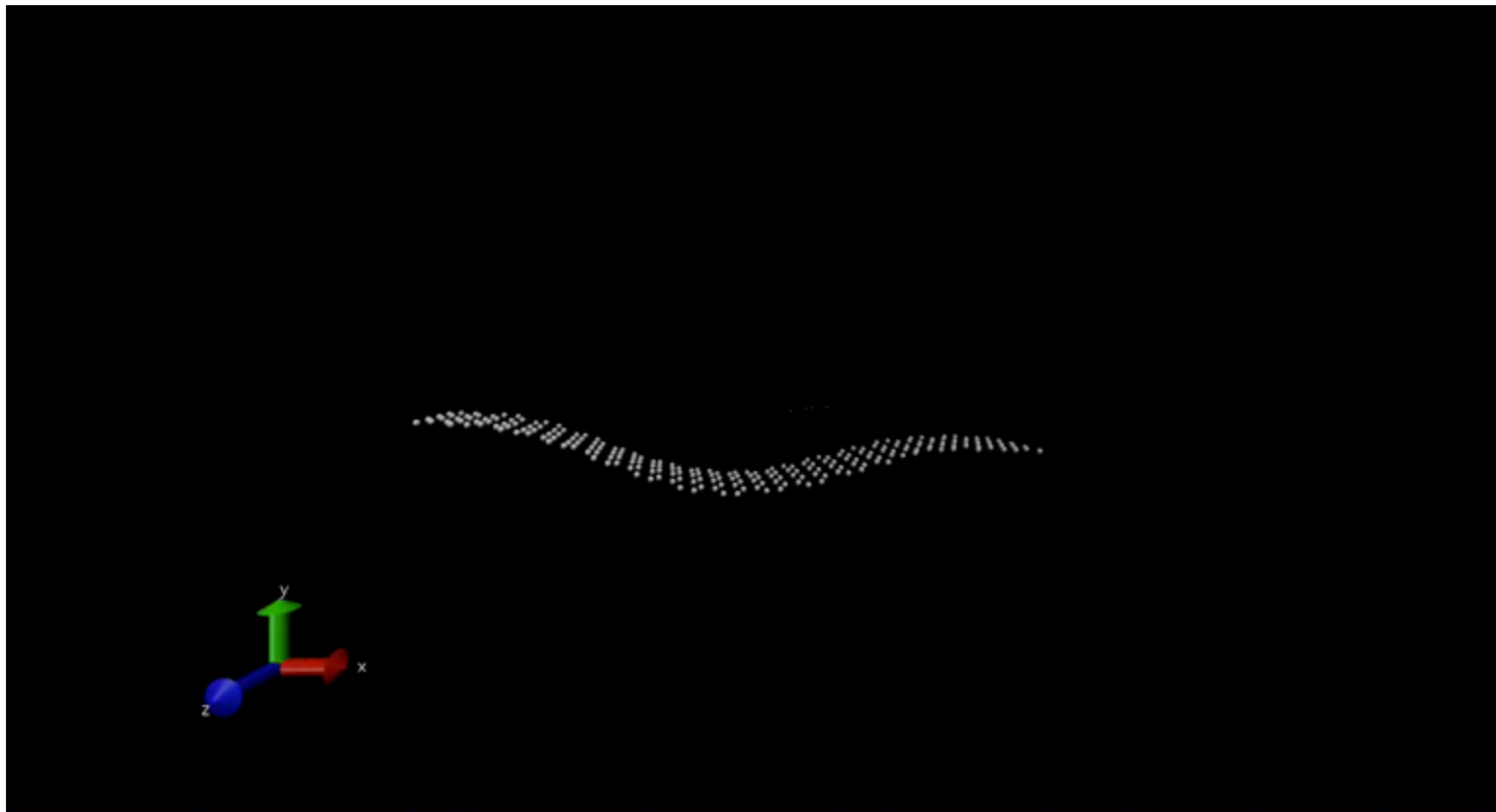
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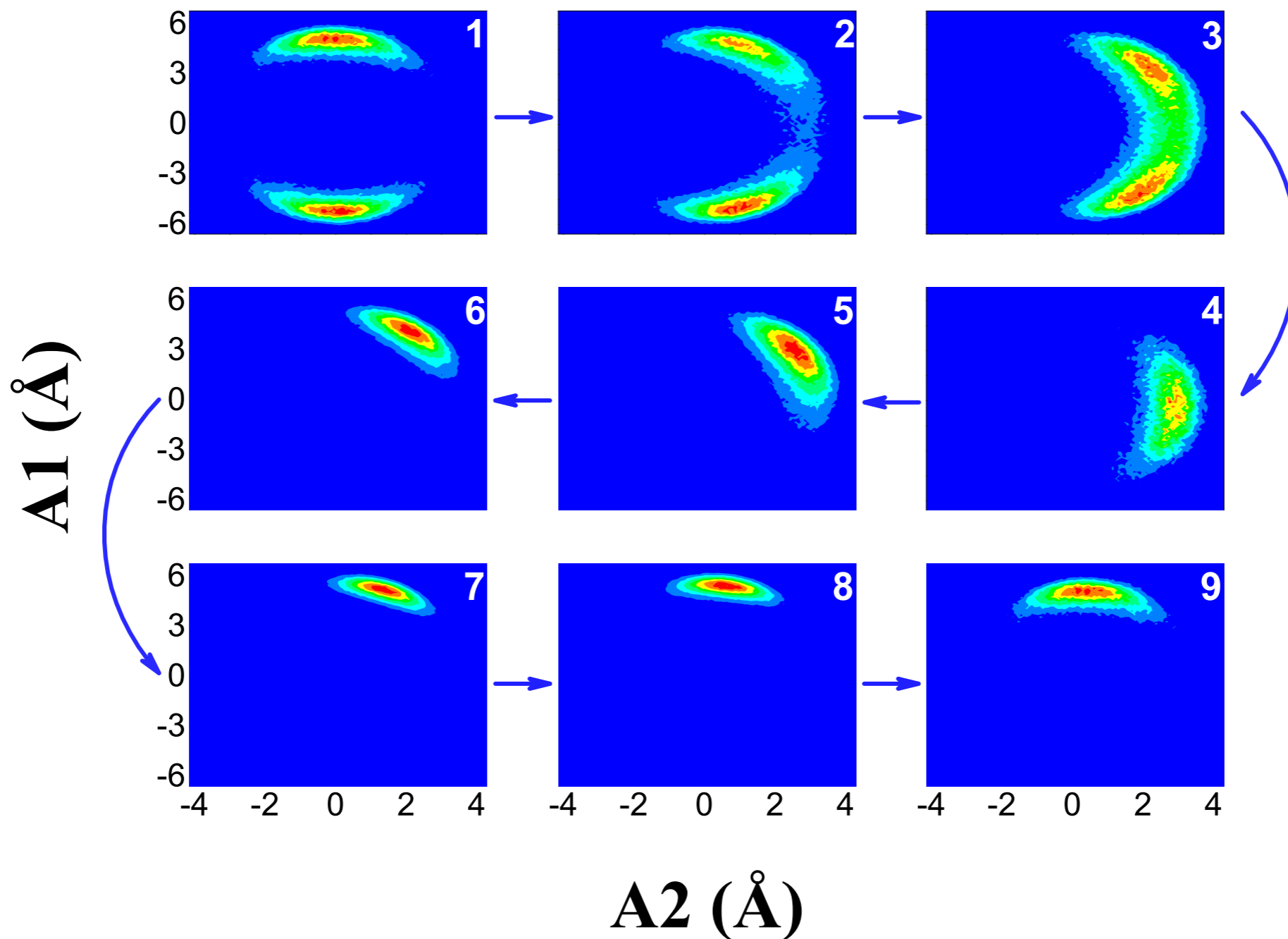
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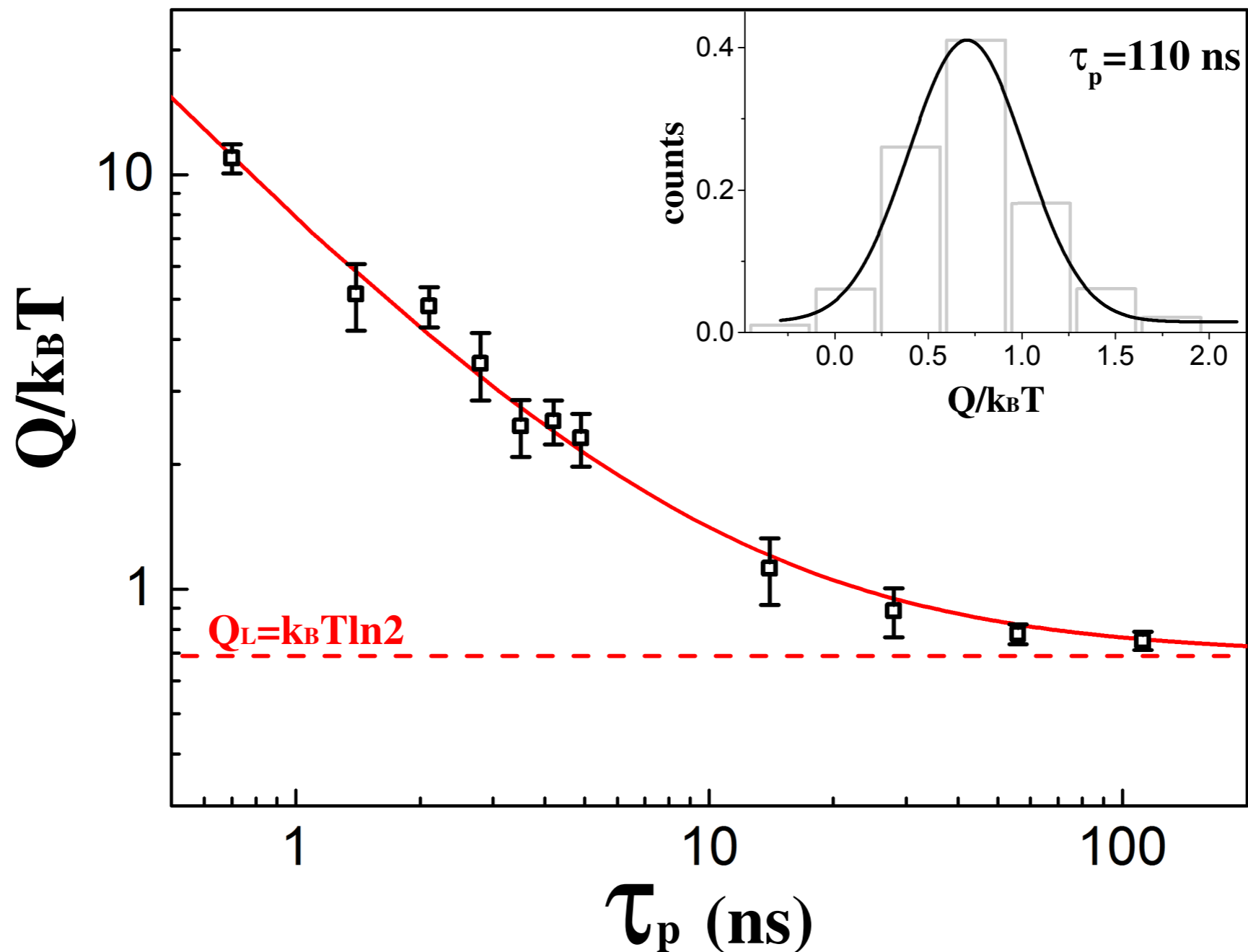
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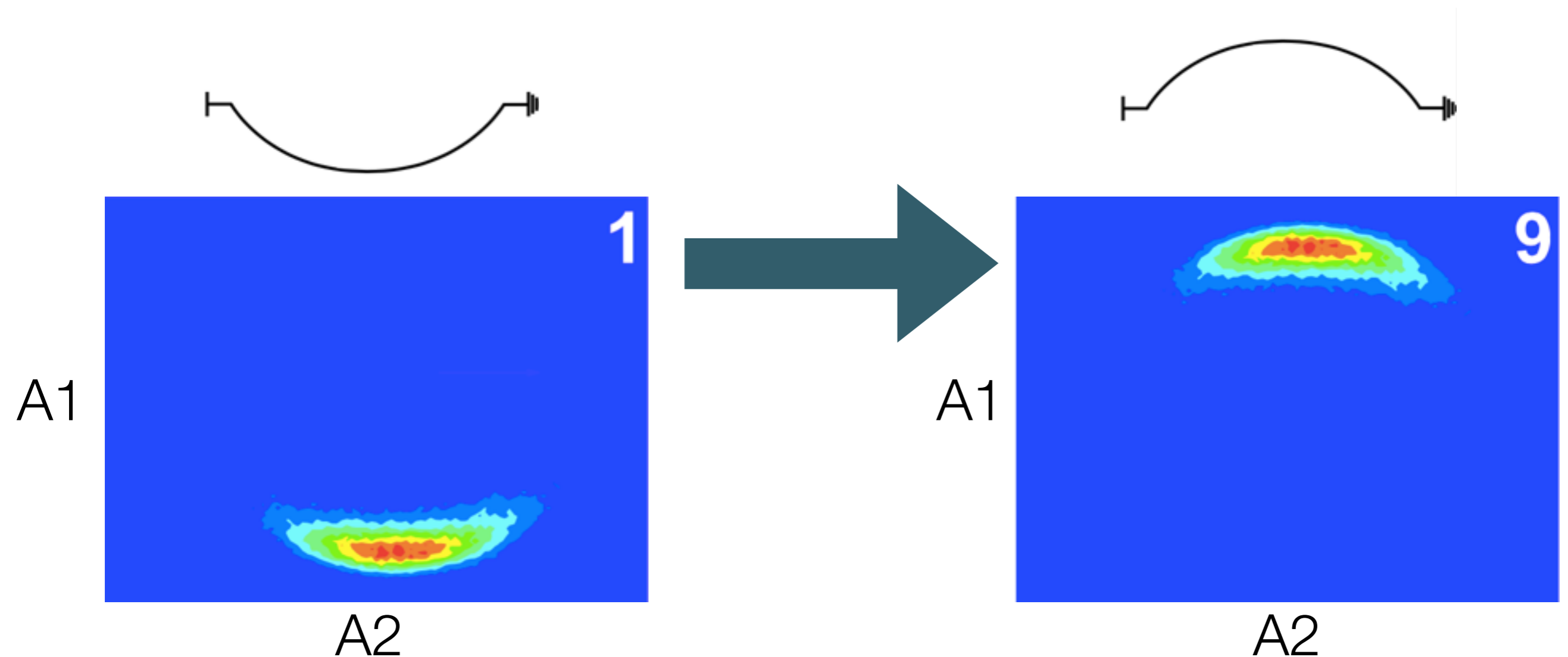
Reset protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



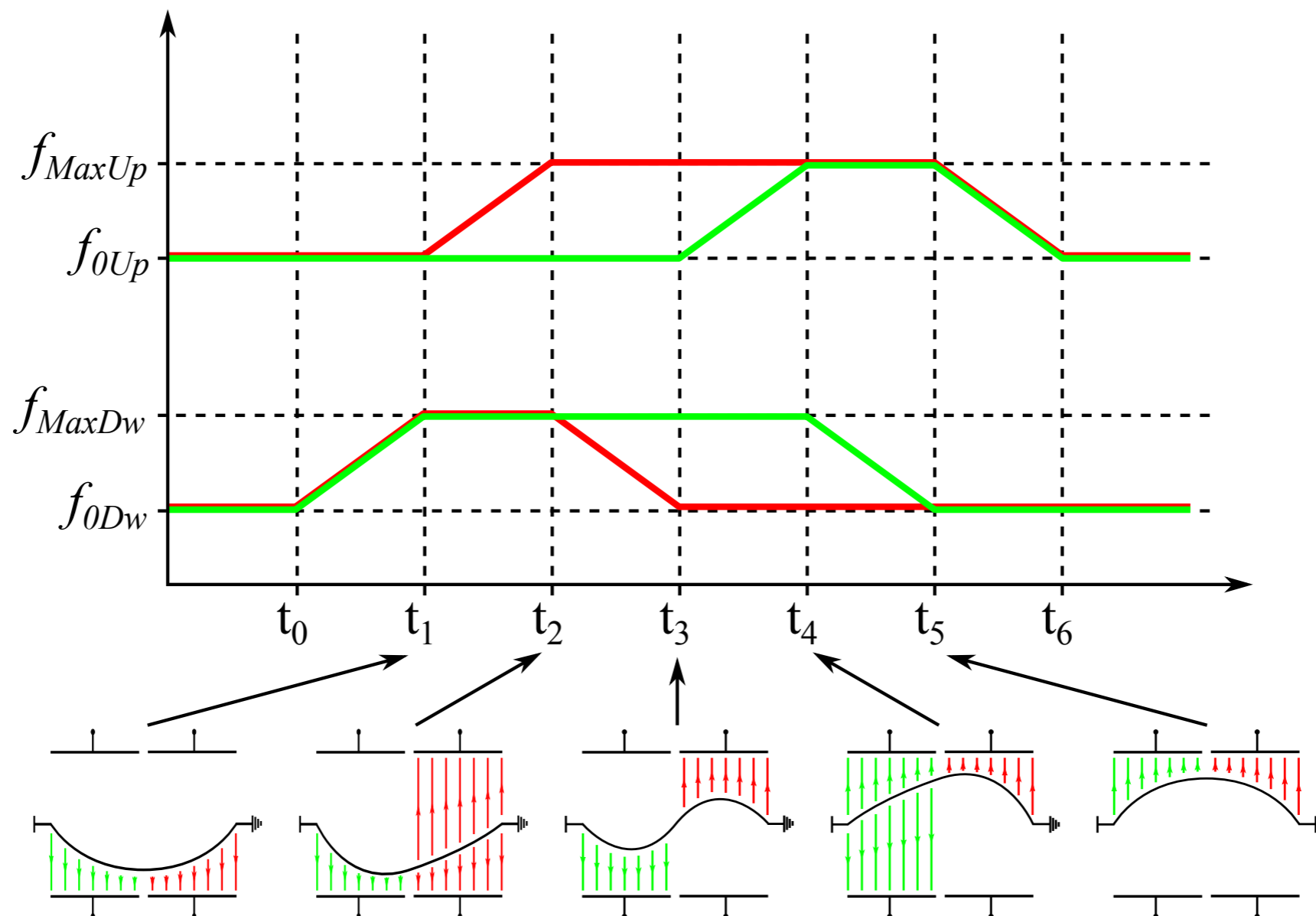
Switch protocol

- Objective: move the system from a known state to another known state
- $\Delta S = 0$
- $Q_{\min} = 0$



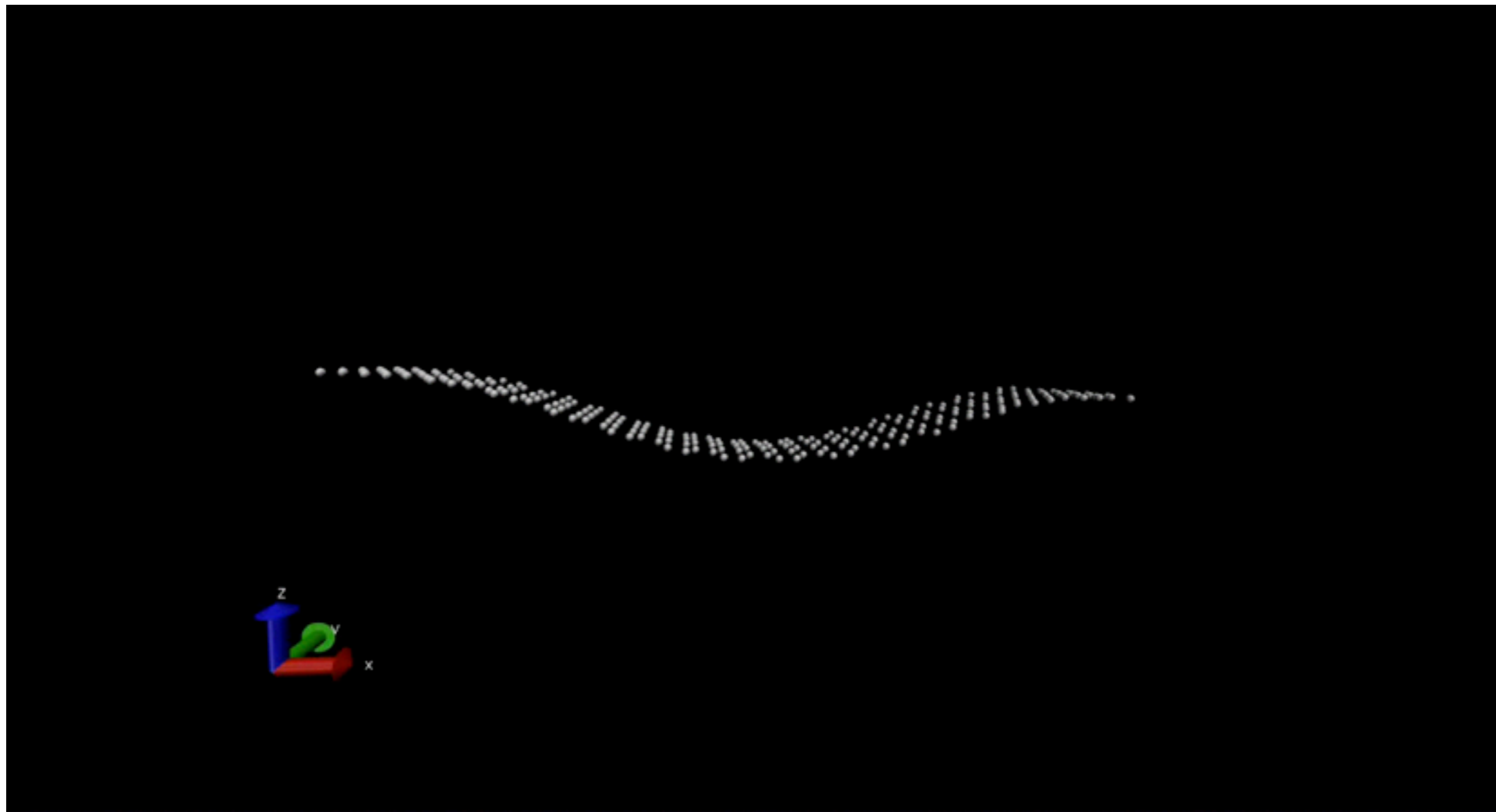
Switch protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



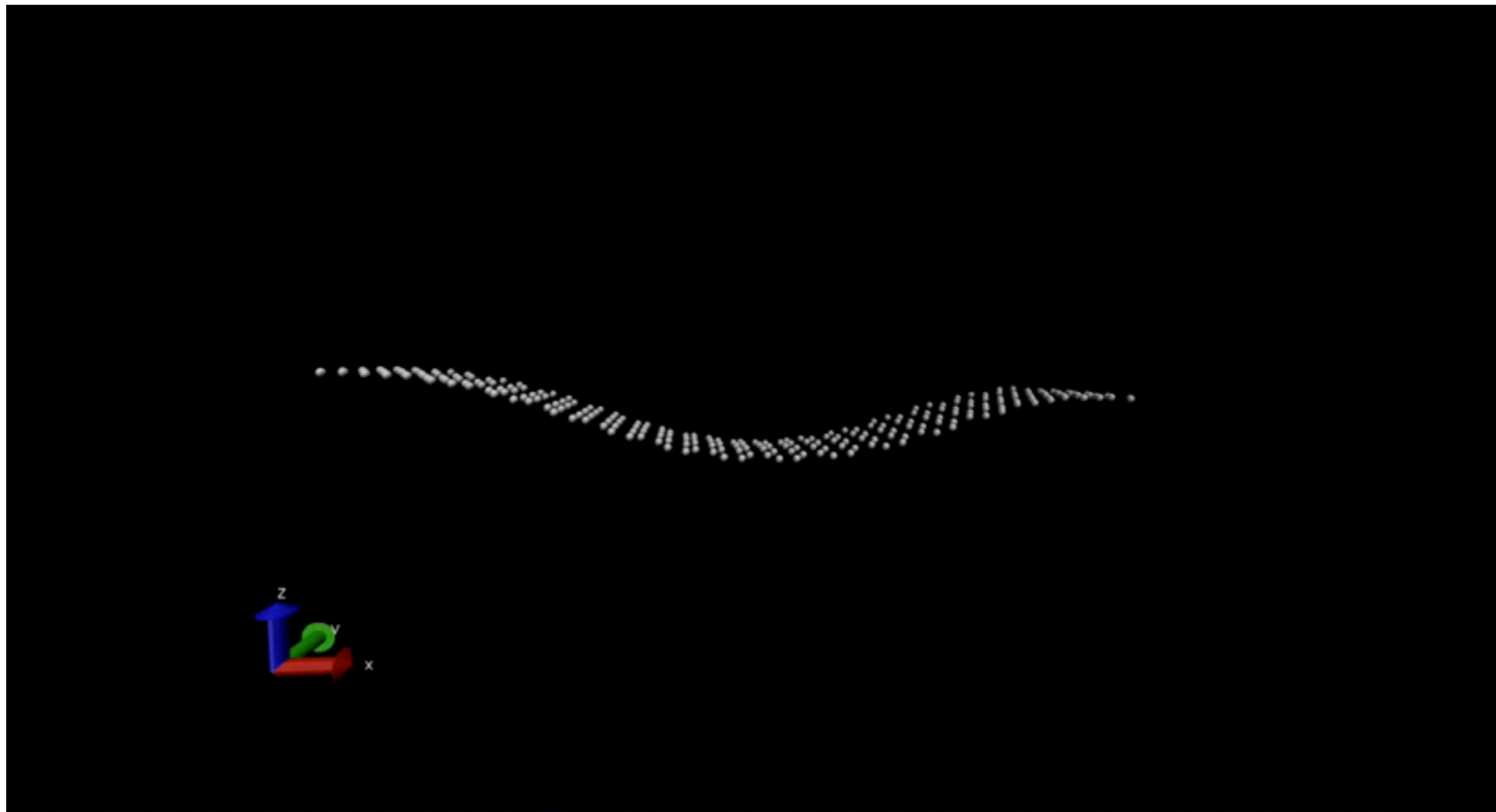
Switch protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



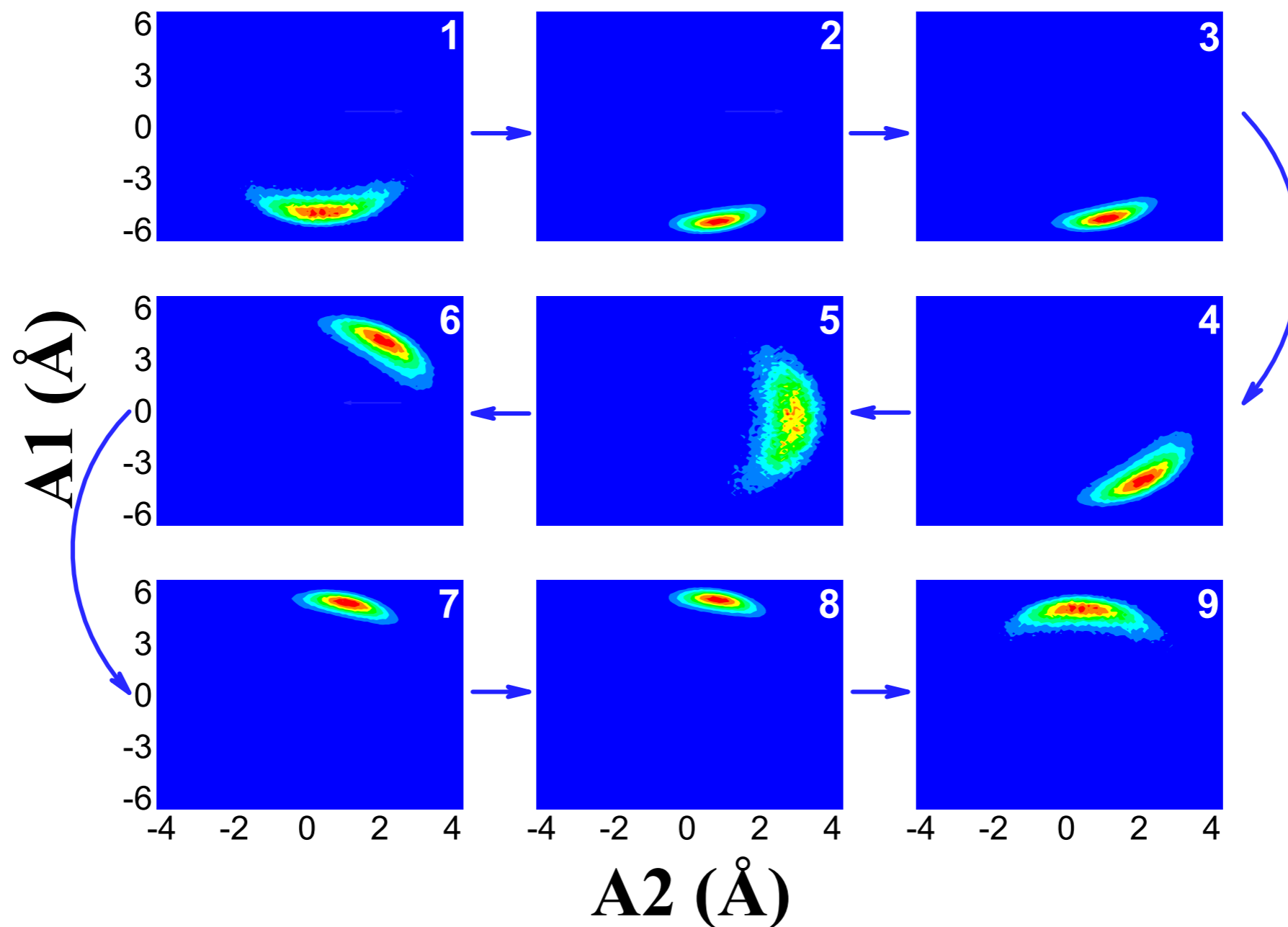
Switch protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



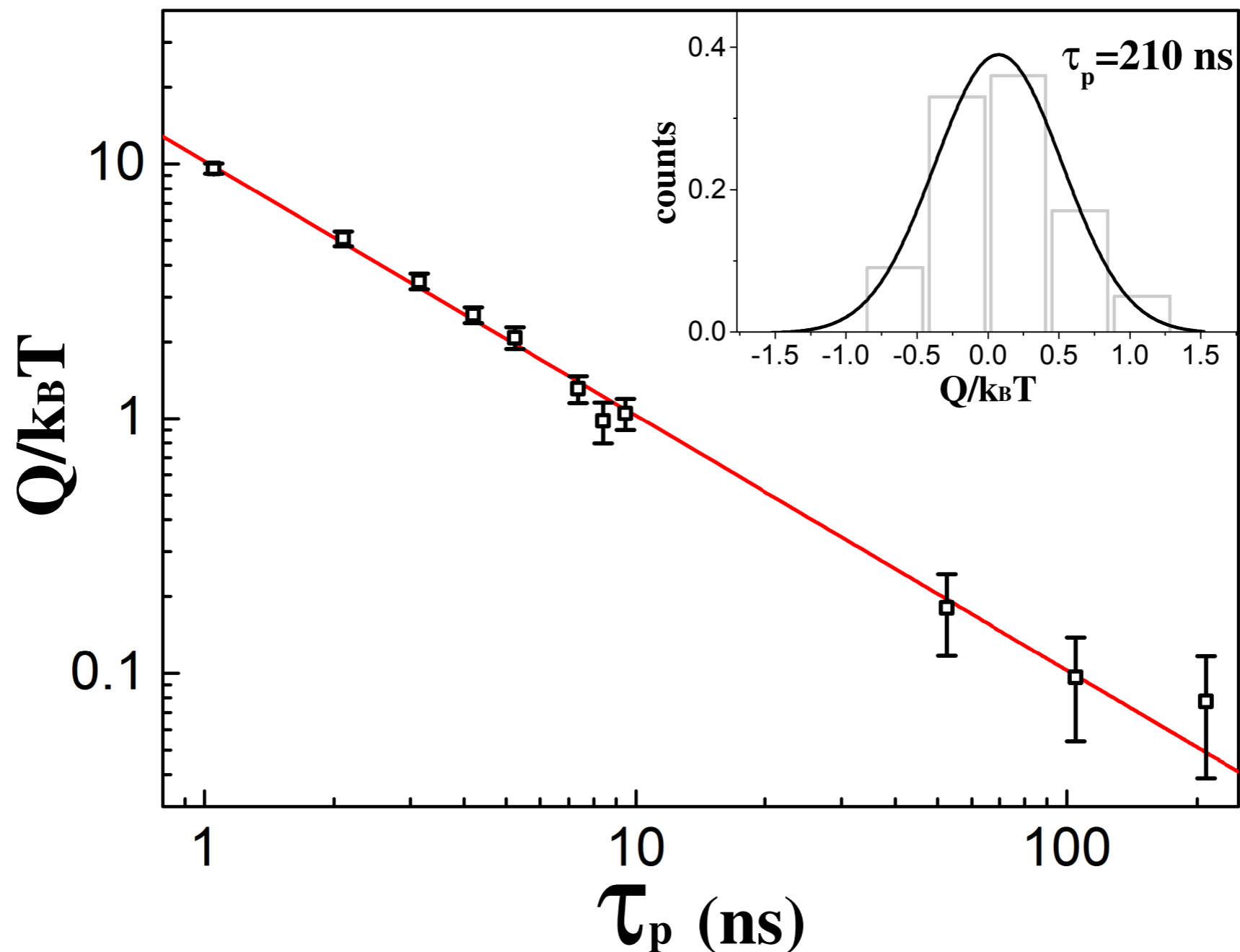
Switch protocol

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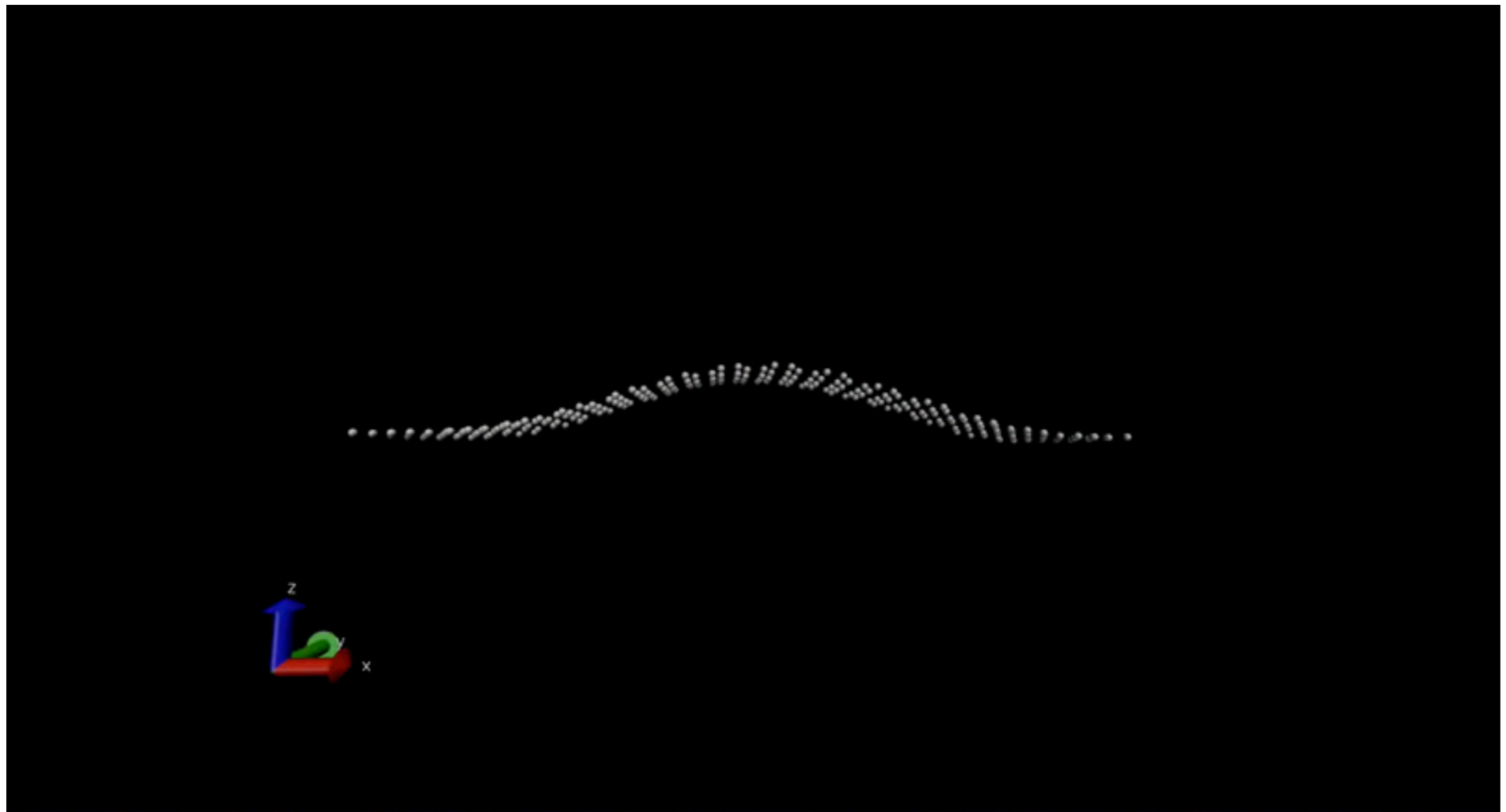
Switch protocol

Controlled way: apply a set of forces in to gently put the system in the desired configuration



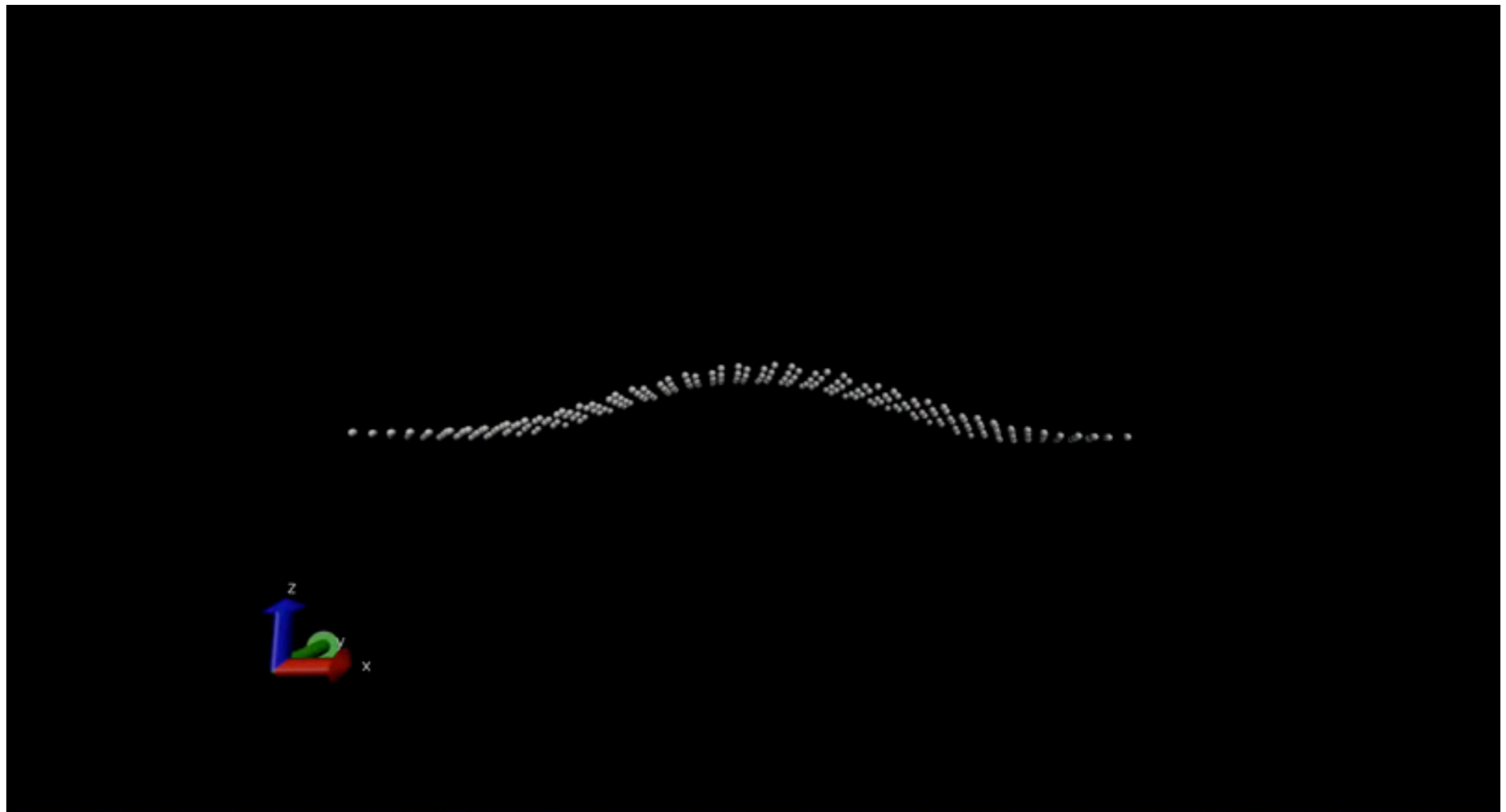
Switch protocol

Wrong way: apply the switch protocol from the wrong initial state



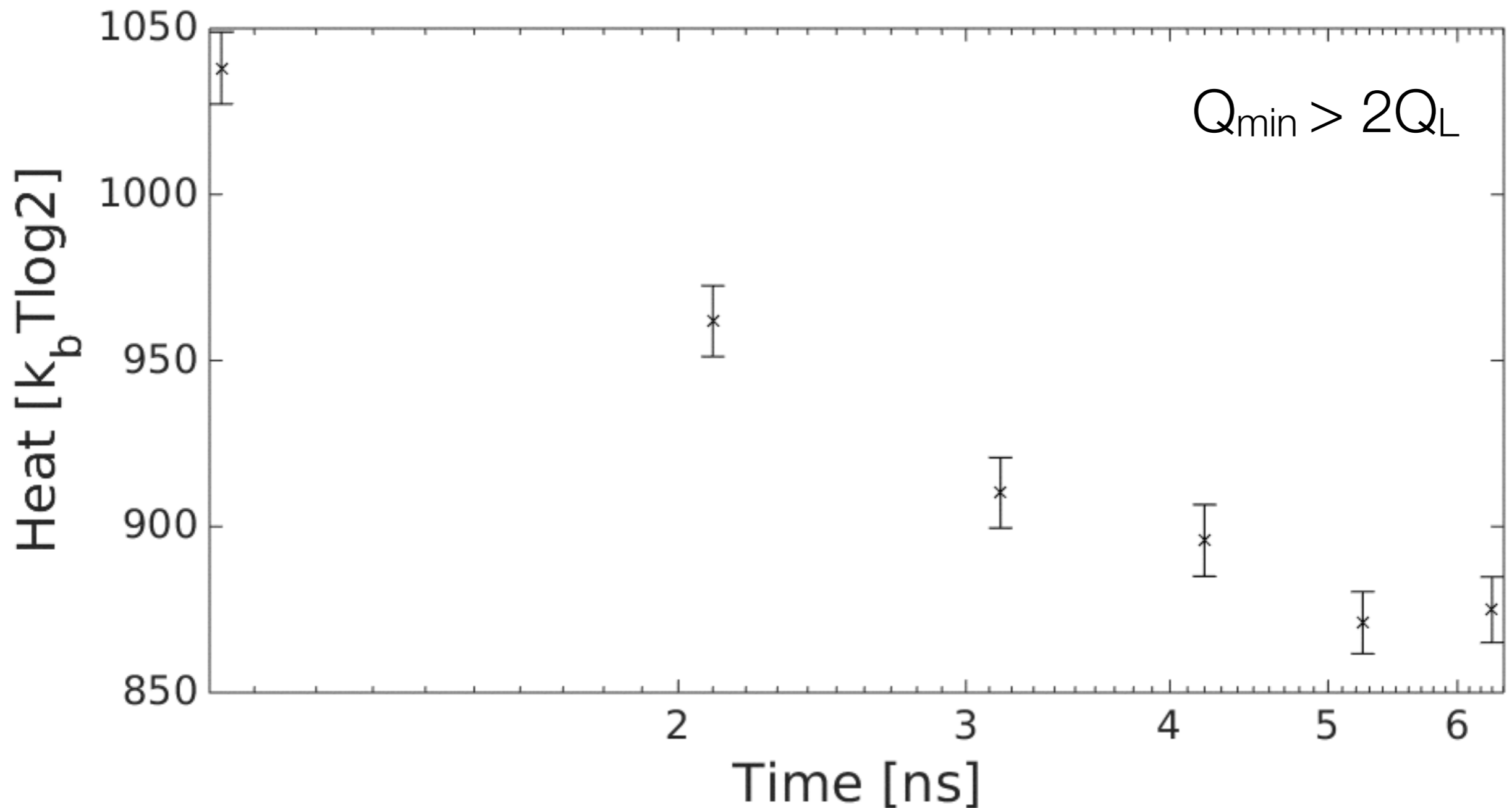
Switch protocol

Wrong way: apply the switch protocol from the wrong initial state



Switch protocol

Wrong way: apply the switch protocol from the wrong initial state



Thank you for your attention!



igor.neri@nipslab.org

